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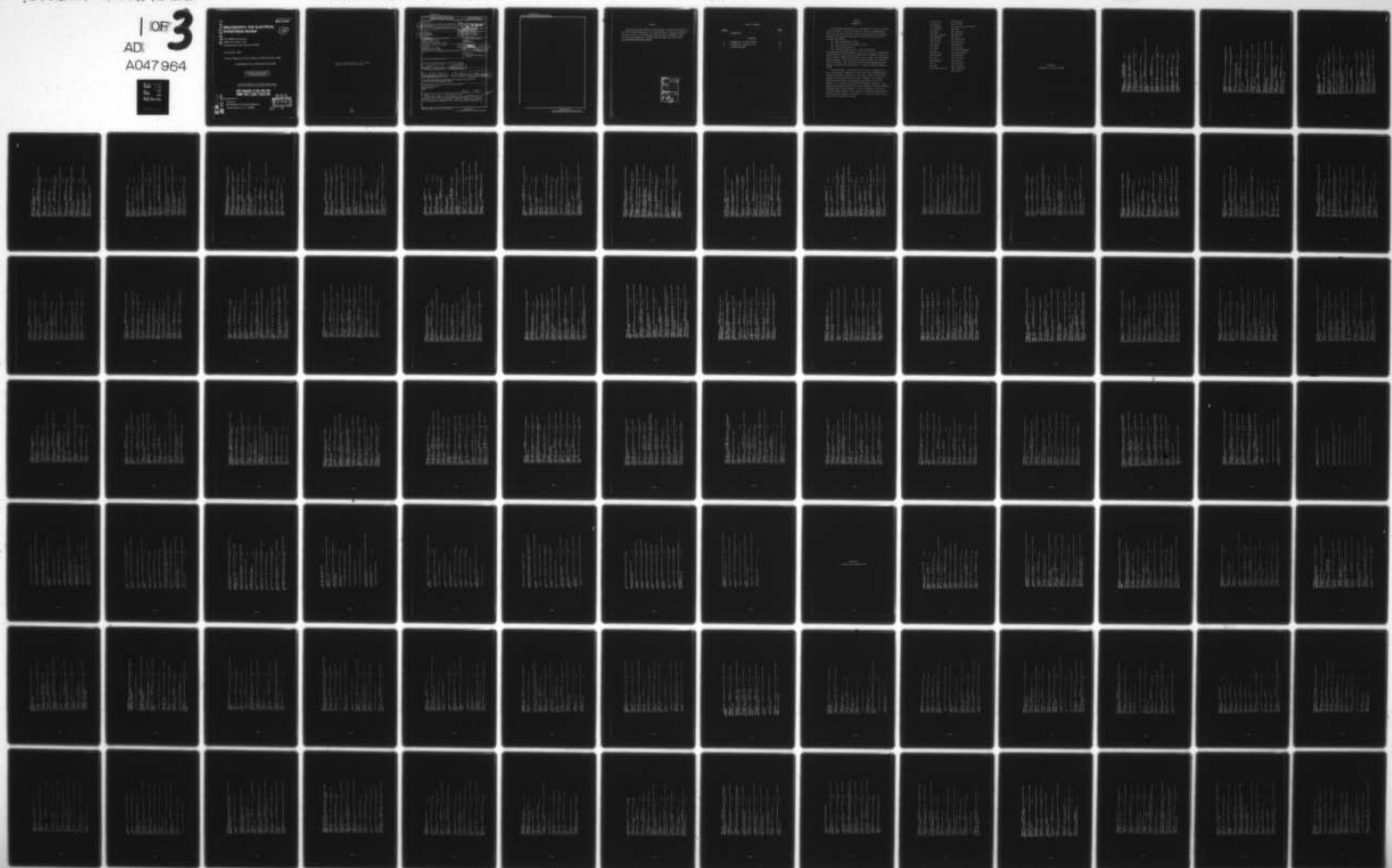
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# BIBLIOGRAPHY FOR ELECTRICAL OVERSTRESS REVIEW

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The BDM Corporation  
2600 Yale Blvd., S.E.  
Albuquerque, New Mexico 87106

10 October 1976

Topical Report for Period March 1976—October 1976

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# PREFACE

The following report contains a bibliographic listing of all materials utilized by The BDM Corporation in the performance of a review of electrical overstress effects in semiconductors under DNA Contract DNA001-76-C-0191. This work was sponsored by The Defense Nuclear Agency under RDT&E RMSS Code B323076464 Z99QAXTB097 H2490D.

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## TABLE OF CONTENTS

<u>Chapter</u>		<u>Page</u>
I	INTRODUCTION	I-1
	APPENDIXES	
A	ALPHABETICAL LISTING BY AUTHOR	A-1
B	ALPHABETICAL LISTING BY TITLE	B-1
C	LISTING BY SUBJECT	C-1



## CHAPTER 1

### INTRODUCTION

The following report contains a bibliographic listing of literature sources utilized in a review of electrical overstress phenomenology. The review included the topics concerned with burnout of semiconductor junctions when exposed to electrical transients resulting from the following environments:

- (1) EMP (Electromagnetic Pulse)
- (2) IEMP (Internal Electromagnetic Pulse)
- (3) Ionizing Dose Rate ( $\dot{\gamma}$ )
- (4) Synergistic Combinations of These Environments

The documents which were examined in the literature survey included both system documents, which related the waveforms at component terminals to the interaction between the environment and the system, and semiconductor physics documents, which related the terminal waveforms to the device failure threshold. The results of the review and recommendations for further investigations are contained in a separate document (BDM/A-212-76-TR).

The bibliography is presented in three sections, appendixes A, B, and C, respectively. Appendix A contains the listing arranged alphabetically according to the author's last name. Entries in the listing include the title, publication, and date. Appendix B is identical except that the entries are arranged alphabetically by the title. Appendix C is a subject listing of the bibliographic material. Since reports often contain material on multiple subjects, individual documents may appear under several headings. Entries in appendix C give only title and document number. More complete information on the reference can be obtained by referring to appendix B. The subject areas used for organization of appendix C include:

- |                      |                               |
|----------------------|-------------------------------|
| (1) Aircraft         | (20) Microwave                |
| (2) Analysis         | (21) MISSILES                 |
| (3) Avalanche        | (22) Nondestructive Screening |
| (4) Avionics         | (23) Power                    |
| (5) Cables           | (24) Prediction               |
| (6) Cable, Coaxial   | (25) Radiation                |
| (7) Components       | (26) Radios                   |
| (8) Coupling         | (27) Reliability              |
| (9) Current          | (28) Resistance               |
| (10) Diodes          | (29) Response                 |
| (11) Doping          | (30) Screening                |
| (12) EMP             | (31) Second Breakdown         |
| (13) Equipment       | (32) Semiconductors           |
| (14) Failures        | (33) Spacecraft               |
| (15) FETS            | (34) Subsystems               |
| (16) Hardening -     | (35) Systems                  |
| (17) IC              | (36) Thyristors               |
| (18) IEMP            | (37) Transients               |
| (19) Instrumentation | (38) Transistors              |
|                      | (39) Voltage                  |

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TRANSISTOR  
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CLARK, L.E.     GEORGE, J.L.  
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MOTOROLA

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ROEING     JAN 75

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BREAKDOWN  
MICROELECTRONICS AND RELIABILITY , 72

DURGIN, D.L. ET. AL.,  
METHODS DEVICES AND CIRCUITS FOR THE EMP HARDENING OF ARMY  
ELECTRONICS  
ARM ELE RONI OMM NO M 4

DURGIN, D.L. ET. AL.,  
METHODS, DEVICES AND CIRCUITS FOR THE EMP HARDENING OF ARMY  
ELECTRONICS  
U.S. ARMY ELECTRONICS COMMAND , JUL 72

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UPSET  
BDM CORP , JUL 75

DURGIN, D.L. , BROWN, R.W.  
KEY SUPPRESSION DEVICES PARAMETERS FOR EMP HARDENING  
LAWRENCE LIVERMORE LABS , MAR 75



DURGIN, D.L., GAGE, B.P., ET. AL.  
EMP DAMAGE HARDENING GUIDELINES , NOV 72  
BOEING

DURGIN, D.L., GAGE, B.P., ET. AL.  
EMP HARDENING OF G.F.E. , JUL 73  
BOEING

DURGIN, D.L.,  
BOUNDING EMP DAMAGE PREDICTION UNCERTAINTIES (PRESENTATION)  
BDM CORP , MAY 74

DURGIN, D.L., JENKINS, C.R., ET. AL.  
METHODS, DEVICES, AND CIRCUITS FOR THE EMP HARDENING  
OF ARMY ELECTRONICS (REPORTS<FINAL, 9/70, 1/71, 3/71, 5/71, 2/72, 3/72,  
RDM CORP ,

DURGIN, D.L.,  
INTERIM NOTES 8-52 EMP TEST PROGRAM NOTE 6 GENERAL PROCEDURES FOR  
SUBSYSTEM EMP TESTING , DEC 70  
RDM CORP

DURGIN, D.L.,  
SUPPRESSION DEVICES USED FOR EMP PROTECTION , NOV 72  
BDM CORP

DURGIN, D.L., GAGE, B.P., ET. AL.  
EMP UPSET HARDENING GUIDELINES , DEC 72  
BOEING/BDM CORP

DURGIN, D.L., GAGE, B.P., ET. AL.  
EMP ELECTRONIC ANALYSIS HANDBOOK , MAY 73  
BOEING/BDM CORP

DURGIN, D., JENKINS, CR, ET. AL.  
METHODS, DEVICES AND CIRCUITS FOR THE EMP HARDENING OF ARMY  
ELECTRONICS , JUN 72  
RDM CORP

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NUMERICAL APPROACH FOR CALCULATING THE RESPONSE OF A P-N JUNCTION  
CAPACITOR TO A RAMP SIGNAL , SEP 72  
CORRESPONDENCE

EBNER, G.C., GRAY, P.E.,  
STATIC V-I RELATIONSHIPS IN TRANSISTORS AT HIGH INJECTION LEVELS  
IEEE TRANSACTIONS , OCT 65



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METHODS FOR ENSURING SEMICONDUCTOR METALLIZATION SURVIVABILITY  
FIRST DRAFT  
AUG 75

EMERSON, W.C.  
ROUGH DRAFT-EMP PREFERRED TEST PROCEDURES (SELECTED ELECTRONIC  
PARTS)  
IIT RESEARCH INSTITUTE , NOV 72

ENGLISH, A.C.  
MESAPLASMA BREAKDOWN IN SILICON JUNCTIONS  
PROCEEDINGS OF THE IEEE CORRESPONDENCE , MAY 63

ENGLISH, A.C.  
PHYSICAL INVESTIGATION OF THE MESOPLASMA IN SILICON  
IEEE TRANSACTIONS , AUG 66

ERICKSON, J.  
LIGHTNING AND HIGH VOLTAGE SURGE PROTECTION FOR BALANCED DIGITAL  
TRANSMISSION DEVICES  
US ARMY ELECTRONICS COMMAND , SEP 72

FERNANDEZ, T.M.  
INSTRUMENTATION FOR NUCLEAR WEAPONS EFFECTS SIMULATION SYMPOSIUM-  
VOLUME I-ELECTROMAGNETIC PULSE  
AFSWC , MAR 70

FERNANDEZ, T.M.  
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VOLUME II - TRANSIENT RADIATION EFFECTS ON ELECTRONIC SYSTEMS  
AFSWC , MAR 70

FITZGERALD, D.J., STEWERT, J.J.  
SHORT PULSE EFFECTS IN SEMICONDUCTOR DIODES  
IKOR , MAY 72

FITZGERALD, D.J.  
APPLICATION OF TIME DOMAIN METHODS TO INTEGRATED CIRCUIT  
SUSCEPTIBILITY  
IKOR , MAR 73

FLEMING, D.J.  
THERMAL BREAKDOWN DELAY TIME IN SILICON P-N JUNCTIONS  
IEEE TRANSACTIONS ON ELECTRON DEVICES , FEB 71



GARTNER, W.M.,  
TEMPERATURE DEPENDENCE OF JUNCTION TRANSISTOR PARAMETERS  
IRE PROCEEDINGS

GENTRY, F.E.,  
FORWARD CURRENT SURGE FAILURE IN SEMICONDUCTOR RECTIFIERS  
AIEE TRANSACTIONS, NOV 68

GILBERT, J.L.,  
ADVANCED ELECTRO-OPTICAL SYSTEM HARDENING  
HARRY DIAMOND LABS, DEC 74

GILDER, J.M.,  
FOCUS ON POWER SEMICONDUCTORS  
ELECTRONIC DESIGN, 08 NOV 73

GILMOUR, A.S.,  
HIGH VOLTAGE ARC INTERRUPTION STUDY  
RADC, APR 72

GODTS, J.E.,  
ELECTROMAGNETIC PULSE SIMULATOR  
MARTIN MARIETTA, OCT 69

GOLEN, C.H.,  
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TRANSISTOR BASE REGIONS  
UNIV. OF MISSOURI

GOODALL, C.A.,  
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AUTONETICS, JAN 69

GRAY, R.M.,  
AN EXPERIMENTAL INVESTIGATION OF EMP INDUCED TRANSIENT UPSET OF  
INTEGRATED CIRCUITS  
SANDIA LABS, JUN 71

GREAVES, L.D.,  
SUBSYSTEM TEST METHODOLOGY FOR THE AFML DIRECT DRIVE LABORATORY  
BOEING/BDM CORP, FEB 75

GREAVES, L.D.,  
SUBSYSTEM TEST METHODOLOGY FOR THE AFML DIRECT DRIVE LABORATORY  
BOEING/BDM CORP, OCT 75

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PERFORMANCE PREDICTION  
NOV 72

GREENE, H. W.  
SPRUELL, W. F.  
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US ARMY MISSILE COMMAND  
JAN 70

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IEEE TRANSACTIONS  
NOV 66

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JUL 73

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SANDIA LABS  
JUL 71

HAICH, E. J., ET AL.  
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LAWRENCE LIVERMORE LAB.  
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APR 71

HALING, D. H.  
MORNING, L. K., ET AL.  
COMBINED EMP AND IONIZATION EFFECTS  
FEB 70

HAMBURGER, T. ET AL.  
MICROELECTRONIC PACKAGING CONCEPTS  
RADC  
JUL 65

HAMPEL, D.  
STEWART, R. G.  
EMP HARDED CMOS CIRCUIT  
HARRY DIAMOND LABS  
OCT 73

HAMPEL, D.  
STEWART, R. G.  
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PCA  
JUL 74

HAMPEL, D. ,PROST, K.J.  
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RCA ADVANCED COMMUNICATIONS LAB , JAN 75

HARDEN, J.J. ,MARTZLOFF, F.D.  
GE-MOS VARISTOR-THE SUPER ALPHA VARISTOR  
GENERAL ELECTRIC , DEC 72

HART, A.E., ET. AL. ,  
R.F. FAILURE MECHANISMS RELATED TO MICROELECTRONICS PROCESS CONTROL  
NAVAL ELECTRONICS LAB , DEC 73

HART, A.R. EL. AL. ,  
MICROWAVE INDUCED DAMAGE AND FAILURE MODES IN LOW FREQUENCY  
TRANSISTORS RELATED TO DEVICE DESIGN AND PROCESS CONTROL  
GOMAC CONFERENCE DIGEST OF PAPERS , 74

HART, A.R. ,  
RF FAILURE PREDICTION FOR MOS 4001 AND 4011 INTEGRATED CIRCUITS -  
WORKING PAPER  
NELC , JAN 76

HART, W.C. ,HIGGINS, D.F.  
A GUIDE TO THE USE OF SPARK GAPS FOR ELECTROMAGNETIC PULSE (EMP)  
PROTECTION  
JUL 73

HEIMEIER, H.H. ,  
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IEEE TRANSACTIONS ON ELECTRON DEVICES , AUG 73

HENDERSON, B. ,GLASSER, S.  
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THE TIME DERIVATIVE AND FOURIER TRANSFORM  
MISSION RESEARCH , NOV 73

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/DEVELOPMENT  
BALLISTIC RESEARCH LABS , JUN 72



HOERNERSEN, B. • MEAD, C.A.  
LIMITATIONS IN MICROELECTRONICS-II. BIPOLAR TECHNOLOGY  
SOLID STATE ELECTRONICS • 72

HOFFERMAN, T.J. •  
HIGH ENERGY PHYSICS ABSTRACTS AND TRANSLATIONS VOL. V  
AFWL FOREIGN TECHNOLOGY DIVISION • MAY 72

HOLDER, J.D. • RIME, V.W.  
STATISTICAL COMPONENT DAMAGE STUDY • JAN 71  
US ARMY MISSILE COMMAND

HOLDER, J.D. •  
DAMAGE LEVEL EVALUATION OF SEMICONDUCTOR COMPONENTS USING ULTRA  
FAST PISETIME PULSER  
U.S. ARMY MISSILE COMMAND • JUL 69

HOOPER, E.H. • JORDAN, R.L.  
ADVANCED REVERSED SWITCHING RECTIFIER MODULATOR  
WESTINGHOUSE DE SYSTEMS CENTER • OCT 75

HOOVER, C.G. • KUNZ, K.S., ET. AL.  
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RDM CORP • FEB 75

HOWARD T.A. •  
CIRCUIT ANALYSIS USING THE DRIVING-POINT-IMPEDANCE TECHNIQUE  
SANDIA LABS • FEB 72

HOWELL, C. • ANAND, V.  
THE REAL CULP-IT IN DIODE FAILURE • AUG 70  
MICROWAVES

HUENEMANN, R.G. •  
TRANSISTOR DEGRADATION FOLLOWING SECOND BREAKDOWN  
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HUFFMAN, R.L. • COLEMAN, D.W.  
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MARTIN MARIETTA CORP. • SEP 69

HUTCHINS, R.L. • DYCHE, J.W.  
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RDM CORP • MAR 74

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RADIATION, PREPRINT  
JUL 75

IRVIN, J.C.                    •  
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JACKSON, S.P.                    •  
HIGH VOLTAGE THYRISTOR STRINGS FOR INVERTER APPLICATIONS  
IEEE PROCEEDINGS - LETTERS                    •    AUG 67

JAMES, K.A.                    •SMITH, L.D.  
MOS DEVICE FAILURE PROGRAM FINAL REPORT  
ANTONETICS                    •    NOV 73

JAMES, K.A.                    •  
TEST PLAN FOR MOS DEVICE FAILURE  
ROCKWELL INTERNATIONAL ELECTRONICS RESEA.    JAN 73

JAMES, K.A.                    •  
PLAN FOR PULSE POWER TESTING OF MOS DEVICES  
ROCKWELL INTERNATIONAL-ELECTRONICS RESEA.    JUL 73

JAMES, K.A.                    •SMITH, L.D.  
PROGRAM FINAL REPORT  
ROCKWELL INTERNATIONAL ELECTRONICS RESEA.    NOV 73

JENKINS, C.R.                    •DURGIN, J.L.  
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IEEE TRANSACTIONS ON NUCLEAR SCIENCE                    •    DEC 75

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ELECTRICAL OVERSTRESS  
BDM CORP.                    •

JENKINS, C.R.                    •SCHWARTZ, J.J.  
DETAILED TEST PLAN-INTEGRATED CIRCUIT TEST  
BDM CORP                    •    MAY 73

JENKINS, C.R.                    •MYERS, J.A.  
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BDM CORP                    •    JUL 73

JENKINS, C.R. • KUNZ, M.--  
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 ROEING • MAY 75

JENKINS, C.R. • ALEXANDER, D.R., ET.  
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 BDM CORP • APR 75

JENKINS, C.R. • DURGIN, J.L.  
 EMP SUSCEPTIBILITY OF INTEGRATED CIRCUITS  
 BDM CORP • JUL 75

JENKINS, C.R. •  
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 CONSTANTS •  
 RDM CORP

JENKINS, C.R., ET. A.  
 INTEGRATED CIRCUIT EMP DATA SUMMARY • SEP 74  
 BDM CORP

JETER, T.R. • MINZ, D.J.  
 FUNCTIONAL DESIGN OF GENERIC ELECTRONIC ELECTRIC TARGETS  
 U.S. ARMY BALLISTIC RESEARCH LAB • SEP 71

JOHANUSEN, J.C., ET.  
 PULSE DAMAGE DATA FROM INTEGRATED CIRCUITS AND ELECTRONIC PARTS  
 BOEING •

JOHN, H.F. •  
 SILICON POWER DEVICE MATERIALS PROBLEMS • AUG 67  
 IEEE PROCEEDINGS

JORPPA, R.M. •  
 AN ANALYTICAL AND LOW-LEVEL TESTING APPROACH TO THE EMP SYSTEMS  
 PROBLEM •  
 AFSCW • AUG 70

KALAB, B. •  
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 OF SEMICONDUCTOR JUNCTIONS FROM ELECTRICAL TRANSIENTS  
 HARRY DIAMOND LABS •

KALAB, B. •  
 ANALYSIS OF FAILURE OF ELECTRONIC CIRCUITS FROM EMP-INDUCED SIGNALS  
 REVIEW AND CONTRIBUTION •  
 HARRY DIAMOND LABORATORIES • AUG 73

KALINOWSKI, J.J., \*WELLS, T.G.  
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SIMULATION  
BDM CORP  
FEB 74

KANO, K., \*REICH, M.J.  
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LEVELS  
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NOV 64

KELLY, R.D.,  
USING DRIVING POINT IMPEDANCE METHODS ON ACTIVE NETWORKS  
UNM

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AVALANCE BREAKDOWN CHARACTERISTICS OF A DIFFUSED P-N JUNCTION  
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NOV 62

KENNEDY, D.P., \*ET.AL.,  
COMPUTER AIDED ENGINEERING OF SEMICONDUCTOR INTEGRATED CIRCUITS  
UNIV. OF FLA.  
APR 75

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AND TUNNEL DIODES  
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GULF RADIATION TECHNOLOGY

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EXEMPT A DIGITAL COMPUTER EXECUTIVE PROGRAM FOR SYSTEMS ANALYSIS  
USER'S GUIDE  
BOEING  
NOV 74

KLARS, P.J.,  
RADIATION HARDENED AVIONICS GAIN INTEREST  
AWST  
SEP 69

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- KOKOSA, R.A. , DAVIES, R.L.  
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BOEING , AUG 71
- LANGE, T.J. ,  
IN-PLACE EMP RING III THRESHOLD VARIATION SURVEY  
BOEING
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SOLID STATE ELECTRONICS , 65 PAP
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EXPERIMENTAL RESULTS OF TESTING RESISTORS UNDER PULSE CONDITIONS  
LAWRENCE LIVERMORE LABS , NOV 67



LENNOX, C. R. ,  
EXPERIMENTAL RESULTS OF TESTING RESISTORS UNDER PULSE CONDITIONS  
SANDIA LABS , NOV 67

LENZINGER, M. ,  
GATE PROTECTION OF MOS DEVICES  
IEEE TRANSACTIONS ON ELECTRON DEVICES , APR 71

LEVERETTE, R. R. ,  
OUTLINE FOR SYSTEM VULNERABILITY/SURVIVABILITY ANALYSIS  
AFWL , DEC 68

LINDHOLM, S. F. ET. AL. ,  
A CENTER OF COMPETENCE IN SOLID STATE MATERIALS AND DEVICES  
AIR FORCE CAMBRIDGE RESEARCH LABS. , MAY 71

LINDSTEAD, R. U. , SURLY, R. J. ,  
STEADY STATE JUNCTION TEMPERATURES OF SEMICONDUCTOR CHIPS  
IEEE TRANSACTIONS ON ELECTRON DEVICES , JAN 72

LLOYD, K. J. ET. AL. ,  
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ELECTRICAL CIRCUITS  
GENERAL ELECTRIC , MAY 70

LOCASSO, J. V. ,  
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CHARACTERISTICS VOLUME II  
AUTONETICS ,

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IMPROVEMENTS IN THE TREATMENT OF COMPTON CURRENT AND AIR  
CONDUCTIVITY IN EMP PROBLEMS  
MISSION RESEARCH , SEP 73

LONG, D. ET. AL. ,  
APPENDIX A-2 BURNOUT CHAPTER OF A REPORT TITLED JFET HARDENING AND  
HIGH DOSE RATE STUDY  
GENERAL ELECTRIC ,

LOUCKS, H. D. ,  
B-52/VPD GENERAL TEST PLAN  
BOEING , FEB 72

LOUCKS, H. D. , SCHROEDER, W. T. ,  
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SYSTEMS EMP INTEGRATED TEST PROGRAM DRAFT  
JUN 72

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ANTENNA EXPERIMENTS  
ROEING  
NOV 74

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F-111/ARES DETAIL TEST PLAN, VOLUME V PHASE II INTEGRATED TEST PLAN  
(FINAL)  
ROEING  
APR 75

LUKASZEK, W.A.,  
CHENETTE, E.J.,  
INVESTIGATION OF THE TRANSITION FROM FUNNELING TO IMPACT IONIZATION  
MULTIPLICATION IN SILICON P-N JUNCTION  
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MAY 75

LUNN, T.C.,  
SHORT PULSE WIDTH FAILURE LEVEL CHARACTERIZATION FOR THE 2N3621  
JUNCTION FIELD EFFECT TRANSISTOR  
LAWRENCE LIVERMORE LAB

LUNN, T.C.,  
TECHNIQUES TO DETERMINE SUBSYSTEM LEVEL ELECTROMAGNETIC PULSE  
SUSCEPTIBILITY  
MCDONNELL DOUGLAS  
SEP 73

LUTZKEY, M.,  
DEAN, E.J., ET. AL.,  
MODELING SECOND BREAKDOWN WITH VET-2  
NAVAL SURFACE WEAPONS CENTER

MADLE, R. J.,  
CABLE AND CONNECTOR SHIELDING ATTENUATION AND TRANSFER IMPEDANCE  
MEASUREMENT USING QUADRAXIAL AND GJINTAXIAL TEST METHODS  
TRW/LAWRENCE LIVERMORE LABS  
NOV 75

MALONE, E.,  
HYBRID SPARK GAP SURGE ARRESTORS, A HIGH FREQUENCY RECEIVER SYSTEM  
ARRESTOR FOR LIGHTNING AND EMP PROTECTION  
LAWRENCE LIVERMORE LABS  
SEP 74

MANUS, D.J., ET. AL.,  
SPECIAL DEVICES, TEST STRUCTURES, AND HYBRID CIRCUITS FOR SPECIAL  
ENVIRONMENTS  
HARRY DIAMOND LABS  
JAN 74

MARKS, J.A.,  
PINE, V.J.,  
ELECTROMAGNETIC PULSE ENVIRONMENT STUDIES VOLUME II LATE TIME HIGH  
ALTITUDE ELECTROMAGNETIC PULSE CODE DEVELOPMENT  
SCIENCE APPLICATIONS  
MAY 72

MARSHAK, A.H.     TAYLOR, J.E.  
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DIFFUSION PROCESS  
IEEE TRANSACTIONS ON ELECTRON DEVICES     SEP 72

MARTIN, L.C.  
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DESIGN PRINCIPLES PUBLISHED BY BELL LABORATORIES  
LAWRENCE LIVERMORE LABS     JUN 75

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TREE MODELING REQUIREMENTS. DNA COMPONENTS RESPONSE AND  
PREDICTION WORKING GROUP MEETING MATERIAL     JAN 74

MCKAY, K.G.     MCAFFEE, K.R.  
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PHYSICAL REVIEW     SEP 53

MC MURRAY, L.R.     KLEINER, C.T.  
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CODES  
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BDM CORP

MELKONIAN, H.A.     WILLIAMS, M.F.  
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AN/APX-72 SYSTEM DESCRIPTION     JUN 74

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SANDIA LABS     SEP 72

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MISSION RESEARCH     SEP 74

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MILETTA, J.R.  
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 PROTECTIVE TECHNIQUES)

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 NOV 73

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MILLER, S.L.  
 AVALANCHE BREAKDOWN IN GERMANIUM  
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CONDUCTANCE MEASUREMENTS  
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HARRY DIAMOND LABS , MAR 75

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RAYTHEON , SEP 73

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SOLID STATE ELECTRONICS , 72

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STANFORD RESEARCH INSTITUTE , SEP 74



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 FACILITIES  
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 MEASUREMENTS ON THE DEPLETION LAYER PROPERTIES OF PLANAR DIODES  
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SEMICONDUCTOR DIODE AND TRANSISTOR MODELS  
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72
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BREAKDOWN
- BIPOLAR VOLTAGE PULSE DAMAGE EFFECTS ON TRANSISTORS
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- EFFECT OF NUCLEAR RADIATION ON THE ELECTRICAL CHARACTERISTICS OF  
SEMICONDUCTOR DEVICES

DEVELOPMENT OF A NON-DESTRUCTIVE RADIATION EFFECTS  
PREDICTION TECHNIQUE

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VANZETTI INFRARED AND COMPUTER SYSTEMS 71

FINAL SUMMARY REPORT ON SEMICONDUCTOR DAMAGE STUDY PHASE II  
BDM CORP , AUG 70

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TRANSIENTS

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TRANSIENTS  
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FRANKLIN INSTITUTE , NOV 69

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BDM CORP , 69

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(EED) RESPONSE TO ELECTROMAGNETIC RADIATION (EMR)  
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INTEGRATED CIRCUIT ELECTROMAGNETIC SUSCEPTIBILITY INVESTIGATION PHASE II MCDONNELL DOUGLAS	OCT 73
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USE OF THE FAIRCHILD 600 TO DETERMINE DAMAGE PARAMETERS	
CIRCUIT DAMAGE ANALYSIS TECHNIQUE	
A SURVEY OF SELECTED NETWORK ANALYSIS PROGRAMS	
ELECTROMAGNETIC EFFECTS OF NUCLEAR EXPLOSIONS ON ELECTRONIC SYSTEMS FREQUENCY TECHNOLOGY	69
SPARK GAP SIMULATES A-BOMB EMP ELECTRO-TECHNOLOGY	SEP 69
SEMICONDUCTOR DAMAGE CONSTANTS	

SEMICONDUCTOR DAMAGE TEST RESULTS FOR SANDIA DEVICES UZ110, UZ130,  
UZ9079 , MAR 69  
RDM CORP

HIGH POWER EFFECTS IN SEMICONDUCTOR COMPONENTS  
MCDONNELL DOUGLAS , JUN 70

## SECTION II DISCRETE DAMAGE TESTS

CHAPTER 7 SUBSYSTEM DAMAGE SUSCEPTIBILITY  
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RDM CORP , AUG 68

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## SECTION VI DESIGN PRACTICES

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AND MISSILE APPLICATIONS, STANDARD CONTROL PROGRAM FOR

SECTION II A MODEL TO PREDICT POWER FAILURE OF SEMICONDUCTOR DEVICES  
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APPENDIX B  
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TRANSISTOR BASE REGIONS  
UNIV. OF MISSOURI  
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THE TIME DERIVATIVE AND FOURIER TRANSFORM  
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BDM CORP  
• JAN 74

JENKINS, C. L.  
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RDM CORP.  
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ZANIOLO, C.  
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72

CHARLES, H. S., ET. AL.  
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JOHN HOPKINS UNIV.  
FEB 75

SCHAFFT, H. A.  
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SEP 68

RUDENSTEIN, D. A. PAUL  
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U.S. ARMY MISSILE COMMAND  
DEC 70

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 A SURVEY OF SECOND BREAKDOWN PHENOMENA, MECHANISMS AND DAMAGE IN  
 SEMICONDUCTOR JUNCTION DEVICES  
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A SURVEY OF SELECTED NETWORK ANALYSIS PROGRAMS

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 JUNCTIONS UNDER REVERSE BIAS  
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HEIMEIER, H.M.  
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 STUDY  
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BIPOLAR VOLTAGE PULSE DAMAGE EFFECTS ON TRANSISTIONS

SUTHERLAND, P.G.  
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DURGIN, D.L.  
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 RDM CORP.      • MAY 74

LEISTIKO, O.      • GROVE, A.S.  
 BREAKDOWN VOLTAGE OF PLANAR SILICON JUNCTIONS  
 SOLID STATE ELECTRONICS      • 65 PAP

RUCKLING OF THERMALLY GROWN SiO<sub>2</sub> THIN FILMS  
 IEEE TRANSACTIONS ON ELECTRON DEVICES      • JAN 72

VINCENT, W.C.  
 B-1 ALECS POST EXPERIMENT SUMMARY FOR TECHNICAL DIRECTIVE 3-18  
 MEASUREMENTS  
 BOEING      • DEC 74

VINCENT, M.C., ET. A.  
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(DRAFT)  
BOEING • APR 75

FLORES, A. • GOULD, J.  
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BOEING • NOV 74

FLORES, A. • GOULD, J.  
B-1 EMP SUBSYSTEM ASSESSMENT DATA, IFF AN/AFC-64  
BOEING • DEC 74

FLORES, A. • GOULD, J.  
B-1 EMP SUBSYSTEM ASSESSMENT DATA, UHF RADIO AN/AFC-119  
DEC 74

VINCENT, M.C., ET. A.  
B-1 SCALE MODEL PRELIMINARY TEST PLAN FOR MEASUREMENT OF WEAPONS  
BAY AND WHEEL WELL COUPLING (FINAL)  
BOEING • OCT 74

DICKHAUT, R.H.  
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DAMAGE MODELING  
CALSPAN • JUN 75

LOUCKS, H.D.  
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SUTTER, C.C. • VINCENT, M.L., ET. A.  
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MEASUREMENT USING QUADRANTIAL AND QUANTAXIAL TEST METHODS  
TRW/LAWRENCE LIVERMORE LABS • NOV 75

DAIRIKI, S. • VANCE, E.F.  
CABLE SYSTEM ANALYSIS  
AFWL • AUG 71



LEE, T.P.  
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FOR DIFFUSED JUNCTIONS IN THIN EPITAXIAL SILICON LAYERS  
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CASE, C.  
MILETTA, J.  
CAPACITOR FAILURE DUE TO HIGH LEVEL ELECTRICAL TRANSIENTS  
HARRY DIAMOND LABS , DEC 75

CASE, C.  
MILETTA, J.  
CAPACITOR FAILURE TO HIGH LEVEL ELECTRICAL TRANSIENTS DRAFT  
HARRY DIAMOND LABS , SEP 74

#### CHAPTER II - PROGRAM APPROACH AND TECHNICAL DISCUSSION

MILETTA, J.A.  
CHAPTER IV EMP EFFECTS ON COMPONENTS (PART OF EMP RADIATION AND  
PROTECTIVE TECHNIQUES)

#### CHAPTER 7 SUBSYSTEM DAMAGE SUSCEPTIBILITY ROEING

TASCA, D.M.  
PEDEN, J.C.  
CHARACTERISTICS AND APPLICATIONS OF METAL OXIDE VARISTORS FOR EMP  
HARDENING  
LAWRENCE LIVERMORE LABS , AUG 74

SANSEN, W.M.C.  
MEYER, P.S.  
CHARACTERIZATION AND MEASUREMENT OF THE BASE AND EMITTER  
RESISTANCE OF BIPOLAR TRANSISTORS  
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HOWARD T.A.  
CIRCUIT ANALYSIS USING THE DRIVING-POINT-IMPEDANCE TECHNIQUE  
SANDIA LABS , FEB 72

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DEMART, B.  
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ROEING

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CMOS RADIATION HARDENING  
HUGHES AIRCRAFT • OCT 74

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FLASH X-RAY MACHINES  
MCDONNELL DOUGLAS AERONAUTICS CO. • JUL 70

SCHWARTZ, J.J., ET. AL.  
COMBINED DOCUMENTATION WORK ORDER 2-14  
BOEING/BDM CORP • APR 73

HALING, D.H., MORNING, L.K., ET. A  
COMBINED EMP AND IONIZATION EFFECTS  
FEB 70

COMMON MODE MODEL DEVELOPMENT FOR COMPLEX CABLE SYSTEMS  
BOEING • JUN 73

COE, R.,  
COMPARISON OF ANTENNA-RELATED PREDICTIVE MODELS WITH R-1 SCALE  
MODEL MEASUREMENTS IN ALECS  
BOEING • JAN 75

MILETTA, J.,  
COMPONENT DAMAGE FROM ELECTROMAGNETIC PULSE (EMP) INDUCED TRANSIENTS  
(DRAFT)  
NOV 73

COMPONENT MODELING AND TEST  
INW VULNERABILITY AND HARDNESS LAB • APR 75

COOPER, J.A.,  
COMPONENT VULNERABILITY  
SANDIA LABS • AUG 76

SLOTBOOM, J.W.,  
COMPUTER-AIDED TWO DIMENSIONAL NUMERICAL ANALYSIS OF BIPOLAR  
TRANSISTORS  
IEEE TRANSACTIONS ON ELECTRON DEVICES • AUG 73

KENNEDY, D.P., ET. AL.,  
COMPUTER AIDED ENGINEERING OF SEMICONDUCTOR INTEGRATED CIRCUITS  
UNIV. OF FLA. • APR 76

SUTHERLAND, A.O. •KENNEY, D.  
COMPUTER ANALYSIS OF HOT SPOT FORMATION IN POWER TRANSISTORS  
UNIV. OF FLORIDA •

LAWRY, D.I.  
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INPUTS, SPONSORED BY US ARMY MOBILITY EQUIPMENT RESEARCH : DEV. CTR  
U.S. ARMY MOBILITY EQUIPMENT RESEARCH AN. APR 70

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IEEE TRANSACTIONS • JUL 64

CORRELATION BETWEEN SECOND BREAKDOWN AND INFRARED RADIATION IN  
POWER TRANSISTORS  
VANZETTI INFRARED AND COMPUTER SYSTEMS • 71

CLARK, L.E. •GEORGE, W.L.  
CURRENT CROWDING IN HARDENED POWER TRANSISTORS  
MOTOROLA •

GRUTCHFIELD, T.B. •MONITORIA, T.J.  
CURRENT MODE SECOND BREAKDOWN IN EPITAXIAL PLANAR TRANSISTORS  
IEEE TRANSACTIONS • NOV 66

HOLDEN, J.D.  
DAMAGE LEVEL EVALUATION OF SEMICONDUCTOR COMPONENTS USING ULTRA  
FAST RISETIME PULSER  
U.S. ARMY MISSILE COMMAND • JUL 69

DEFENSE NUCLEAR AGENCY EMP SEMINAR-SUBSYSTEM AND COMPONENT  
SUSCEPTIBILITY  
IIT RESEARCH INSTITUTE • MAY 74

DEFENSE NUCLEAR AGENCY EMP SEMINAR "SUBSYSTEM AND COMPONENT  
SUSCEPTIBILITY"  
IIT RESEARCH INSTITUTE • MAY 74

SHANNON, C.W.  
DEGRADATION OF MONOLITHIC SEMICONDUCTOR DEVICES BY HIGH AMPLITUDE  
CURRENT PULSES  
RADC  
FEB 73

WILSON, P.R.  
DEPLETION LAYER AND CAPACITANCE CALCULATIONS FOR GAUSSIAN DIFFUSED  
JUNCTIONS  
SOLID STATE ELECTRONICS  
64

WILSON, P.R.  
DEPLETION LAYER CALCULATIONS FOR ERKOR FUNCTION DIFFUSED JUNCTIONS  
SOLID STATE ELECTRONICS  
64

GWYN, C.W.  
DESIGNING ULTRAFAST BIPOLAR TRANSISTORS  
SANDIA LABS  
JUL 71

MORGAN, G.E., ET AL.  
DESIGN GUIDELINES FOR EMP HARDENING OF AERONAUTICAL SYSTEMS  
AFWL  
JUL 73

MORGAN, G.E.,  
DESIGN GUIDELINES FOR EMP HARDENING OF AERONAUTICAL SYSTEMS (DRAFT)  
AUTONETICS  
APR 72

BREWSTER, J.L., ET AL.  
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PULSED SYSTEMS  
AFWL  
NOV 65

JENKINS, C.R.  
DETAILED TEST PLAN-INTEGRATED CIRCUIT TEST  
HDM CORP  
MAY 73

DETAILED TEST PLAN 9-1 SCALE MODELS/ALECS TEST PROGRAM SECTION 5  
NOV 74

THOMAS, R.F.  
DETERMINATION OF A PHYSICAL MODEL FOR DOUBLE DIFFUSED TRANSISTORS  
SOLID STATE ELECTRONICS, PERGAMON PRESS  
64

DETERMINATION OF SEMICONDUCTOR FAILURE LEVELS DUE TO HIGH VOLTAGE  
TRANSIENTS





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DEVELOPMENT OF DISC TRANSISTORS FOR TPO APPLICATIONS IN EMP  
SUPPRESSION  
HARRY DIAMOND LABS • OCT 74

TASCA, D.M.  
MUNSCHE, D.C., ET. AL  
DEVICE DEGRADATION BY HIGH AMPLITUDE CURRENTS AND RESPONSE  
CHARACTERISTICS OF DISCRETE RESISTORS

HUDENSTEIN, P.P.  
DIELECTRIC BREAKDOWN IN SOLIDS  
US ARMY MISSILE COMMAND • DEC 74

LAWRENCE, H.  
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HDM CORP • SEP 74

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IIT RESEARCH INSTITUTE • AUG 71

OURGIN, D.L.  
SCHWARTZ, J.J., ET. AL  
DNA EMP HANDBOOK CHAPTER 13 COMPONENT EMP SENSITIVITY AND SYSTEM  
UPSET  
ADM CORP • JUL 75

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DNA EMP SEMINAR SYSTEM LEVEL TESTING  
IIT RESEARCH INSTITUTE • SEP 75

AZARAWICZ, J.L.  
DNA HARDNESS ASSURANCE PROGRAM PLAN (DRAFT)  
IRT , DEC 75

SCHWARZ, J. J.  
DRAFT AEROSPACE VEHICLE EMI TRANSIENT TEST TECHNIQUES  
RDM CORP , MAR 72

SINGLETARY, J.H.  
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RDM CORP , OCT 70

SCHWARZ, J.J.  
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APR 75

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(BOUND TOGETHER)  
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NASA ,

SAH, C.T.  
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HARRY DIAMOND LABS , MAR 75

RUDENSTEIN, P.P.  
EFFECT OF IONIZING RADIATION ON SECOND BREAKDOWN  
SOLID STATE ELECTRONICS , FEB 73

SIZE, S.M.  
EFFECT OF JUNCTION CURVATURE ON BREAKDOWN VOLTAGE IN SEMICONDUCTORS  
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EFFECT OF NUCLEAR RADIATION ON THE ELECTRICAL CHARACTERISTICS OF  
SEMICONDUCTOR DEVICES ,

RADI, G.  
EFFECT OF THE SPATIALLY VARYING MINORITY CARRIER MOBILITY IN THE  
DRIFT TRANSISTOR  
SOLID STATE ELECTRONICS • 72

SLIVKOV, T. N., ET. •  
ELECTRICAL BREAKDOWN AND DISCHARGE IN A VACUUM  
AFSC FOREIGN TECHNOLOGY DIVISION • 72

BAKANOWSKI, A.E. • FORSTER, J.M.  
ELECTRICAL PROPERTIES OF G.O.D DOPED DIFFUSED SILICON COMPUTER  
DIODES  
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NORTHROP CORPORATE LABS • FEB 72

CUMMING, J.R. •  
ELECTROMAGNETIC COMPATIBILITY-MCDONNELL DOUGLAS CORPORATION  
ELECTRONIC SYMPOSIUM  
MCDONNELL DOUGLAS • NOV 69

• ELECTROMAGNETIC EFFECTS OF NUCLEAR EXPLOSIONS ON ELECTRONIC SYSTEMS  
FREQUENCY TECHNOLOGY • 69

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ELECTROMAGNETIC PULSE SENSOR HANDBOOK VOLUME I  
AFWL • JUN 71

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ELECTROMAGNETIC PULSE INSTRUMENTATION HANDBOOK-VOLUME I  
AFWL • OCT 71

MEREWETHER, D.E. • COOPER, J.A., ET. AL  
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SANDIA LABS • SEP 72

MARKS, J.A. • PINE, V.W.  
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ALTITUDE ELECTROMAGNETIC PULSE CODE DEVELOPMENT  
SCIENCE APPLICATIONS • MAY 72

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SCIENCE APPLICATION • DEC 73

VANCE, E.F.  
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STANFORD RESEARCH INSTITUTE • FEB 75

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MARTIN MARIETTA

BAUM, C.E., ED.  
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DETONATIONS  
UNIV. OF DELAWARE •

MCKAY, K.G. •MCAFEE, K.R.  
ELECTRON MULTIPLICATION IN SILICON AND GERMANIUM  
PHYSICAL REVIEW • SEP 53

DOMINGOS, H.  
ELECTRO THERMAL OVERSTRESS FAILURE IN MICROELECTRONICS  
RADC • APR 73

HUFFMAN, R. L. •COLEMAN, D.W.  
EMP CHARACTERIZATION OF SPRINT AUTOPILOT COMPONENTS--FINAL REPORT  
MARTIN MARIETTA CORP. • SEP 69

DURGIN, D.L. •GAGE, H.P., ET. AL.  
EMP DAMAGE HARDENING GUIDELINES • NOV 72  
POEING

EMP DEGRADATION ANALYSIS AND APPLICATION OF EMP FILTERS  
AUTONETICS • OCT 73

DURGIN, D.L.                    \*GAGE, B.P., ET. AL.  
EMP ELECTRONIC ANALYSIS HANDBOOK                    , MAY 73  
BOEING/BDM CORP

BROWN, R.M.                    \*DURGIN, D.L., ET. AL  
EMP ELECTRONIC DESIGN HANDBOOK                    , APR 73  
BOEING

SHERMAN, R.                    \*DE GOSS, P.M.  
EMP ENGINEERING AND DESIGN PRINCIPLES                    , 73  
BELL LABORATORIES

HAMPEL, D.                    \*STEWART, R.G.  
EMP HARDENED CMOS CIRCUIT                    , OCT 73  
HARRY DIAMOND LABS

HAMPEL, D.                    \*STEWART, R.G.  
EMP HARDENED CMOS CIRCUITS-FINAL REPORT                    , JUL 74  
PCA

WARNER, G.L.                    \*DOSKOCIL, A.C.  
EMP HARDENING APPROACH FOR SAM-D                    , SEP 73  
RAYTHEON

DURGIN, D.L.                    \*GAGE, B.P., ET. AL.  
EMP HARDENING OF G.F.E.                    , JUL 73  
BOEING

WOUTERS, L.F.                    \*  
EMP PROTECTION ENGINEERING THE NEED FOR DOCUMENTATION                    , MAR 72  
LAWRENCE LIVERMORE LABS

EMP PROTECTION FOR EMERGENCY OPERATING CENTERS                    , JUL 72  
DOD

CLARK, D.B.                    \*JOHNSTON, J.A.  
EMP PROTECTIVE SYSTEMS                    , NOV 71  
DOD

CLARK, D.B.                    \*JOHNSTON, J.A.  
EMP PROTECTIVE SYSTEMS                    , JUL 72  
DOD

TASCA, D.M.                    \*STOKEN, S.J.  
EMP RESPONSE : DAMAGE MODELLING OF DIODES, JUNCTION FIELD EFFECT                    ,  
TRANSISTOR DAMAGE TESTING AND SEMICONDUCTOR DEVICE FAILURE ANALYSIS                    , DEC 75  
GENERAL ELECTRIC



VINCENT, M.C. • CURTIS, M.L.  
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COMPLING VOLUME I, FINAL REPORT • JUL 75  
BOEING

MONROE, M.L. •  
EMP SHIELDING EFFECTIVENESS AND MIL STD. 295  
HARRY DIAMOND LABS • JUL 73

TASCA, D.M. • PEDEN, J.C.  
EMP SURGE SUPPRESSION CONNECTORS UTILIZING METAL OXIDE VARISTORS  
GENERAL ELECTRIC • DEC 73

TASCA, D.M. • PEDEN, J.C.  
EMP SURGE SUPPRESSION CONNECTORS UTILIZING METAL OXIDE VARISTORS  
HARRY DIAMOND LABS • AUG 74

JENKINS, C.R. • DUNGIN, D.L.  
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IEEE TRANSACTIONS ON NUCLEAR SCIENCE • DEC 75

ALEXANDER, D.R. ET. •  
EMP SUSCEPTIBILITY OF SEMICONDUCTOR COMPONENTS  
BDM CORP • SEP 74

JENKINS, C.R. • DUNGIN, D.L.  
EMP SUSCEPTIBILITY OF INTEGRATED CIRCUITS  
BDM CORP • JUL 75

BRIDGES, J.E. • EMBERSON, M.C.  
EMP TEST PROCEDURES (SELECTED ELECTRONIC PARTS)  
IIT RESEARCH INSTITUTE • AUG 74

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EMP THREAT AND PROTECTIVE MEASURES • AUG 70  
DOD

CLARK, O.W. •  
EMP TRANSIENT PROTECTION  
LAWRENCE LIVERMORE LAB •

CLARK, D. M. •  
EMP TRANSIENT SUPPRESSION  
LAWRENCE LIVERMORE LABS • AUG 74

DURGIN, D.L. • GAGE, R.P., ET. AL.  
EMP UPSET HARDENING GUIDELINES • DEC 72  
ROEING/ROM CORP

TASCA, D.W.  
ENERGY-TIME DEPENDENCE OF SECOND BREAKDOWN IN SEMICONDUCTORS FOR  
SUBMICROSECOND ELECTRICAL PULSES • OCT 67  
GENERAL ELECTRIC

PERALLA, R.A. • EZELL, T.F.  
ENGINEERING DESIGN GUIDELINES FOR EMP HARDENING OF NAVAL MISSILES  
AND AIRPLANES • DEC 73  
NOL

WHITSON, A.-.  
ENGINEERING TECHNIQUES FOR ELECTROMAGNETIC PULSE HARDNESS TESTING  
STANFORD RESEARCH INSTITUTE • SEP 74

WUNSCH, D.C.  
ESTIMATES OF SEMICONDUCTION FAILURE DUE TO MULTIPLE VOLTAGE PULSES  
BOM CORP • NOV 68

VANOPDOORP, C.  
EVALUATION OF DOPING PROFILES FROM CAPACITIVE MEASUREMENTS  
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RAYMOND, J.P. • KREMS, M.G.  
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PROGRAM-FINAL REPORT  
NORTHROP CORPORATE LABS/HARRY DIAMOND LAB • OCT 72

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EXEMPT A DIGITAL COMPUTER EXECUTIVE PROGRAM FOR SYSTEMS ANALYSIS  
USER'S GUIDE • NOV 74  
ROEING

NICOLLIAN, E.T., ET. •  
EXPEDIENT METHOD OF OBTAINING INTERFACE STATE PROPERTIES FROM MIS  
CONDUCTANCE MEASUREMENTS • 67  
SOLID STATE ELECTRONICS

BROWN, G., ET. AL. •  
EXPERIMENTAL DAMAGE CONSTANT SUMMARY • SEP 74  
ROM CORP

- EXPERIMENTAL DATA REPORT FOR TECHNICAL DIRECTIVE 4-23  
ROEING , APR 75
- EXPERIMENTAL DATA REPORT FOR TECHNICAL DIRECTIVE 4-23  
HOEING , APR 75
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IN X-BAND ON ELECTRONIC COMPONENTS , JUL 69  
HARRY DIAMOND LABS
- LENNOX, C.P.  
EXPERIMENTAL RESULTS OF TESTING RESISTORS UNDER PULSE CONDITIONS  
LAWRENCE LIVERMORE LABS , NOV 67
- LENNOX, C. T.  
EXPERIMENTAL RESULTS OF TESTING RESISTORS UNDER PULSE CONDITIONS  
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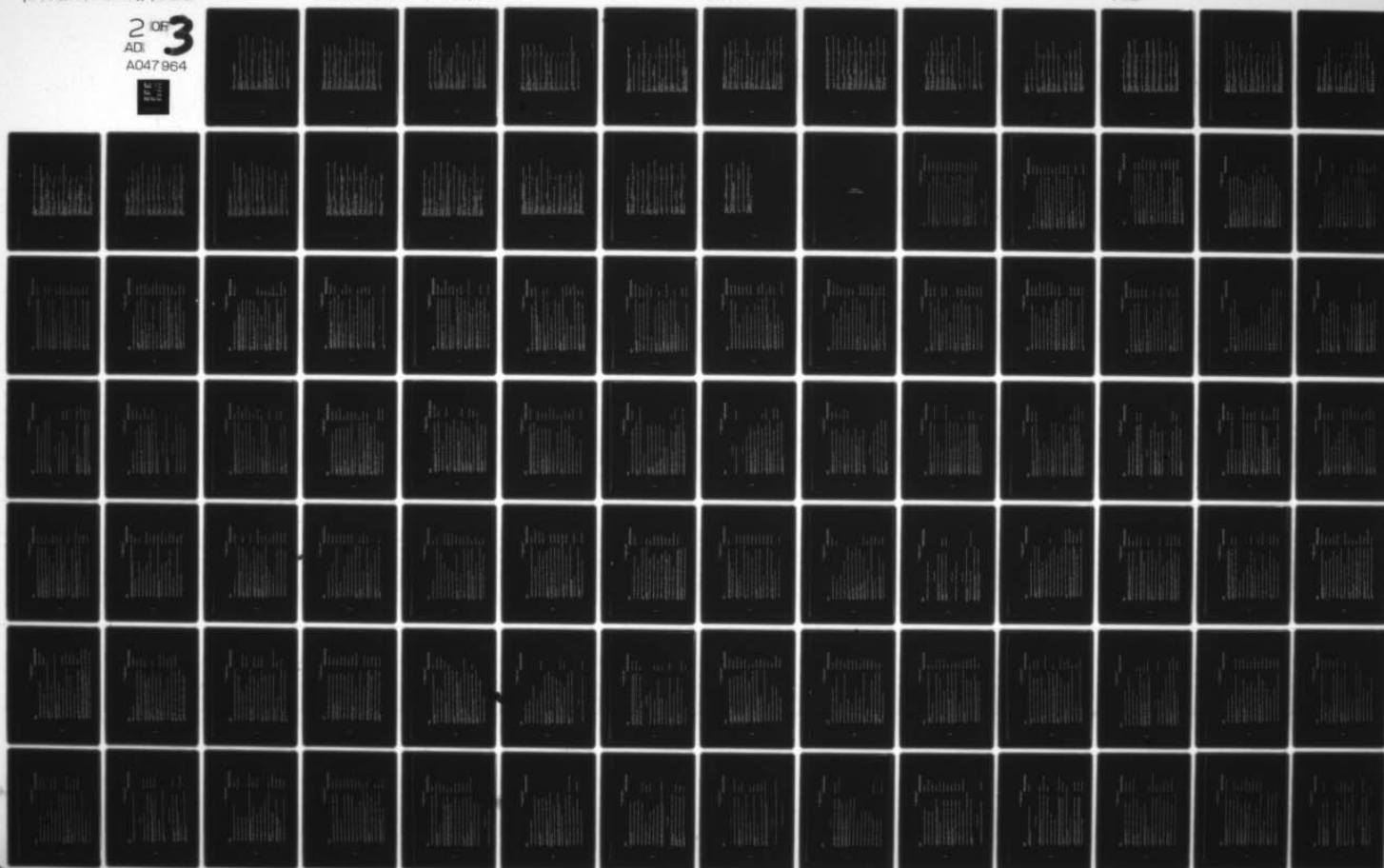
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WUNSCH, D.C.  
 COLLIER, W.O.  
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 SEMICONDUCTOR DAMAGE PROGRAM , AUG 69

PRELIMINARY REPORT-SEMICONDUCTOR DAMAGE STUDY  
 HDM CORP , AUG 68

PRELIMINARY REPORT II-SEMICONDUCTOR DAMAGE STUDY  
RDM CORP • NOV 68

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RDM CORP • DEC 68

BRIDGES, J.E. • NANDA, V.P., ET. AL.  
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IIT RESEARCH INSTITUTE • JAN 75

JAMES, K.A. • SMITH, L.D.  
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ROCKWELL INTERNATIONAL ELECTRONICS RESEA. • NOV 73

JENKINS, C.R. • ALEXANDER, D.R., ET.  
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BDM CORP • APR 75

REICH, R. •  
PROTECTION OF SEMICONDUCTOR DEVICES, CIRCUITS AND EQUIPMENT  
FROM VOLTAGE TRANSIENTS  
IEEE PROCEEDINGS • AUG 67

VANDRE, R.J. •  
PULSED-POWER BURNOUT OF INTEGRATED CIRCUITS  
THE AEROSPACE CORPORATION • AUG 72

PULSED POWER BURNOUT OF INTEGRATED CIRCUITS

PULSED VOLTAGE FAILURE LEVELS OF CAPACITORS GENERAL TEST PLAN  
GENERAL ELECTRIC • AUG 75

GUCCIONE, S. A. •  
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JOHANNESEN, J.C., ET.  
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ROING •

TASCA, D.M.  
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BOEING , FEB 75

TASCA, D.M.  
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BOEING , APR 75

TASCA, D.M.  
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GENERAL ELECTRIC , JUL 70

SMITH, J.S.  
PULSE POWER TESTING OF MICROCIRCUITS , OCT 71  
RADC

SMITH, J.S.  
PULSE POWER TESTING OF MICROCIRCUITS , JAN 71  
RADC

SMITH, J.S.  
PULSE POWER TESTING OF MICROCIRCUITS , OCT 71  
RADC

R:D CONTRACT STATUS REPORT FOR EVALUATION OF ELECTROEXPLOSIVE DEVICE  
(EED) RESPONSE TO ELECTROMAGNETIC RADIATION (EMR)  
LASL , AUG 72

RADC SERIES IN RELIABILITY VOLS. 3005



BERNSTEIN, V.J.  
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THE AEROSPACE CORP.  
DEC 75

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RADIATION EFFECTS IN MICROWAVE BIPOLAR TRANSISTORS

SOUTHWARD, T.D.  
RADIATION EFFECTS ON GALLIUM ARSENIDE DEVICES AND SCHOTTKY DIODES  
AFWL  
AJG 68

KLARS, P.J.  
RADIATION HARDENED AVIONICS GAIN INTEREST  
AMST  
SEP 69

CARR, E.A.  
RADIATION INDUCED SECOND BREAKDOWN  
HUGHES  
JUL 70

WHITTAKER, J.  
RADIO FREQUENCY NOISE PRODUCED BY HIGH INTENSITY FLASH X-RAY  
FACILITIES  
HARRY DIAMOND LABS  
MAY 70

ALEXANDER, D.M., ET AL.  
RECOMMENDED COMPONENT/SUBSYSTEM RESEARCH PROGRAM BRIEFING  
BDM CORP  
APR 75

SCHWARZ, J.J.  
RECOMMENDED INTERNAL COUPLING ANALYSIS TECHNIQUES FOR THE B-52G EMP  
TEST PROGRAM  
BDM CORP  
MAR 71

SCOTT, W.R.  
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REPORT  
NASA  
APR 75

GADHERY, R.E.  
REPORT NUMBER TPO 002 FEASIBILITY STUDY INTO THE USE OF  
TRANSISTORS FOR EMP SUPPRESSION  
GENERAL SEMICONDUCTOR INDUSTRIES

AZAREWICZ, JOSEPH L.,  
RESEARCH ON THE PHYSICS OF TRANSIENT RADIATION EFFECTS  
HARRY DIAMOND LABS , FEB 72

IRVIN, J.C.,  
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BELL SYSTEM TECHNICAL JOURNAL , MAR 62

SIZE, S.M.,  
IRVIN, J.C.,  
RESISTIVITY, MOBILITY AND IMPURITY LEVELS IN GEAS. GE AND SI AT  
300 DEG. K  
SOLID STATE ELECTRONICS, PERGAMON PRESS , 68

RESISTOR MODELING PROGRAM--FINAL REPORT , JUN 70  
RDM CORP

VAULT, W.L.,  
RESPONSE OF INTEGRATED CIRCUITS TO A SIMULATED IEMP ENVIRONMENT  
HARRY DIAMOND LABS , OCT 73

ALEXANDER, D.J.,  
REVIEW OF BDM EMP COMPONENT TEST PROGRAMS , OCT 73  
BDM CORP

DENHOLM, A. S., ET. ,  
REVIEW OF DIELECTRICS AND SWITCHING , FEB 73  
AFWL

ALMAD, K.,  
RF BURNOUT IN X-RAND SCHOTTKY MIXERS  
INST. OF PHYSICS, U. OF ISLAMABAD, PAKIS, AUG 71

HART, A.H.,  
RF FAILURE PREDICTION FOR MOS 4001 AND 4011 INTEGRATED CIRCUITS -  
WORKING PAPER  
NELC , JAN 76

EMERSON, W.C.,  
ROUGH DRAFT-EMP PREFERRED TEST PROCEDURES (SELECTED ELECTRONIC  
PARTS)  
IIT RESEARCH INSTITUTE , NOV 72

HART, A.E., ET. AL. ,  
R.F. FAILURE MECHANISMS RELATED TO MICROELECTRONICS PROCESS CONTROL  
NAVAL ELECTRONICS LAB , DEC 73

SAMSO STANDARD- ELECTRONIC PARTS, MATERIALS AND PROCESSES FOR SPACE  
AND MISSILE APPLICATIONS, STANDARD CONTROL PROGRAM FOR

SAMSO STANDARD- LIST OF PREFERRED PARTS FOR SPACE AND MISSILE SYSTEM  
JUL 75

CROSTHWAIT, D.L., ET.,  
SCANNING ELECTRON MICROSCOPE EXAMINATION OF METALLIZATION DEFECTS  
AFWL , APR 73

COHN, N.S.  
SECONDARY BREAKDOWN IN GERMANIUM SOLD-WUNDED DIODES  
NAVAL ORDINANCE LAB ,

REICH, B.  
SECONDARY BREAKDOWN THERMAL CHARACTERIZATION AND IMPROVEMENT OF  
SEMICONDUCTOR DEVICES  
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SUNSHINE, R.A.  
SECOND-BREAKDOWN PHENOMENA IN AVALANCHING SILICON ON SAPPHIRE DIODES  
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BUDENSTEIN, P.P., ET.  
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U.S. ARMY MISSILE COMMAND , APR 72

SMITH, W.B.  
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IEEE TRANSACTION ON ELECTRON DEVICES , AUG 73

CHENETTE, E.M.  
SECOND BREAKDOWN AND LOW FREQUENCY NOISE IN BIPOLAR JUNCTION  
TRANSISTORS  
BATELLE , JUN 75

PONTIUS, D.M., ET. A.  
SECOND BREAKDOWN IN THE PRESENCE OF INTENSE IONIZING RADIATION AND  
RELATED STUDIES  
AMBURN UNIVERSITY , JUN 73

SCHROEN, W.  
SECOND BREAKDOWN IN SIMPLIFIED TRANSISTOR STRUCTURES AND DIODES  
IEEE TRANSACTIONS , SEP 66

ASAKAWA, T. • TSUBOUCHI, N.  
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 IEEE TRANSACTIONS

PONTIUS, D.L. • SMITH, W.R., ET. AL.  
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 US ARMY MISSILE COMMAND • DEC 74

NIENHUIS, P.J. •  
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SUNSHINE, R.A. • LAMPERT, M.A.  
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SCHAFFT, H.A. •  
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 IEEE PROCEEDINGS

KALINOWSKI, J.J. • WELLS, T.G.  
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 SIMULATION • FEB 74  
 BDM CORP

SECTION II A MODEL TO PREDICT POWER FAILURE OF SEMICONDUCTOR DEVICES  
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SECTION II DISCRETE DAMAGE TESTS

SECTION VI DESIGN PRACTICES

SINCLAIR, P.E. •  
 SEMICONDUCTOR CIRCUIT FAILURE AND PROTECTION IMPLEMENTATION SCHEMES  
 LOCKHEED

SEMICONDUCTOR DAMAGE STUDY-PRELIMINARY REPORTS • 68  
 BDM CORP

MUNSCH, D.C.  
SEMICONDUCTOR DAMAGE STUDY  
RDM CORP

SEMICONDUCTOR DAMAGE CONSTANTS

SEMICONDUCTOR DAMAGE TEST RESULTS FOR SANDIA DEVICES UZ110, UZ130,  
UZ9679  
RDM CORP

MAR 69

ALEXANDER, D.R.  
SEMICONDUCTOR DATA REDUCTION ALGORITHM CONTENTS  
ROEING/RDM CORP

JUL 75

BROWN, W.D.  
SEMICONDUCTOR DEVICE DEGRADATION BY HIGH CURRENT PULSES  
SANDIA LABORATORIES

JUL 72

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SEMICONDUCTOR DEVICE DEGRADATION BY HIGH AMPLITUDE CURRENT PULSES  
SANDIA LABS

JUL 72

MUNSCH, D.C.  
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AFSWC

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QUARTERLY REPORT  
NATIONAL BUREAU OF STANDARDS

SEP 74

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DEC 74

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SEP 74

SCHAFFT, M.A., ED.  
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PATTERNS FOR INTEGRATED CIRCUITS  
JAN 76



SEMICONDUCTOR VULNERABILITY PHASE I REPORT  
 BDM CORP  
 • NOV 69

MUNSCH, D.C.  
 SEMICONDUCTOR VULNERABILITY PHASE II REPORT THEORETICAL ESTIMATES  
 FAILURE LEVELS OF SELECTED SEMICONDUCTOR DIODES AND TRANSISTORS  
 BDM CORP  
 • DEC 69

SINGLEARY, J.B.  
 SEMICONDUCTOR VULNERABILITY PHASE III REPORT EXPERIMENTAL THRESHOLD  
 FAILURE LEVELS OF SELECTED DIODES AND TRANSISTORS  
 BDM CORP  
 • AUG 70

SEMICONDUCTOR VULNERABILITY-PHASE I REPORT  
 BDM CORP  
 • NOV 69

MUNSCH, D.C. ET. AL.  
 SEMICONDUCTOR VULNERABILITY-PHASE II REPORT-THEORETICAL ESTIMATES  
 OF FAILURE LEVELS OF SELECTED SEMICONDUCTOR DIODES AND TRANSISTORS  
 BDM CORP  
 • DEC 69

MUNSCH, D.C. ET. AL.  
 SEMICONDUCTOR VULNERABILITY VOL I THEORETICAL ESTIMATES OF FAILURE  
 LEVELS OF SELECTED SEMICONDUCTOR DIODES AND TRANSISTORS-PHASE II  
 AFWL  
 • JUL 73

SINGLEARY, J.B. ET.  
 SEMICONDUCTOR VULNERABILITY VOL II - EXPERIMENTAL THRESHOLD FAILURE  
 LEVELS OF SELECTED DIODES AND TRANSISTORS - PHASE III  
 AFWL  
 • JUL 73

DOYLE, O.  
 SEMICONDUCTOR MODUNIT- HOW'S TO BLAME FOR FAILURES  
 ELECTRONICS  
 • 18 AUG 69

MUNSCH, D.C.  
 SEMICONDUCTOR AND NON-SEMICONDUCTOR DAMAGE STUDY PERSHING DEVICES  
 BDM CORP  
 • APR 69

WILEY, T.D.  
 SERIES RESISTANCE EFFECTS IN SEMICONDUCTOR C V PROFILING  
 IEEE TRANSACTIONS ON ELECTRON DEVICES  
 • MAY 75

VANCE, E.F.  
SHIELDING EFFECTIVENESS OF THE LIQUID TIGHT FLEXIBLE CONDUIT FROM  
TRANSIENT TESTS  
STANFORD RESEARCH INSTITUTE \* MAY 72

ROWN, G.L.  
SHIELDING EVALUATION OF BRAIDED CABLE SHEATHS AND MULTICONDUCTOR  
CABLES USING PULSE TEST METHODS  
LAWRENCE LIVERMORE LABS \* AUG 74

SHORT COURSE IN NUCLEAR WEAPON EFFECTS AND SURVIVABILITY OF  
AEROSPACE SYSTEMS  
USAF AIR UNIVERSITY \* NOV 73

FITZGERALD, D.J.  
SHORT PULSE EFFECTS IN SEMICONDUCTOR DIODES  
IKOR \* MAY 72

LUNN, T.C.  
SHORT PULSE WIDTH FAILURE LEVEL CHARACTERIZATION FOR THE 2N3821  
JUNCTION FIELD EFFECT TRANSISTOR  
LAWRENCE LIVERMORE LAB \*

FRANZ, I.  
LANG HEINRICH, M.  
SILICON NITRIDE AS A MASK IN PHOSPHOROUS DIFFUSION  
SOLID STATE ELECTRONICS \* 69

JOHN, H.F.  
SILICON POWER DEVICE MATERIALS PROBLEMS  
IEEE PROCEEDINGS \* AUG 67

STURM, O.  
SILICON POWER ZENER TRANSIENT SUPPRESSORS  
IEEE PROCEEDINGS-LETTERS \* AUG 67

SIMPLIFICATIONS IN THE STUDY OF GROUNDED-SHIELD, "BALANCED" TWIN-  
LEAD CABLES  
SIDNEY FRANKEL \* JUL 71

ROULSTON, D.J.  
SIMPLIFIED COMPUTER AIDED ANALYSIS OF DOUBLE DIFFUSED TRANSISTORS  
INCLUDING TWO-DIMENSIONAL HIGH LEVEL EFFECTS  
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BDM CORP.  
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GREENBAUM, J.H.  
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PERFORMANCE PREDICTION  
NOV 72  
SIMPLIFIED SUBSYSTEM INTERFACE MODELS  
RDM CORP.  
SCHWARZ, J.J.  
SIMPLIFIED SUBSYSTEM INTERFACE MODEL  
BDM CORP. DEC 74  
SAMOYLOV, L.K.  
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AFSC FOREIGN TECHNOLOGY DIV. AB  
CARTER, L.M.  
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TRUMBORE, F.A.  
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FY-72  
U.S. NAVAL WEAPONS LAB SEP 72  
SOLID STATE COMPONENT HF SUSCEPTIBILITY PROGRAM-PROGRESS REPORT FY73  
NAVAL WEAPONS LAB NOV 73  
BROWN, G.L.  
SOME ASPECTS OF EMP HARDNESS ASSURANCE  
RESOURCE ENGINEERING : PLANNING

JENKINS, C.R.  
 SOME COMMENTS ON THE MODELS USED TO PREDICT SEMICONDUCTOR DAMAGE  
 CONSTANTS  
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MARTIN, L.C.  
 SOME HANDBOOK REFERENCES AND A SUMMARY FOR EMP ENGINEERING AND  
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BERGMANN, F.  
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SOLN, J.Z.  
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 HARRY DIAMOND LABS

SPARK GAP SIMULATES A-BOMB EMP  
 ELECTRO-TECHNOLOGY

MANUS, D.J., ET. AL.  
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 ENVIRONMENTS  
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LINDSTEAD, P.D., \*SURLY, R.J.  
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 AND TIME ON BIPOLAR DEVICES.

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 SUBNANOSECOND RISE TIME MULTIKILOVOLT PULSE GENERATOR  
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 SUBSYSTEM TEST METHODOLOGY FOR THE AFWL DIRECT DRIVE LABORATORY  
 ROEING/HDM CORP , FEB 75

GREAVES, L.J., \*SCHWARZ, J.J., ET. AL  
 SUBSYSTEM TEST METHODOLOGY FOR THE AFWL DIRECT DRIVE LABORATORY  
 BOEING/HDM CORP , OCT 75

COOKE, J.L., \*DUNCAN, D.E., ET. AL  
 SUPERSAP 2 USER'S MANUAL  
 ROEING/HDM CORP , OCT 74

DURGIN, D.L.  
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 RDM CORP , NOV 72

KESSE, H  
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 SURFACE ASPECTS OF THE THERMAL DEGRADATION OF GE-45 P-N JUNCTION  
 LASER AND TUNNEL DIODES  
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BLOOM, G.E., \*DUNCAN, L.W.  
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 FROM SYSTEMS GENERATED ELECTRO MAGNETIC PULSE EFFECTS  
 AFWL , JUL 75



SCATURRO, J.  
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CLARKSON COLLEGE OF TECHNOLOGY  
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COHN, N.S.  
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NAVAL ORDINANCE LAB.  
• MAY 73

PEDEN, J.C.  
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JUNCTION IN A PULSED ELECTRICAL AND PULSED RADIATION ENVIRONMENT  
JAN 70

MARSHAK, A.H.  
SYNTHESIS OF GENERAL IMPURITY PROFILES USING A TWO-STEP  
DIFFUSION PROCESS  
IEEE TRANSACTIONS ON ELECTRON DEVICES • SEP 72

TECHNICAL NOTE 3 MODIFIED DISCRETE SEMICONDUCTOR FIRST LEVEL SCREEN  
BDM CORP  
• FEB 75

SEELY, G.  
TECHNIQUES FOR MEASUREMENT OF THE VPD SPECTRUM: A TRADE STUDY  
EGIG  
• DEC 72

BRUNCKE, W.C.  
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IONIZING RADIATION  
NOV 74

LUNN, T.C.  
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SUSCEPTIBILITY  
MCDONNELL DOUGLAS  
• SEP 73

GARTNER, W.W.  
TEMPERATURE DEPENDENCE OF JUNCTION TRANSISTOR PARAMETERS  
IRE PROCEEDING  
•

JAMES, K.A.  
TEST PLAN FOR MOS DEVICE FAILURE  
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JAN 73

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ROEING  
• NOV 73

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CONNECTOR SHELLS WITH FINGERS  
NORTH AMERICAN ROCKWELL
- CARR, E.A.  
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INTEGRATED CIRCUITS  
HUGHES
- TASCA, D.M. ET. AL.  
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DEGRADATION DUE TO HIGH POWER ELECTRICAL TRANSIENTS  
GENERAL ELECTRIC
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DIODES AND TRANSISTORS  
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- STEFFE, W.  
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PERSKY, G.  
THERMIONIC SATURATION OF DIFFUSION CURRENTS IN TRANSISTORS  
SOLID STATE ELECTRONICS , 72

WILSON, P.R.  
THE BUILT-IN VOLTAGE OF DIFFUSED P-N JUNCTIONS  
SOLID STATE ELECTRONICS , 69

VAULT, W.L.  
THE DAMAGE SUSCEPTIBILITY OF INTEGRATED CIRCUITS TO A SIMULATED IEMP  
TRANSIENT  
HARRY DIAMOND LABS ,

DUNN, P.J.  
THE DEGRADATION OF MOS TRANSISTORS RESULTING FROM JUNCTION AVALANCHE  
BREAKDOWN  
MICROELECTRONICS AND RELIABILITY , 72

RABURN, W.D., ET. AL.  
THE DETERMINATION OF SEMICONDUCTOR JUNCTION VULNERABILITY TO SECOND  
BREAKDOWN BY LOW ENERGY ELECTRICAL MEASUREMENTS  
UNIV. OF ALA. , JUL 73

THE EFFECTS OF PULSED GAMMA RADIATION ON ELECTRONIC COMPONENTS

MESSIER, M.A.  
THE EFFECT OF GROUND REFLECTION ON OBSERVED EMP WAVEFORMS  
MISSION RESEARCH , SEP 74

DENDRICK, F.J.  
THE LLL TRANSIENT ELECTROMAGNETICS-MEASUREMENT FACILITY  
LAWRENCE LIVERMORE LABS , DEC 75

VANCE, E.F.  
THE MODIFIED SIEGE 1.2 PULSE DRIVER  
AFWL , APR 71

DISTEFANO, T.H.  
THE PHYSICS OF INTERFACE INTERACTIONS RELATED TO RELIABILITY OF  
FUTURE ELECTRONIC DEVICES  
AIR FORCE CAMBRIDGE RESEARCH LABS , JUL 73

HOWELL, C.  
THE REAL CULPRIT IN DIODE FAILURE  
MICROWAVES , ANAND, V. , AUG 70

NEVE, N.F. B. ,SULWAY, D.V., ET AL  
THE SCANNING ELECTRON MICROSCOPE AS A MEANS OF INVESTIGATING  
"SECOND BREAKDOWN" AND SIMILAR PHENOMENA , AUG 66  
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RADIATION , JUN 73  
U.S. NAVAL WEAPONS LAB

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CLEARINGHOUSE FOR FEDERAL SCIENTIFIC : T, MAR 70

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CONDUCTED EMP  
GTE SYLVANIA ,

TAGAKI, K. ,MANO, K.  
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IEEE TRANSACTIONS

MORTENSON, K.E.  
TRANSISTOR JUNCTION TEMPERATURE AS A FUNCTION OF TIME  
PROCEEDINGS OF THE IRE , APR 57

BOOK, R.S. ,PEDEN, J.C.  
TRENDS IN POWER HANDLING EQUIPMENT , NOV 69  
GENERAL ELECTRIC

MCCOSKEY, R.E.  
TREE MODELING REQUIREMENTS, DNA COMPONENTS RESPONSE AND  
PREDICTION WORKING GROUP MEETING MATERIAL , JAN 74  
DNA





JENKINS, C.R. , MYERS, J.A.  
WORK ORDER 2-14 INTEGRATED CIRCUITS TEST PROGRAM-FINAL REPORT  
BDM CORP , JUL 73

SINGH TYAGI, M. ,  
ZENER AND AVALANCHE BREAKDOWN IN SILICON ALLOYED P-N JUNCTIONS  
-I- ANALYSIS OF REVERSE CHARACTERISTICS  
SOLID STATE ELECTRONICS, PERGAMON PRESS , 68

1966 IEEE ELECTROMAGNETIC COMPATIBILITY SYMPOSIUM RECORD  
IEEE , JUL 68

1972 THIRTEENTH SCINTILLATION AND SEMICONDUCTION COUNTER SYMPOSIUM  
MAR 72

HINZ, D.J. , JETER, T.R., ET. AL.  
MEMORANDUM REPORT N.2200 GENERIC ELECTRONIC TARGET< DESIGN  
/DEVELOPMENT  
BALLISTIC RESEARCH LABS , JUN 72

APPENDIX C  
LISTING BY SUBJECT

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*  
DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

B-1 EMP SUBSYSTEM ASSESSMENT DATA UHF RADIO AN/ARC-109	0224-13022-8
COMPARISON OF ANTENNA-RELATED PREDICTIVE MODELS WITH B-1 SCALE MODEL MEASUREMENTS IN ALECS	0224-13052-2
F-111/ARES DETAIL TEST PLAN, VOLUME V PHASE II INTEGRATED TEST PLAN (FINAL)	0224-13008-5
DTP B-1 SCALE MODEL ALECS, SEC.6 FINAL DETAILED TEST PLAN	0224-13006-1
B-1 EMP RESPONSE FOR INADVERTENT PENETRATION COMPLYING FINAL REPORT (DRAFT)	0224-13064-1
F-111/ARES TEST SUPPORT, VOLUME I DRAFT FINAL REPORT	0224-13059-1
B-52 G/AGM-28A/VPO EXPERIMENT TECHNICAL REPORT VOLUME II DRAFT FINAL REPORT	0224-13069-2
VERTICALLY POLARIZED DIPOLE (VPO) B-52/G/AGM-28A TECHNICAL REPORT VOLUME I (DRAFT)	0224-13069-1
EXTERNAL COMPLYING OF AN ELECTROMAGNETIC PULSE TO THE B-1 AIRCRAFT	0224-13060-1
EMP RESPONSE OF THE B-1 AIRCRAFT FOR INADVERTENT PENETRATION COMPLYING VOLUME I, FINAL REPORT	0224-13064-1
FINAL REPORT ON THE PRELIMINARY B-1 EVALUATION EMP RELATED AIRCRAFT C/J-310/201 CHARACTERISTICS VOLUME II	
FINAL REPORT EC-130 PRETEST ANALYSIS VOLUME II SYSTEMS DESCRIPTION	BOM/A 12-71-41
AARNCP LOW LEVEL TEST PLAN	0226-10109-1

\*\*\*\*\*ANALYSIS

DIFFUSED JUNCTION DEPLETION LAYER CALCULATIONS

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

TITLE  
\*\*\*\*\*

ASAP-1 FINAL REPORT 0224-12013-1

TEST REPORT FOR EC-135C INTERNAL COUPLING MEASUREMENTS 0180-17726-1

ENGINEERING DESIGN GUIDELINES FOR EMP HARDENING OF NAVAL MISSILES AND AIRPLANES AMRC-R-17

MATHEMATICAL MODELS FOR THE RESPONSE OF AEROSPACE SYSTEMS TO HIGH FREQUENCY ELECTROMAGNETIC ENVIRONMENTS SLA-74-0131

IDENTIFICATION FRIEND OR FOE/AIR TRAFFIC CONTROL (IFF/ATC) SYSTEM AN/APX-72 SYSTEM DESCRIPTION CDRL A017

AN/ART-47 UHF RADIO TRANSMITTER SET SYSTEM DESCRIPTION CDRLA017

AIRBORNE COMMAND POST AARMCX ELECTRONIC SYSTEM DETAILED PROGRAM PLAN CDRL A018 INTERIM REPORT

B-1 SCALE MODEL PRELIMINARY TEST PLAN FOR MEASUREMENT OF WEAPONS BAY AND WHEEL WELL COUPLING (FINAL) 0224-13038-1

DETAILED TEST PLAN B-1 SCALE MODEL/ALECS TEST PROGRAM SECTION 5 0224-13006-1

F-111/ARES DETAIL TEST PLAN VOL.222, EXTERNAL COUPLING AND DELIBERATE ANTENNA EXPERIMENTS D224-13008-3

POST EXPERIMENT SUMMARY OF B-1 SCALE MODEL MEASUREMENTS FOR T03-19 INADVERTENT PENETRATIONS

SRAM/ARES DETAIL TEST PLAN 0224-13008-4

B-1 ALECS POST EXPERIMENT SUMMARY FOR TECHNICAL DIRECTIVE 3-14 MEASUREMENTS

B-1 EMP SUBSYSTEM ASSESSMENT DATA, IFF AN/APX-64 0224-13022-10

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

\*\*\*\*\*AIRCRAFT

EMP CHARACTERIZATION OF SPRINT AIRCRAFT COMPONENTS-FINAL REPORT	CREG 69-2
MEASUREMENTS AND ANALYSIS OF LIGHTNING INDUCED VOLTAGE IN AIRCRAFT ELECTRICAL CIRCUITS	HVL-69-161
INTERIM NOTES B-52 EMP TEST PROGRAM NOTE 5 GENERAL PROCEDURES FOR SUBSYSTEM EMP TESTING	HDM/A-121-70-PN
MISSILE AND AIRCRAFT COMPONENT VULNERABILITY TO EMP	SC-1M-70-902
RECOMMENDED INTERNAL COUPLING ANALYSIS TECHNIQUES FOR THE B-52S EMP TEST PROGRAM	HDM/A-66-71-TH
AERONAUTICAL SYSTEMS EMP TECHNOLOGY REVIEW	D224-10004-1
ELECTROMAGNETIC PULSE HANDBOOK FOR MISSILES AND AIRCRAFT IN FLIGHT	
DESIGN GUIDELINES FOR EMP HARDENING OF AERONAUTICAL SYSTEMS (DRAFT)	C72-451/201
B-52/VPD GENERAL TEST PLAN	D224-10000-1
AEROSPACE VEHICLE EMI TRANSIENT TEST TECHNIQUES	AFAL-TR-72-102
FIELD AND LABORATORY TESTING IDENTIFICATION AND SUMMARY AERONAUTICAL SYSTEMS EMP INTEGRATED TEST PROGRAM ROUGH DRAFT	D224-10012-1
DESIGN GUIDELINES FOR EMP HARDENING OF AERONAUTICAL SYSTEMS	AFWL-TH-73-117
SHORT COURSE IN NUCLEAR WEAPON EFFECTS AND SURVIVABILITY OF AEROSPACE SYSTEMS	



DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

FOURIER ANALYSIS OF EMPIRICAL DATA. VMSU ENGINEERING EXPERIMENT  
STATION REPORT NO.14

ANALYSIS OF THE IMPURITY ATOM DISTRIBUTION NEAR THE DIFFUSION MASK  
FOR A PLANAR P-N JUNCTION

ANALYSIS OF THE TEMPERATURE RISE IN PIN DIODES CAUSED BY MICROWAVE  
PULSE DISSIPATION

THE SCANNING ELECTRON MICROSCOPE AS A MEANS OF INVESTIGATING  
"SECOND BREAKDOWN" AND SIMILAR PHENOMENA

A CHARACTERIZATION TECHNIQUE FOR SECOND BREAKDOWN IN GE  
ALLOYED JUNCTION TRANSISTORS

PHYSICAL INVESTIGATION OF THE MESOPLASMA IN SILICON

CALCULATIONS OF CUTOFF FREQUENCY, BREAKDOWN VOLTAGE, AND CAPACITANCE  
FOR DIFFUSED JUNCTIONS IN THIN EPITAXIAL SILICON LAYERS

EXPERIMENTAL RESULTS OF TESTING RESISTORS UNDER PULSE CONDITIONS PEM-6

EXPERIMENTAL RESULTS OF TESTING RESISTORS UNDER PULSE CONDITIONS

AN EXAMPLE OF THE APPLICATION OF ECAP TO CIRCUIT ANALYSIS OF AN  
A-C POWER SUPPLY MG-TR-67-16

AN ACCURATE NUMERICAL STEADY STATE ONE DIMENSIONAL SOLUTION OF THE  
P-N JUNCTION

AN ACCURATE NUMERICAL ONE-DIMENSIONAL SOLUTION OF THE P-N JUNCTION  
UNDER ARBITRARY TRANSIENT CONDITIONS

OUTLINE FOR SYSTEM VULNERABILITY/SURVIVABILITY ANALYSIS

SEMICONDUCTOR DAMAGE STUDY--PRELIMINARY REPORTS

DVA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

PRELIMINARY REPORT-SEMICONDUCTOR DAMAGE STUDY

PRELIMINARY REPORT II-SEMICONDUCTOR DAMAGE STUDY

1968 IEEE ELECTROMAGNETIC COMPATIBILITY SYMPOSIUM RECORD

IEEE 58C12-EMC

PRELIMINARY REPORT SEMICONDUCTOR DAMAGE STUDY (REVISED)

SPREADING RESISTANCE CORRECTION FACTORS

DEPLETION LAYER AND CAPACITANCE CALCULATIONS FOR GAUSSIAN DIFFUSED  
JUNCTIONS

DEPLETION LAYER CALCULATIONS FOR EPOCH FUNCTION DIFFUSED JUNCTIONS

SEMICONDUCTOR VULNERABILITY PHASE I REPORT

HDM/A-37-69-4

A MODEL TO PREDICT PULSE POWER FAILURE OF SEMICONDUCTOR DEVICES

3DM FINAL REPORT-VOLUME I SEMICONDUCTOR AND NONSEMICONDUCTOR DAMAGE  
STUDY

HDM-375-69-F-0158

SEMICONDUCTOR AND NON-SEMICONDUCTOR DAMAGE STUDY PERSHING DEVICES

HDM-375-69-F-0168

DETERMINATION OF THRESHOLD FAILURE LEVELS DUE TO HIGH VOLTAGE  
TRANSIENTS FOR A 6A 53933 TRANSISTOR

HDM/A-27-69-4

FRANKLIN INSTITUTE REPORT ON FED PULSE TESTING

F-C2540

SEMICONDUCTOR VULNERABILITY-PHASE I REPORT

HDM/A-37-69-4

ONA OVERSTRESS REVIEW  
SUBJECT INDEX

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

TITLE  
\*\*\*\*\*

HDM/A-42-69-M

SEMICONDUCTOR VULNERABILITY-PHASE II REPORT-THEORETICAL ESTIMATES  
OF FAILURE LEVELS OF SELECTED SEMICONDUCTOR DIODES AND TRANSISTORS

FORT BELVOIR SEMICONDUCTOR FAILURE PROGRAM REPORT

LASER TRIGGERED SWITCHING STUDY

AFWL-TR-69-B/

DAMAGE LEVEL EVALUATION OF SEMICONDUCTOR COMPONENTS USING ULTRA  
FAST RISETIME PULSER

RSE-IN-69-3

MODELS FOR THE PN DIODE AND THE NPN AND PNP TRANSISTOR FOR USE IN  
COMPUTER AIDED DESIGN AND ANALYSIS PROGRAMS

TRANSISTOR AND DIODE MODEL HANDBOOK

69-521-1

FINAL REPORT ON SEMICONDUCTOR DAMAGE STUDY PHASE II

NFM/S 66-70-1R

SEMICONDUCTOR VULNERABILITY PHASE III REPORT EXPERIMENTAL THRESHOLD  
FAILURE LEVELS OF SELECTED DIODES AND TRANSISTORS

HDM/A-75-70-1R

MINUTEMAN IPI RE-ENTRY SYSTEM-ALECS-5 PROGRAM PIECE PARTS TEST  
SUPPORTS-FINAL REPORT

70SD401

RESISTOR MODELING PROGRAM-FINAL REPORT

HDM/A-75-10-1R

USER'S MANUAL FOR THE NETWORK EMP DAMAGE ANALYSIS PROGRAM (NEDAP)

RG-TR-70-2

APPROACHES TO SYSTEM HARDENING

SSH-349

AN ANALYTICAL AND LOW-LEVEL TESTING APPROACH TO THE EMP SYSTEMS  
PROBLEM

SWV TR-70-7

SYNERGISTIC CONSIDERATIONS FOR THE SECOND BREAKDOWN OF A P-N  
JUNCTION IN A PULSED ELECTRICAL AND PULSED RADIATION ENVIRONMENT

MEMO 1457-55

ONA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

NET TRANSISTOR AND DIODE LIBRARY TAPE 4925

A COMPUTER AIDED ANALYSIS MODEL FOR THE JUNCTION FIELD EFFECT  
TRANSISTOR SC-DR-70-365

INTERIM REPORT RESPONSE OF A MULTICONDUCTOR CABLE TO EXCITATION AT  
AN OPEN BREAK IN THE SHIELD SC-CR-70-6152

INTERIM NOTES 3-52 EMP TEST PROGRAM NOTE 6 GENERAL PROCEDURES FOR  
SUBSYSTEM EMP TESTING BDM/A-121-70-PN

STATISTICAL COMPONENT DAMAGE STUDY

HG-TR-71-1

FINAL SUMMARY REPORT ON SEMICONDUCTOR DAMAGE STUDY-PHASE II

BDM/A-84-70-TR

CABLE SYSTEM ANALYSIS

AFWL-TR-71-100 VOL I

METALLIZATION BURNDOUT RESEARCH AT THE UNITED STATES AIR FORCE  
ACADEMY AFWL-TR-71-4

RECOMMENDED INTERNAL COUPLING ANALYSIS TECHNIQUES FOR THE B-52S EMP  
TEST PROGRAM BDM/A-66-71-TR

INTERIM REPORT RESPONSE OF A MULTICONDUCTOR TRANSMISSION LINE TO  
EXCITATION BY AN ARBITRARY MONOCHROMATIC IMPRESSED FIELD ALONG THE LINE SC-CR-715076

FAILURE ANALYSIS OF DAMAGED 2N700 TRANSISTORS

NV/E-20/71

CIRCUS-2 A DIGITAL COMPUTER PROGRAM FOR TRANSIENT ANALYSIS OF  
ELECTRONIC CIRCUITS USER'S GUIDE 0070-1

SIMPLIFICATIONS IN THE STUDY OF GROUNDED-SHIELD, "BALANCED" TWIN-  
LEAD CABLES SC-CR-715110

IN-PLACE EMP CRITICAL CIRCUIT THRESHOLD ANALYSIS

02-19693-2

UNA OVERSTRESS REVIEW  
SUBJECT INDEX

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

TITLE  
\*\*\*\*\*

PULSE POWER TESTING OF MICROCIRCUITS

MADC-TR-71-54

AN ANALYTICAL EXPRESSION FOR THE MULTIPLICATION FACTOR M IN SEMICONDUCTORS WITH EQUAL IONIZATION COEFFICIENT

SIMPLIFIED COMPUTER AIDED ANALYSIS OF DOUBLE DIFFUSED TRANSISTORS INCLUDING TWO-DIMENSIONAL HIGH LEVEL EFFECTS

ITERATIVE SCHEME FOR COMPUTER SIMULATION OF SEMICONDUCTOR DEVICES

ADAPTATION OF THE P-N JUNCTION BJRNJOIT MODEL TO CIRCUIT ANALYSIS CODES

LUMPED MODEL ANALYSIS OF SEMICONDUCTOR DEVICES USING THE NET-2 CIRCUIT/SYSTEM ANALYSIS PROGRAM

RESEARCH ON THE PHYSICS OF TRANSIENT RADIATION EFFECTS

HDL-TR-060-3

SPECIAL PULSE TESTING OF THE D45A1 DETONATOR

F-C3081

A COMPARISON OF RF AND DC - INDUCED DAMAGE TO METAL-SEMICONDUCTOR JUNCTIONS

TR-2707

LIFE TESTS OF KEMET SOLID TANTALUM CHIP CAPACITORS AT HIGHLY ACCELERATED VOLTAGES

M72-10

HIGH VOLTAGE ARC INTERRUPTION STUDY

RADC-TR-72-40

FAILURE THRESHOLD AND RESISTANCE OF THE PROTECTED AND UNPROTECTED 2N2222 TRANSISTOR IN THE SHORT PULSE WIDTH REGIME

PEM-7

HIGH ENERGY PHYSICS ABSTRACTS AND TRANSLATIONS VOL. V

AFWL-IN-CW-01-19-72

FINAL REPORT ON THE EVALUATION OF SURGE PROTECTION DEVICES FOR EMP HARDENING APPLICATIONS

C72-712/201



DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*  
DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

DETERMINATION OF THRESHOLD FAILURE LEVELS DUE TO HIGH VOLTAGE  
TRANSIENTS FOR A GA 53933 TRANSISTOR BDM/A-27-69-W

MEASUREMENTS AND ANALYSIS OF LIGHTNING INDUCED VOLTAGE IN AIRCRAFT  
ELECTRICAL CIRCUITS HVL-64-161

JUNCTION CAPACITANCE AS A FUNCTION OF VOLTAGE FOR DIFFUSED P-N JUNCTIONS  
WITH EXPONENTIAL DOPING GRADIENTS

LIFE TESTS OF KEMET SOLID TANTALUM CHIP CAPACITORS AT HIGHLY  
ACCELERATED VOLTAGES M72-10

HIGH VOLTAGE ARC INTERRUPTION STUDY RADC-TR-72-40

LIGHTNING AND HIGH VOLTAGE SURGE PROTECTION FOR BALANCED DIGITAL  
TRANSMISSION DEVICES ECOM-4027

CONSTANT VOLTAGE DIODES ARE GETTING SHARPER

VOLTAGE CLAMPING LEVELS FOR SEVERAL "TRANSURB" TRANSIENT SUPPRESSION  
DEVICES PEM-33

PULSED VOLTAGE FAILURE LEVELS OF CAPACITORS GENERAL TEST PLAN 75SDS4241

BIPOLAR VOLTAGE PULSE DAMAGE EFFECTS ON TRANSISTORS AD 766-685

OVERVOLTAGE TRANSIENT STUDIES OF LEVEL SENSOR AMPLIFIER CKTS. RG-TR-71-5

DETERMINATION OF SEMICONDUCTOR FAILURE LEVELS DUE TO HIGH VOLTAGE  
TRANSIENTS

\*\*\*\*\*

3-1 EMP RESPONSE FOR INADVERTENT PENETRATION COMPLING FINAL REPORT U224-13064-1  
(DRAFT)

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*  
DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

SEMICONDUCTOR DEVICE DEGRADATION BY HIGH AMPLITUDE CURRENT PULSES	SC-RR-72-0515
INTEGRATED CIRCUIT ELECTRO MAGNETIC SUSCEPTIBILITY INVESTIGATION DEVELOPMENT PHASE REPORT	MDC D0690
SOLID STATE COMPONENTS RF SUSCEPTIBILITY PROGRAM-PROGRESS REPORT FY-72	FVR/VGPCHAC 35000/EMC
FINAL REPORT ON THE EVALUATION OF SURGE PROTECTION DEVICES FOR EMP HARDENING APPLICATION REVISION NO.1	C72-712/201
MULTICONDUCTOR CABLE MODELING	D224-10013-2
R&D CONTRACT STATUS REPORT FOR EVALUATION OF ELECTROEXPLOSIVE DEVICE (EED) RESPONSE TO ELECTROMAGNETIC RADIATION (EMR)	LA-5050-P4
INTERIM REPORT-DEVELOPMENT OF DATA BASE AND RELATED COMPUTER CODE	D224-12003-1
ROUGH DRAFT-EMP PREFERRED TEST PROCEDURES (SELECTED ELECTRONIC PARTS)	
ELECTROMAGNETIC PULSE ENVIRONMENT STUDIES VOLUME II LATE TIME HIGH ALTITUDE ELECTROMAGNETIC PULSE CODE DEVELOPMENT	AFWL-TR-73-286 VOL II
MEETING MINUTES EED DIRECT DRIVE TESTING HELD AT AFWL	
NUMERICAL APPROACH FOR CALCULATING THE RESPONSE OF A P-N JUNCTION CAPACITOR TO A RAMP SIGNAL	
CIRCUIT ANALYSIS USING THE DRIVING-POINT-IMPEDANCE TECHNIQUE	SC-M-71 0895
1972 THIRTEENTH SCINTILLATION AND SEMICONDUCTOR COUNTER SYMPOSIUM	
AEROSPACE VEHICLE EMI TRANSIENT TEST TECHNIQUES	AFAL-TR-72-102

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

TITLE  
\*\*\*\*\*

FINAL REPORT OF THE H-1 EMP SCALE MODEL FEASIBILITY STUDY C72-302/201

FIELD AND LABORATORY TESTING IDENTIFICATION AND SUMMARY AERONAUTICAL D224-10012-1  
SYSTEMS EMP INTEGRATED TEST PROGRAM ROUGH DRAFT

NUCLEAR AND SPACE RADIATION EFFECTS

EVALUATION OF SEMICONDUCTOR DEVICE ANALYSIS USING THE NET-2 COMPUTER HDL-065-1  
PROGRAM-FINAL REPORT

TECHNIQUES FOR MEASUREMENT OF THE VFO SPECTRUM A TRADE STUDY AL-897(72)

ANALYSIS OF ELECTRICAL OVERSTRESS FAILURES

A TWO-DIMENSIONAL NUMERICAL ANALYSIS OF A SILICON NPN TRANSISTOR

COMPUTER-AIDED TWO DIMENSIONAL NUMERICAL ANALYSIS OF BIPOLAR  
TRANSISTORS

ANALYSIS OF FAILURE OF ELECTRONIC CIRCUITS FROM EMP-INDUCED SIGNALS HDL-TN-1615  
REVIEW AND CONTRIBUTION

DETAILED TEST PLAN-INTEGRATED CIRCUIT TEST BDM/A-48-73-1R

TEST PLAN FOR MOS DEVICE FAILURE C73-573/501

INVESTIGATION OF SECOND BREAKDOWN IN SEMICONDUCTOR JUNCTION DEVICES 34/UAIN-73-002

THE SUSCEPTIBILITY OF X-BAND POINT CONTACT DIODES TO MICROWAVE  
RADIATION TR-2963

FEASIBILITY OF USING FINITE ELEMENTS IN ANALYSIS OF SECOND  
BREAKDOWN IN SEMICONDUCTOR DEVICES HG-73-14

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

TITLE  
\*\*\*\*\*

SECOND BREAKDOWN IN THE PRESENCE OF INTENSE IONIZING RADIATION AND  
RELATED STUDIES DAAM-01-72-C-0894

WORK ORDER 2-14 INTEGRATED CIRCUITS TEST PROGRAM-FINAL REPORT RDM/A-98-73-TR

RESPONSE OF INTEGRATED CIRCUITS TO A SIMULATED EMP ENVIRONMENT HDL-TR-1649

SOLID STATE COMPONENT RF SUSCEPTIBILITY PROGRAM-PROGRESS REPORT FY73 FJK/VGPK MAC 3920

PROGRAM FINAL REPORT C73-1175/501

APPLICATION OF TIME DOMAIN METHODS TO INTEGRATED CIRCUIT  
SUSCEPTIBILITY

INTEGRATED CIRCUIT ELECTROMAGNETIC SUSCEPTIBILITY INVESTIGATION  
PHASE II MDCE0921

ELECTROMAGNETIC PULSE STUDIES VOL I TWO DIMENSIONAL SOUND RUMST  
ELECTROMAGNETIC PULSE CALCULATION METHODS

TECHNIQUES TO DETERMINE SUBSYSTEM LEVEL ELECTROMAGNETIC PULSE  
SUSCEPTIBILITY MDAC PAPER #D2280

A REPORT AND PROPOSAL FOR EXTREMELY HIGH CURRENT INJECTION MODELING  
OF SEMICONDUCTOR DEVICES

A METHOD FOR FITTING EMP WAVEFORMS THAT FACILITATES CALCULATIONS OF  
THE TIME DERIVATIVE AND FOURIER TRANSFORM DNA 32317

COMBINED DOCUMENTATION WORK ORDER 2-14

VPD/AGM-28 GENERAL TEST PLAN C73-356-201

VPD/AGM-28A DETAILED TEST PLAN LONG WIRE BASELINE EXPERIMENT C73-312.1/201



DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE *****	DOCUMENT NO./OTHER NO. *****
VPD/AGM-26 DETAILED TEST PLAN B-526/AG-284 BASELINE EXPERIMENT	C73-312.2/201
VPD/AGM-28A DETAILED TEST PLAN EXTERNAL COUPLING EXPERIMENT	C73-312.3/201
EMP ELECTRONIC ANALYSIS HANDBOOK	U224-10022-1
OBJECTIVES OF THE FB-111 A EMP TEST IN ARTS	C73-424/201
COMMON MODE MODEL DEVELOPMENT FOR COMPLEX CABLE SYSTEMS	D224-10015-4
ANALYSIS AND TEST OF COMMUNICATIONS ANTENNAS	HDM/M-TR145-73
FINAL REPORT RESISTOR MODELLING PROGRAM ASV WORK ORDER 2-14	
EMP DEGRADATION ANALYSIS AND APPLICATION OF EMP FILTERS	C73-946/201
WORK ORDER 2-14 FINAL TECHNICAL REPORT HF RADIO AN/ARC-123 PULSE TESTS	2-5170-ABUE-003
THE DETERMINATION OF SEMICONDUCTOR JUNCTION VULNERABILITY TO SECOND BREAKDOWN BY LOW ENERGY ELECTRICAL MEASUREMENTS	155-93
AARNCP LOW LEVEL TEST FINAL REPORT	U224-13009-1
INTEGRATED CIRCUIT ELECTROMAGNETIC SUSCEPTIBILITY INVESTIGATION PHASE II-BIPOLAR NAND GATE STUDY	MDC E1123
INTEGRATED CIRCUIT MODEL DEVELOPMENT FOR EMP	
EXPERIMENTAL DAMAGE CONSTANT SUMMARY	HDM/A-49-74-TR-R1



DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE *****	DOCUMENT NO./OTHER NO. *****
EMP SUSCEPTIBILITY OF SEMICONDUCTOR COMPONENTS	BDM/A-110-74-1R
DISCRETE SEMICONDUCTOR EMP DATA SUMMARY	BDM/A-111-74-1R
HIGH CURRENT INJECTION MODELING OF SEMICONDUCTOR DEVICES	TR-EE-74-43
FUNDAMENTALS OF EMP DATA MANAGEMENT AND PROCESSING FINAL REPORT	DNA 3179 F
EMP TEST PROCEDURES (SELECTED ELECTRONIC PARTS)	DNA 3286H
ENGINEERING TECHNIQUES FOR ELECTROMAGNETIC PULSE HARDNESS TESTING	DNA3332F
FAILURE ANALYSIS BY STATISTICAL TECHNIQUES (FAST) VOLUME II, USERS MANUAL (APPENDICES)	
BOUNDING EMP DAMAGE PREDICTION UNCERTAINTIES (PRESENTATION)	BDM/A-27-74-8R
SECOND PROGRESS REPORT ON ELECTRONICS MODELING AND CIRCUIT SIMULATION	BDM/W-74-0211R
SIMPLIFIED MICROCIRCUIT MODELING	AFWL-TR-73-272
FINAL REPORT ANALYSIS OF COMMUNICATIONS SYSTEMS EQUIPMENT FAILURE MODELING	BDM/A-60-74-1R
AIRBORNE COMMAND POST AABNCP ELECTRONIC SYSTEM DETAILED PROGRAM PLAN CDRL A01R INTERIM REPORT	
SUPERSAP 2 USER'S MANUAL	U224-13047-1
9-1 SCALE MODEL PRELIMINARY TEST PLAN FOR MEASUREMENT OF WEAPONS RAY AND WHEEL WELL COUPLING (FINAL)	U224-1303B-1

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE *****	DOCUMENT NO./OTHER NO. *****
EXEMPT A DIGITAL COMPUTER EXECUTIVE PROGRAM FOR SYSTEMS ANALYSIS USER'S GUIDE	0224-13050-1
B-1 EMP SUBSYSTEM ASSESSMENT DATA, HF RADIO AN/ARC-123	0224-13022-7
POST EXPERIMENT SUMMARY OF B-1 SCALE MODEL MEASUREMENTS FOR T03-19 INADVERTENT PENETRATIONS	
B-1 EMP SUBSYSTEM ASSESSMENT DATA, IFF AN/APA-54	0224-13022-10
B-1 EMP SUBSYSTEM ASSESSMENT DATA UHF RADIO AN/ARC-109	0224-13022-9
SIMPLIFIED SUBSYSTEM INTERFACE MODEL	
A STUDY OF AMORPHOUS SEMICONDUCTORS FOR SYMMETRICAL VARISTOR APPLICATIONS	
PULSE POWER DAMAGE CHARACTERISTICS OF ELECTRICAL RESISTORS	0224-13058-1
POSITION ON SEMICONDUCTOR DEVICE RESPONSE MODELING FOR THE NUCLEAR ENVIRONMENT	CSC-3040-1
PULSE POWER DAMAGE CHARACTERISTICS OF ELECTRICAL RESISTORS FINAL TECHNICAL REPORT	75SDS4213
RECOMMENDED COMPONENT/SUBSYSTEM RESEARCH PROGRAM BRIEFING	BDM/A-22-75-BR
COMPONENT MODELING AND TEST	4732-8-75-34
PULSE POWER DAMAGE CHARACTERISTICS OF ELECTRICAL RESISTORS	0224-13058-1
EXPERIMENTAL DATA REPORT FOR TECHNICAL DIRECTIVE 4-23	0224-13058-2

UNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE *****	DOCUMENT NO./OTHER NO. *****
ADDENDUM TO EMP SUSCEPTIBILITY OF SEMICONDUCTOR COMPONENTS	D224-13042-2
SEMICONDUCTOR DATA REDUCTION ALGORITHM CONTENTS	D224-13042-3
PROGRAM REPORT ON T.D. 4-6 DEVICE TESTING	BDM/A-CRJ-0346-75
SERIES RESISTANCE EFFECTS IN SEMICONDUCTOR C V PROFILING	VOL. ED-22 NO.5
EMP SUSCEPTIBILITY OF INTEGRATED CIRCUITS	BDM/A-69-75-IR-R1
AN MOS MODELING HIERARCHY INCLUDING RADIATION EFFECTS	BDM/A-89-75-IR-R1
EMP RESPONSE : DAMAGE MODELING OF DIODES, JUNCTION FIELD EFFECT TRANSISTOR DAMAGE TESTING AND SEMICONDUCTOR DEVICE FAILURE ANALYSIS	75 SDS 4279
EXPERIMENTAL DATA REPORT FOR TECHNICAL DIRECTIVE 4-23	D224-13058-2
PRELIMINARY REVIEW DRAFT-EMP PREFERRED TEST PROCEDURES (SELECTED ELECTRONIC PARTS)	
NUCLEAR RADIATION TESTS OF EMP HARDENED CMOS CIRCUITS-FINAL REPORT	
COMPARISON OF ANTENNA-RELATED PREDICTIVE MODELS WITH B-1 SCALE MODEL MEASUREMENTS IN ALECS	D224-13052-2
GEOPHMS3 PROGRAM MANUAL (DRAFT)	D224-13071-1
DTP B-1 SCALE MODEL ALECS, SEC.6 FINAL DETAILED TEST PLAN	D224-13006-1
B-1 EMP RESPONSE FOR INADVERTENT PENETRATION COMPLING FINAL REPORT (DRAFT)	D224-13064-1

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE *****	DOCUMENT NO./OTHER NO. *****
F-111/ARES TEST SUPPORT, VOLUME I DRAFT FINAL REPORT	0224-13059-1
B-52 G/AGM-28A/V2D EXPERIMENT TECHNICAL REPORT VOLUME II DRAFT FINAL REPORT	0224-13069-2
VERTICALLY POLARIZED DIPOLE (VPD) B-52G/AGM-28A TECHNICAL REPORT VOLUME I (DRAFT)	0224-13069-1
SINGLIN PROGRAM MANUAL (FINAL)	0224-13072-1
EMP RESPONSE OF THE B-1 AIRCRAFT FOR INADVERTENT PENETRATION COMPLING VOLUME I, FINAL REPORT	0224-13064-1
DNA EMP SEMINAR SYSTEM LEVEL TESTING	
HIGH CURRENT INJECTION MODELING OF SEMICONDUCTOR DEVICES	TR-EE-76-1
AN ELECTRO-THERMAL MODEL OF SECOND BREAKDOWN, SUMMARY	
COMPUTER AIDED ENGINEERING OF SEMICONDUCTOR INTEGRATED CIRCUITS	ECOM-75-1344-1
HDL IEMP EXPERIMENT SUMMARY	
FEASIBILITY OF USING FINITE ELEMENTS IN ANALYSIS OF BREAKDOWN	AD 766-688
SHORT PULSE WIDTH FAILURE LEVEL CHARACTERIZATION FOR THE 2N3821 JUNCTION FIELD EFFECT TRANSISTOR	PEM-24
MODELING TECHNIQUES FOR MULTICONDUCTOR CAPLESS THEORY AND PRACTICE	AFWL-TR-72-89
DNA EMP HANDBOOK CHAPTER 9 SHIELDING ANALYSIS	

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

TITLE  
\*\*\*\*\*

USING DRIVING POINT IMPEDANCE METHODS ON ACTIVE NETWORKS

MODELING AND SIMULATION TECHNIQUES FOR DAMAGE PREDICTION AND SYSTEM  
ASSESSMENT

A SURVEY OF SELECTED NETWORK ANALYSIS PROGRAMS

SEMICONDUCTOR DAMAGE STUDY

SEMICONDUCTOR DAMAGE CONSTANTS

SIMPLIFIED MICROCIRCUIT MODELING

MODELING SECOND BREAKDOWN WITH NET-2

SECTION II DISCRETE DAMAGE TESTS

COMPUTER ANALYSIS OF HOT SPOT FORMATION IN POWER TRANSISTORS

AN EVALUATION OF SILICON ON SAPPHIRE TECHNOLOGY

HIGH CURRENT INJECTION MODELING OF SEMICONDUCTOR DEVICES  
(DRAFT COPY)

FINAL REPORT ON THE PRELIMINARY R-1 EVALUATION OF EMP RELATED AIRCRAFT C73-310/201  
CHARACTERISTICS VOLUME II

FINAL REPORT EC-135 PRETEST ANALYSIS VOLUME II SYSTEMS DESCRIPTION BDM/A 12-71-41

IN-PLACE EMP WING III THRESHOLD VARIATION SURVEY

D2-19693-3



UNA OVERSTRESS REVIEW#  
SUBJECT INDEX

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

TITLE  
\*\*\*\*\*

COMPUTER ANALYSIS OF EMP INDUCED CIRCUIT FAILURES

THERMAL RESPONSE OF A SEMICONDUCTOR JUNCTION

SOME COMMENTS ON THE MODELS USED TO PREDICT SEMICONDUCTOR DAMAGE  
CONSTANTS

SECTION II A MODEL TO PREDICT POWER FAILURE OF SEMICONDUCTOR DEVICES

A COMPUTER MODEL FOR LATERAL THERMAL INSTABILITIES IN POWER  
TRANSISTORS

\*\*\*\*\*AVALANCHE

AVALANCHE BREAKDOWN IN GERMANIUM

AVALANCHE BREAKDOWN CHARACTERISTICS OF A DIFFUSED P-N JUNCTION

AVALANCHE BREAKDOWN VOLTAGES OF ABRUPT AND LINEARLY GRADED P-N  
JUNCTIONS IN GE, SI, GaAs AND GAP

INPUT POWER INDUCED THERMAL EFFECTS RELATED TO TRANSITION TIME  
BETWEEN AVALANCHE AND SECOND BREAKDOWN IN P-N SILICON JUNCTIONS

AVALANCHE BREAKDOWN OF DIFFUSED SILICON P-N JUNCTIONS

EXPERIMENTAL STUDY OF AVALANCHE BREAKDOWN IN SILICON PLANAR P-N  
JUNCTIONS

ZENER AND AVALANCHE BREAKDOWN IN SILICON ALLOYED P-N JUNCTIONS  
-I- ANALYSIS OF REVERSE CHARACTERISTICS

NEGATIVE RESISTANCE AND FILAMENTARY CURRENTS IN AVALANCHING SILICON

VOL. ED-13 NOS. 8/9

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

MODELING OF AVALANCHE EFFECT IN INTEGRAL CHARGE CONTROL MODEL

AVALANCHE BREAKDOWN IN SILICON DIFFUSED JUNCTIONS

SECOND BREAKDOWN PHENOMENA IN AVALANCHING SILICON ON SAPPHIRE DIODES

THE DEGRADATION OF MOS TRANSISTORS RESULTING FROM JUNCTION AVALANCHE VOL. 11  
BREAKDOWN

\*\*\*\*\*AVIONICS

RADIATION HARDENED AVIONICS GAIN INTEREST

B-1 EMP SUBSYSTEM ASSESSMENT DATA, HF RADIO AN/ARC-123

D224-13022-7

B-1 EMP SUBSYSTEM ASSESSMENT DATA, IFF AV/APA-54

D224-13022-10

\*\*\*\*\*CABLES

INTERIM REPORT RESPONSE OF A MULTICONDUCTOR CABLE TO EXCITATION AT  
AN OPEN BREAK IN THE SHIELD

SC-CW-70-6152

CABLE SYSTEM ANALYSIS

AFML-TR-71-100 VOL 1

INTERIM REPORT RESPONSE OF A MULTICONDUCTOR TRANSMISSION LINE TO  
EXCITATION BY AN ARBITRARY MONOCHROMATIC IMPRESSED FIELD ALONG THE LINE

SC-CW-715076

SIMPLIFICATIONS IN THE STUDY OF GROUNDED-SHIELD, "BALANCED" TWIN-  
LEAD CABLES

SC-CW-715110

UNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

MULTICONDUCTOR CABLE MODELING

0224-10013-2

COMMON MODE MODEL DEVELOPMENT FOR COMPLEX CABLE SYSTEMS

0224-10015-4

SHIELDING EVALUATION OF BRAIDED CABLE SHEATHS AND MULTICONDUCTOR  
CABLES USING PULSE TEST METHODS

PEM-13

RADIATION-INDUCED CURRENTS IN SUBMINIATURE COAXIAL CABLES

SAMSO-TR-75-296

CABLE AND CONNECTOR SHIELDING ATTENUATION AND TRANSFER IMPEDANCE  
MEASUREMENT USING QUADRAXIAL AND QUINTAXIAL TEST METHODS

DEM-45

MODELING TECHNIQUES FOR MULTICONDUCTOR CABLES< THEORY AND PRACTICE

AFWL-TR-72-89

TEST REPORT ON CONDUCTED CURRENT SHIELDING EFFECTIVENESS OF BAYONET  
CONNECTOR SHELLS WITH FINGERS

PEM-12

\*\*\*\*\*CABLE, COAXIAL

COAXIAL CABLE RESPONSE TO IONIZING RADIATION FROM FX-100 AND P3-1590 G0436  
FLASH X-RAY MACHINES

\*\*\*\*\*COMPONENTS

EXPERIMENTAL RESULTS OF TESTING RESISTORS UNDER PULSE CONDITIONS

PEM-6

EXPERIMENTAL RESULTS OF TESTING RESISTORS UNDER PULSE CONDITIONS

PHOTOCAPACITIVE EFFECTS AT SILICON-COLLISION GOLD CONTACTS

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

EXPERIMENTAL INVESTIGATION OF THE PERMANENT EFFECTS OF HF RADIATION IN X-BAND ON ELECTRONIC COMPONENTS	T9-1399
BDM FINAL REPORT VOLUME I SEMICONDUCTOR AND NONSEMICONDUCTOR DAMAGE STUDY	HDM-375-69-F-0168
AUTONETICS ELECTRONIC COMPONENTS FAILURE MODE HANDBOOK	58-1329/501
SEMICONDUCTOR AND NON-SEMICONDUCTOR DAMAGE STUDY PERSHING DEVICES	HDM-375-69-F-0168
EMP CHARACTERIZATION OF SPRINT AUTOPILOT COMPONENTS-FINAL REPORT	CRG 69-2
FRANKLIN INSTITUTE REPORT ON FED PULSE TESTING	F-C2540
LASER TRIGGERED SWITCHING STUDY	AFWL-TM-69-87
COAXIAL CABLE RESPONSE TO IONIZING RADIATION FROM FX-100 AND PR-1590 FLASH X-RAY MACHINES	G0436
CONFERENCE PROCEEDINGS ON COMPONENT DEGRADATION FROM TRANSIENT INPUTS, SPONSORED BY US ARMY MOBILITY EQUIPMENT RESEARCH : DEV. CTR	
RESISTOR MODELING PROGRAM-FINAL REPORT	HDM/A-75-10-1R
COMPONENT VULNERABILITY	
STATISTICAL COMPONENT DAMAGE STUDY	RS-TR-71-1
METHODS, DEVICES AND CIRCUITS FOR THE EMP HARDENING OF ARMY ELECTRONICS	ECOM-0085-F
ECOM CONTRACT DAH07-70-C-0085 MONTHLY AND QUARTERLY REPORTS (BOUND TOGETHER)	

UNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

MISSILE AND AIRCRAFT COMPONENT VULNERABILITY TO EMP	SC-TM-70-902
METHODS DEVICES AND CIRCUITS FOR THE EMP HARDENING OF ARMY ELECTRONICS	ECOM-0275-S
METHODS, DEVICES AND CIRCUITS FOR THE EMP HARDENING OF ARMY ELECTRONICS	BDM/A-119-72-TM
LIFE TESTS OF KEMET SOLID TANTALUM CHIP CAPACITORS AT HIGHLY ACCELERATED VOLTAGES	M72-10
METHODS, DEVICES AND CIRCUITS FOR THE EMP HARDENING OF ARMY ELECTRONICS	ECOM-0275-F
FINAL REPORT ON THE EVALUATION OF SURGE PROTECTION DEVICES FOR EMP HARDENING APPLICATIONS	C72-712/201
GE-MOU VARISTOR-THE SUPER ALPHA VARISTOR	72 CND 260
SHIELDING EFFECTIVENESS OF THE LIQUID TIGHT FLEXIBLE CONDUIT FROM TRANSIENT TESTS	PEN-3
FINAL REPORT ON THE EVALUATION OF SURGE PROTECTION DEVICES FOR EMP HARDENING APPLICATION REVISION NO.1	C72-712/201
R&D CONTRACT STATUS REPORT FOR EVALUATION OF ELECTROEXPLOSIVE DEVICE (EED) RESPONSE TO ELECTROMAGNETIC RADIATION (EMR)	LA-5050-PH
ROUGH DRAFT-EMP PREFERRED TEST PROCEDURES (SELECTED ELECTRONIC PARTS)	
NUMERICAL APPROACH FOR CALCULATING THE RESPONSE OF A P-N JUNCTION CAPACITOR TO A RAMP SIGNAL	
SUPPRESSION DEVICES USED FOR EMP PROTECTION	BDM/A-224-72-TM
REVIEW OF BDM EMP COMPONENT TEST PROGRAMS	BDM/A-143-73-TM



DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*  
DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

THE PHYSICS OF INTERFACE INTERACTIONS RELATED TO RELIABILITY OF  
FUTURE ELECTRONIC DEVICES AFCHL-TR-74-0194

EMP SURGE SUPPRESSION CONNECTORS UTILIZING METAL OXIDE VARISTORS 73504293

COMBINED DOCUMENTATION WORK ORDER 2-14

A GUIDE TO THE USE OF SPARK GAPS FOR ELECTROMAGNETIC PULSE (EMP)  
PROTECTION JES-198-2.54

FINAL REPORT RESISTOR MODELING PROGRAM ASV WORK ORDER 2-14

COMPONENT DAMAGE FROM ELECTROMAGNETIC PULSE (EMP) INDUCED TRANSIENTS  
(DRAFT)

TREE MODELING REQUIREMENTS, DNA COMPONENTS RESPONSE AND  
PREDICTION WORKING GROUP MEETING MATERIAL

SPECIAL DEVICES, TEST STRUCTURES, AND HYBRID CIRCUITS FOR SPECIAL  
ENVIRONMENTS HDL-TR-003-1

DEFENSE NUCLEAR AGENCY EMP SEMINAR-SUBSYSTEM AND COMPONENT  
SUSCEPTIBILITY

DEVELOPMENT OF DISC TRANSFORMERS FOR TPD APPLICATIONS IN EMP  
SUPPRESSION HDL-CR-143-1

EMP TEST PROCEDURES (SELECTED ELECTRONIC PARTS) DNA 3286H

HYBRID SPARK GAP SURGE ARRESTORS< A HIGH FREQUENCY RECEIVED SYSTEM  
ARRESTOR FOR LIGHTNING AND EMP PROTECTION PEM-42

DEFENSE NUCLEAR AGENCY EMP SEMINAR "SUBSYSTEM AND COMPONENT  
SUSCEPTIBILITY"

CAPACITOR FAILURE TO HIGH LEVEL ELECTRICAL TRANSIENTS DRAFT

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

AFWL-TR-74-309

SURVEY OF CIRCUIT ELEMENTS USED FOR REDUCTION OF AND PROTECTION  
FROM SYSTEMS GENERATED ELECTRO MAGNETIC PULSE EFFECTS

DNA EMP HANDBOOK CHAPTER 13 COMPONENT EMP SEMIACTIVITY AND SYSTEM  
UPSET

0224-13058-1

PULSE POWER DAMAGE CHARACTERISTICS OF ELECTRICAL RESISTORS

75SDS4213

PULSE POWER DAMAGE CHARACTERISTICS OF ELECTRICAL RESISTORS  
FINAL TECHNICAL REPORT

75SDS4214

PULSE POWER DAMAGE CHARACTERISTICS OF ELECTRICAL RESISTORS  
EXPERIMENTAL DATA REPORT

BDM/A-22-75-8R

RECOMMENDED COMPONENT/SUBSYSTEM RESEARCH PROGRAM BRIEFING

COMPONENT MODELING AND TEST

4732-8-75-34

KEY SUPPRESSION DEVICES PARAMETERS FOR EMP HARDENING

PEM-38

VOLTAGE CLAMPING LEVELS FOR SEVERAL "TRANSORR" TRANSIENT SUPPRESSION  
DEVICES

PEM-33

0224-13058-1

PULSE POWER DAMAGE CHARACTERISTICS OF ELECTRICAL RESISTORS

75SDS4241

PULSED VOLTAGE FAILURE LEVELS OF CAPACITORS GENERAL TEST PLAN

AFWL-TR-75-100

ADVANCED REVERSED SWITCHING RECTIFIER MODULATOR

PARTS, HYBRIDS AND PACKAGING

BDM/A-75-10-TR

FINAL REPORT RESISTOR SUSCEPTIBILITY SURVEY

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

HOL-TM-75-25

CAPACITOR FAILURE DUE TO HIGH LEVEL ELECTRICAL TRANSIENTS

RELIABILITY DATA FOR ELECTRONIC AND ELECTROMECHANICAL COMPONENTS< A  
REPORT

SAMSO STANDARD- LIST OF PREFERRED PARTS FOR SPACE AND MISSILE SYSTEM SAMSO-STD 73-4 A

NOISE IN ELECTRONIC DEVICES

DEVELOPMENT OF AN APPROVED PARTS LIST FOR RELIABLE ELECTRONIC  
COMPONENTS

ELECTRONIC STATES OF SOLID EXPLOSIVES AND THEIR PROBABLE ROLE IN  
DETONATIONS

DRAFT OF CHAPTER 13 EMP COMPONENT SENSITIVITY AND SYSTEM UPSET  
ADVANCED RELEASE

CHAPTER IV EMP EFFECTS ON COMPONENTS (PART OF< EMP RADIATION AND  
PROTECTIVE TECHNIQUES)

DEVICE DEGRADATION BY HIGH AMPLITUDE CURRENTS AND RESPONSE  
CHARACTERISTICS OF DISCRETE RESISTORS

SURVEY OF ELECTROEXPLOSIVE DEVICES

REPORT NUMBER TPD 002 FEASIBILITY STUDY INTO THE USE OF  
TRANSZORBS FOR EMP SUPPRESSION TPD 002

METHODS, DEVICES, AND CIRCUITS FOR THE EMP HARDENING  
OF ARMY ELECTRONICS (REPORTS<FINAL, R/70, 1/71, 3/71, 5/71, 2/72, 3/72, BDM/A-119-72-TR

PULSE DAMAGE DATA FROM INTEGRATED CIRCUITS AND ELECTRONIC PARTS

SAMSO STANDARD- ELECTRONIC PARTS, MATERIALS AND PROCESSES FOR SPACE AND MISSILE APPLICATIONS, STANDARD CONTROL PROGRAM FOR SAMSO-STD 73-2C

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

\*\*\*\*\*COUP-ING

AABNCP LOW LEVEL TEST FINAL REPORT

0224-13009-1

\*\*\*\*\*CURRENT

A NEW HIGH CURRENT MODE OF TRANSISTOR OPERATION

THEORY OF CURRENT-CARRIER TRANSPORT AND PHOTOCONDUCTIVITY IN  
SEMICONDUCTORS WITH TRAPPING

SOME NEW ASPECTS OF THERMAL INSTABILITY OF THE CURRENT  
DISTRIBUTION IN POWER TRANSISTORS

STATIC V-I RELATIONSHIPS IN TRANSISTORS AT HIGH INJECTION LEVELS

FORWARD CURRENT SURGE FAILURE IN SEMICONDUCTOR RECTIFIERS

77-746

A PROGRAM TO INVESTIGATE RADIATION INITIATED, CURRENT INDUCED  
FAILURES IN SEMICONDUCTOR DEVICES

MEMO 1457-117

A THEORETICAL INVESTIGATION ON THE GENERATION CURRENT IN SILICON P-N  
JUNCTIONS UNDER REVERSE BIAS

SEMICONDUCTOR DEVICE DEGRADATION BY HIGH CURRENT PULSES

SC-DC-72-2288

SEMICONDUCTOR DEVICE DEGRADATION BY HIGH AMPLITUDE CURRENT PULSES

SC-RR-72-0515

A REPORT AND PROPOSAL FOR EXTREMELY HIGH CURRENT INJECTION MODELING  
OF SEMICONDUCTOR DEVICES



DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

IMPROVEMENTS IN THE TREATMENT OF COMPTON CURRENT AND AIR CONDUCTIVITY IN EMP PROBLEMS	DNA 3192 Y
HIGH CURRENT INJECTION MODELING OF SEMICONDUCTOR DEVICES	TR-EE-74-43
AN INVESTIGATION OF CURRENT MODE SECOND BREAKDOWN	177-93
DEGRADATION OF MONOLITHIC SEMICONDUCTOR DEVICES BY HIGH AMPLITUDE CURRENT PULSES	RADC-TR-75-17
HIGH CURRENT INJECTION MODELING OF SEMICONDUCTOR DEVICES	TR-EE-76-1
HIGH CURRENT TRANSIENT INDUCED JUNCTION SHORTS	
DEVICE DEGRADATION BY HIGH AMPLITUDE CURRENTS AND RESPONSE CHARACTERISTICS OF DISCRETE RESISTORS	
CURRENT CROWDING IN HARDENED POWER TRANSISTORS	
HIGH CURRENT INJECTION MODELING OF SEMICONDUCTOR DEVICES (DRAFT COPY)	

\*\*\*\*\*DIODES

HIGH VOLTAGE CONDUCTIVITY MODULATED SILICON RECTIFIER  
DIODES  
ELECTRICAL PROPERTIES OF GOLD DOPED DIFFUSED SILICON COMPUTER  
DIODES  
FORWARD TRANSIENT BEHAVIOR OF P-N JUNCTION DIODES AT HIGH INJECTION  
LEVELS  
SURFACE ASPECTS OF THE THERMAL DEGRADATION OF GSAS P-N JUNCTION LASER  
AND TUNNEL DIODES



DNA OVERSTRESS REVIEW  
SUBJECT INDEX

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

TITLE  
\*\*\*\*\*

ANALYSIS OF THE TEMPERATURE RISE IN PIN DIODES CAUSED BY MICROWAVE  
PULSE DISSIPATION

SECOND BREAKDOWN IN SIMPLIFIED TRANSISTOR STRUCTURES AND DIODES VOL. ED-13, NOS 8/9

SILICON POWER ZENER TRANSIENT SUPPRESSORS

METAL-SILICON SCHOTTKY BARRIERS

RADIATION EFFECTS ON GALLIUM ARSENIDE DEVICES AND SCHOTTKY DIODES AFWL-TR-68-31 VOL222

DETERMINATION OF THRESHOLD FAILURE LEVEL OF SEMICONDUCTOR DIODES AND  
TRANSISTORS DUE TO PULSE VOLTAGES.

DETERMINATION OF THRESHOLD FAILURE LEVELS OF SEMICONDUCTOR DIODES  
AND TRANSISTORS DUE TO PULSE VOLTAGES

DETERMINATION OF THRESHOLD FAILURE LEVELS OF SEMICONDUCTOR DIODES  
AND TRANSISTORS DUE TO PULSE VOLTAGES

FORWARD CURRENT SURGE FAILURE IN SEMICONDUCTOR RECTIFIERS 77-746

MEASUREMENTS ON THE DEPLETION LAYER PROPERTIES OF PLANAR DIODES

SEMICONDUCTOR VULNERABILITY PHASE II REPORT THEORETICAL ESTIMATES  
FAILURE LEVELS OF SELECTED SEMICONDUCTOR DIODES AND TRANSISTORS BDM/A-42-69-M

SEMICONDUCTOR VULNERABILITY-PHASE II REPORT-THEORETICAL ESTIMATES  
OF FAILURE LEVELS OF SELECTED SEMICONDUCTOR DIODES AND TRANSISTORS BDM/A-42-69-M

MODELS FOR THE PN DIODE AND THE NPN AND PNP TRANSISTOR FOR USE IN  
COMPUTER AIDED DESIGN AND ANALYSIS PROGRAMS

TRANSISTOR AND DIODE MODEL HANDBOOK 69-521-1

ONA OVERSTRESS REVIEW  
SUBJECT INDEX

DOCUMENT NO. 707-HER NO.  
\*\*\*\*\*

TITLE  
\*\*\*\*\*

THEORETICAL ESTIMATES OF FAILURE LEVELS OF SELECTED SEMICONDUCTOR  
DIODES AND TRANSISTORS BDM/A-34-69R

SEMICONDUCTOR VULNERABILITY PHASE III REPORT EXPERIMENTAL THRESHOLD  
FAILURE LEVELS OF SELECTED DIODES AND TRANSISTORS BDM/A-75-70-TR

THE REAL CULPRIT IN DIODE FAILURE

NET TRANSISTOR AND DIODE LIBRARY TAPE 4925

RF BURNOUT IN X-BAND SCHOTTKY MIXERS

JUNCTION CAPACITANCE AS A FUNCTION OF VOLTAGE FOR DIFFUSED P-N DIODES  
WITH EXPONENTIAL DOPING GRADIENTS

SECOND-BREAKDOWN PHENOMENA IN AVALANCHING SILICON ON SAPPHIRE DIODES

LIMITATIONS IN MICROELECTRONICS-II. BIPOLAR TECHNOLOGY

A SIMPLE METHOD FOR DETERMINING STATIC PARAMETERS OF LARGE SIGNAL  
SEMICONDUCTOR DIODE AND TRANSISTOR MODELS

SHORT PULSE EFFECTS IN SEMICONDUCTOR DIODES

THE SUSCEPTIBILITY OF X-BAND POINT CONTACT DIODES TO MICROWAVE  
RADIATION TR-2963

SEMICONDUCTOR VULNERABILITY VOL I THEORETICAL ESTIMATES OF FAILURE  
LEVELS OF SELECTED SEMICONDUCTOR DIODES AND TRANSISTORS-PHASE II AFWL-TR-73-119 VOL I

SEMICONDUCTOR VULNERABILITY VOL II - EXPERIMENTAL THRESHOLD FAILURE  
LEVELS OF SELECTED DIODES AND TRANSISTORS - PHASE III AFWL-TR-73-119 VOL II

PULSE BURNOUT OF MICROWAVE MIXER DIODES

VOL. R-22 NO.4

UNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

COMBINED DOCUMENTATION WORK ORDER 2-14

CONSTANT VOLTAGE DIODES ARE GETTING SHARPER

EMP RESPONSE : DAMAGE MODELING OF DIODES, JUNCTION FIELD EFFECT  
TRANSISTOR DAMAGE TESTING AND SEMICONDUCTOR DEVICE FAILURE ANALYSIS 75 SDS 4279

STUDY OF THE COMBINED EFFECTS OF IONIZATION, NEUTRONS, TEMPERATURE  
AND TIME ON BIPOLAR DEVICES. SLA-73-402

\*\*\*\*\*DOPING

EVALUATION OF DOPING PROFILES FROM CAPACITIVE MEASUREMENTS

JUNCTION CAPACITANCE AS A FUNCTION OF VOLTAGE FOR DIFFUSED P-N DIODES  
WITH EXPONENTIAL DOPING GRADIENTS

SYNTHESIS OF GENERAL IMPURITY PROFILES USING A TWO-STEP  
DIFFUSION PROCESS

PERIPHERAL AND DIFFUSED LAYER EFFECTS ON DOPING PROFILES

\*\*\*\*\*EMP

1968 IEEE ELECTROMAGNETIC COMPATIBILITY SYMPOSIUM RECORD IEEE 68C12-EMC

EMP CHARACTERIZATION OF SPRINT AIRCRAFT COMPONENTS-FINAL REPORT CREG 69-2

ELECTROMAGNETIC COMPATIBILITY-MCDONNELL DOUGLAS CORPORATION  
ELECTRONIC SYMPOSIUM

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*  
DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

AFWL-TR-69-87

LASER TRIGGERED SWITCHING STUDY

ELECTROMAGNETIC EFFECTS OF NUCLEAR EXPLOSIONS ON ELECTRONIC SYSTEMS VOL7 NO.5

SPARK GAP SIMULATES A-BOMB EMP

ELECTROMAGNETIC PULSE SIMULATOR

INSTRUMENTATION FOR NUCLEAR WEAPONS EFFECTS SIMULATION SYMPOSIUM-  
VOLUME I-ELECTROMAGNETIC PULSE AFSWC-TR-70-S VOL.I

USER'S MANUAL FOR THE NETWORK EMP DAMAGE ANALYSIS PROGRAM (NEDAP) RG-TR-70-2

MEASUREMENTS AND ANALYSIS OF LIGHTNING INDUCED VOLTAGE IN AIRCRAFT  
ELECTRICAL CIRCUITS HVL-69-161

AN ANALYTICAL AND LOW-LEVEL TESTING APPROACH TO THE EMP SYSTEMS  
PROBLEM SWV TM-70-7

COMBINED EMP AND IONIZATION EFFECTS

SYNERGISTIC CONSIDERATIONS FOR THE SECOND BREAKDOWN OF A P-N  
JUNCTION IN A PULSED ELECTRICAL AND PULSED RADIATION ENVIRONMENT MEMO 1457-55

NUCLEAR ELECTROMAGNETIC PULSE PROTECTIVE MEASURES APPLIED  
TO A TYPICAL COMMUNICATION SHELTER N-1091

EMP THREAT AND PROTECTIVE MEASURES TR-61

DRAFT FINAL REPORT DASA EMP HANDBOOK REVISION RDM/A 104-70-HBK

INTERIM NOTES 9-52 EMP TEST PROGRAM NOTE 6 GENERAL PROCEDURES FOR  
SUBSYSTEM EMP TESTING RDM/A-121-70-PN

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE *****	DOCUMENT NO./OTHER NO. *****
INVESTIGATION INTO ELECTROMAGNETIC PULSE VULNERABILITY ON SELECTED BIPOLAR TRANSISTORS	MDC E0278
METHODS, DEVICES AND CIRCUITS FOR THE EMP HARDENING OF ARMY ELECTRONICS	ECOM-0085-F
THE MODIFIED SIEGE 1.2 PULSE DRIVER	AFWL-TR-71-49
ELECTROMAGNETIC PULSE SENSOR HANDBOOK VOLUME I	
ELECTROMAGNETIC PULSE INSTRUMENTATION HANDBOOK-VOLUME I	
RECOMMENDED INTERNAL COUPLING ANALYSIS TECHNIQUES FOR THE B-52S EMP TEST PROGRAM	BDM/A-66-71-1R
AN EXPERIMENTAL INVESTIGATION OF EMP INDUCED TRANSIENT UPSET OF INTEGRATED CIRCUITS	SC-1M-71 0330
ELECTROMAGNETIC PULSE SENSOR HANDBOOK	AFWL MEASUREMENT 1-1
IN-PLACE EMP CRITICAL CIRCUIT THRESHOLD ANALYSIS	D2-19693-2
DNA EMP AWARENESS COURSE NOTES	AD-741706
EMP PROTECTIVE SYSTEMS	TR-61-B
METHODS DEVICES AND CIRCUITS FOR THE EMP HARDENING OF ARMY ELECTRONICS	ECOM-0275-S
METHODS, DEVICES AND CIRCUITS FOR THE EMP HARDENING OF ARMY ELECTRONICS	BDM/A-119-72-1R
METHODS, DEVICES AND CIRCUITS FOR THE EMP HARDENING OF ARMY ELECTRONICS	ECOM-0275-F



DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE *****	DOCUMENT NO./OTHER NO. *****
FINAL REPORT ON THE EVALUATION OF SURGE PROTECTION DEVICES FOR EMP HARDENING APPLICATIONS	C72-712/201
INTEGRATED CIRCUIT ELECTRO MAGNETIC SUSCEPTIBILITY INVESTIGATION DEVELOPMENT PHASE REPORT	MDC 00690
AIR FORCE SYSTEMS COMMAND - DESIGN HANDBOOK 1-4- ELECTROMAGNETIC COMPATIBILITY - SECOND EDITION	AFSC DM1-4
EMP PROTECTION ENGINEERING THE NEED FOR DOCUMENTATION	PEM-1
AERONAUTICAL SYSTEMS EMP TECHNOLOGY REVIEW	D224-10004-1
FINAL REPORT ON THE EVALUATION OF SURGE PROTECTION DEVICES FOR EMP HARDENING APPLICATION REVISION NO.1	C72-712/201
R:D CONTRACT STATUS REPORT FOR EVALUATION OF ELECTROEXPLOSIVE DEVICE LA-5050-PH (EED) RESPONSE TO ELECTROMAGNETIC RADIATION (EMR)	LA-5050-PH
ELECTROMAGNETIC PULSE HANDBOOK FOR MISSILES AND AIRCRAFT IN FLIGHT	
EMP DAMAGE HARDENING GUIDELINES	D224-10016-1
ROUGH DRAFT-EMP PREFERRED TEST PROCEDURES (SELECTED ELECTRONIC PARTS)	
ELECTROMAGNETIC PULSE ENVIRONMENT STUDIES VOLUME II LATE TIME HIGH ALTITUDE ELECTROMAGNETIC PULSE CODE DEVELOPMENT	AFWL-TR-73-286 VOL II
DESIGN GUIDELINES FOR EMP HARDENING OF AERONAUTICAL SYSTEMS (DRAFT)	C72-451/201
B-52/VPD GENERAL TEST PLAN	D224-10000-1
FINAL REPORT OF THE B-1 EMP SCALE MODEL FEASIBILITY STUDY	C72-302/201

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE	DOCUMENT NO./OTHER NO.
*****	*****
FIELD AND LABORATORY TESTING IDENTIFICATION AND SUMMARY AERONAUTICAL SYSTEMS EMP INTEGRATED TEST PROGRAM HJG4 DRAFT	D224-10012-1
EMP PROTECTIVE SYSTEMS	TR-61-B
EMP PROTECTION FOR EMERGENCY OPERATING CENTERS	TR-61A
NUCLEAR AND SPACE RADIATION EFFECTS	
SUPPRESSION DEVICES USED FOR EMP PROTECTION	BDM/A-224-72-TR
TECHNIQUES FOR MEASUREMENT OF THE VPD SPECTRUM < A TRADE STUDY	AL-897(72)
EMP UPSET HARDENING GUIDELINES	D22A-10016-2
ANALYSIS OF FAILURE OF ELECTRONIC CIRCUITS FROM EMP-INDUCED SIGNALS REVIEW AND CONTRIBUTION	HDL-TR-1615
REVIEW OF BDM EMP COMPONENT TEST PROGRAMS	BDM/A-143-73-TR
FEASIBILITY STUDY FOR EMP TERMINAL PROTECTION	TPD 003
DESIGN GUIDELINES FOR EMP HARDENING OF AERONAUTICAL SYSTEMS	AFWL-TR-73-117
EMP HARDENED CMOS CIRCUIT	HDL-TR-192-1
EMP SURGE SUPPRESSION CONNECTORS UTILIZING METAL OXIDE VARISTORS	73SD4293
EMP ELECTRONIC DESIGN HANDBOOK	D224-10019-1

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*  
DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

EMP HARDENING OF G.F.E.  
0224-10023-1

JOINT EMP TECHNICAL MEETING FIRST ANNUAL NUCLEAR EMP MEETING NEM  
1973 ABSTRACTS OF TECHNICAL PAPERS

MDCE0921

INTEGRATED CIRCUIT ELECTROMAGNETIC SUSCEPTIBILITY INVESTIGATION  
PHASE II

SHORT COURSE IN NUCLEAR WEAPON EFFECTS AND SURVIVABILITY OF  
AEROSPACE SYSTEMS

MDL-TR-1636

EMP SHIELDING EFFECTIVENESS AND MIL STD. 285

ELECTROMAGNETIC PULSE STUDIES VOL. I TWO DIMENSIONAL GROUND RUMST  
ELECTROMAGNETIC PULSE CALCULATION METHODS

MDAC PAPER #D2280

TECHNIQUES TO DETERMINE SUBSYSTEM LEVEL ELECTROMAGNETIC PULSE  
SUSCEPTIBILITY

DNA 3192 T

IMPROVEMENTS IN THE TREATMENT OF COMPTON CURRENT AND AIR  
CONDUCTIVITY IN EMP PROBLEMS

DNA 32317

A METHOD FOR FITTING EMP WAVEFORMS THAT FACILITATES CALCULATIONS OF  
THE TIME DERIVATIVE AND FOURIER TRANSFORM

PEM-3D

EMP HARDENING APPROACH FOR SAM-D

C73-356-201

VPD/AGM-28 GENERAL TEST PLAN

C73-312.1/201

VPD/AGM-28A DETAILED TEST PLAN LONG WIRE BASELINE EXPERIMENT

C73-312.2/201

VPD/AGM-28 DETAILED TEST PLAN B-52G/AGM-28A BASELINE EXPERIMENT

C73-312.3/201

VPD/AGM-28A DETAILED TEST PLAN EXTERNAL COUPLING EXPERIMENT

UNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

EMP ELECTRONIC ANALYSIS HANDBOOK

OBJECTIVES OF THE FB-111 A EMP TEST IN AREAS

A GUIDE TO THE USE OF SPARK GAPS FOR ELECTROMAGNETIC PULSE (EMP)  
PROTECTION

ASAP-1 FINAL REPORT

AABNCP LOW LEVEL TEST AIRPLANE LOGISTICS

EMP DEGRADATION ANALYSIS AND APPLICATION OF EMP FILTERS

TEST REPORT FOR EC-135C INTERNAL COUPLING MEASUREMENTS

COMPONENT DAMAGE FROM ELECTROMAGNETIC PULSE (EMP) INDUCED TRANSIENTS  
(DRAFT)

ENGINEERING DESIGN GUIDELINES FOR EMP HARDENING OF NAVAL MISSILES  
AND AIRPLANES

AABNCP LOW LEVEL TEST FINAL REPORT

INTEGRATED CIRCUIT ELECTROMAGNETIC SUSCEPTIBILITY INVESTIGATION  
PHASE II-BIPOLAR NAND GATE STUDY

INTEGRATED CIRCUIT MODEL DEVELOPMENT FOR EMP

DEFENSE NUCLEAR AGENCY EMP SEMINAR-SUBSYSTEM AND COMPONENT  
SUSCEPTIBILITY

CHARACTERISTICS AND APPLICATIONS OF METAL OXIDE VARISTORS FOR EMP  
HARDENING

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

0224-10022-J

C73-424/201

JES-198-2.5W

0224-12013-1

0226-10113-1

C73-946/201

D180-17726-1

AMRC-R-17

0224-13009-1

MDC E1123

PEM-43

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE *****	DOCUMENT NO./OTHER NO. *****
EMP TRANSIENT SUPPRESSION	PEM-31
EMP SURGE SUPPRESSION CONNECTORS UTILIZING METAL OXIDE VARISTORS	HDL-TR-177-1
INTEGRATED CIRCUIT ELECTROMAGNETIC SUSCEPTIBILITY NOTEBOOK	
EMP SUSCEPTIBILITY OF SEMICONDUCTOR COMPONENTS	HDM/A-110-74-TR
DISCRETE SEMICONDUCTOR EMP DATA SUMMARY	HDM/A-111-74-TR
INTEGRATED CIRCUIT EMP DATA SUMMARY	HDM/A-112-74-TR
DEVELOPMENT OF DISC TRANSISTORS FOR TPJ APPLICATIONS IN EMP SUPPRESSION	HDL-CR-143-1
DIRECT INTERACTION EFFECTS IN EMP	DNA 3249T
FUNDAMENTALS OF EMP DATA MANAGEMENT AND PROCESSING FINAL REPORT	DNA 3179 F
MATHEMATICAL MODELS FOR THE RESPONSE OF AEROSPACE SYSTEMS TO HIGH FREQUENCY ELECTROMAGNETIC ENVIRONMENTS	SLA-74-0131
SHIELDING EVALUATION OF BRAIDED CABLE SHEATHS AND MULTICONDUCTOR CABLES USING PULSE TEST METHODS	PEM-13
EMP TEST PROCEDURES (SELECTED ELECTRONIC PARTS)	DNA 3286H
HYBRID SPARK GAP SURGE ARRESTORS< A HIGH FREQUENCY RECEIVER SYSTEM ARRESTOR FOR LIGHTNING AND EMP PROTECTION	PEM-42
THE EFFECT OF GROUND REFLECTION ON OBSERVED EMP WAVEFORMS	DNA3370T



DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE *****	DOCUMENT NO./OTHER NO. *****
ENGINEERING TECHNIQUES FOR ELECTROMAGNETIC PULSE HARDNESS TESTING	DNA3332F
GENERATION OF INTENSE NANOSECOND PULSES	FTD-HC-23-2796-74
BOUNDING EMP DAMAGE PREDICTION UNCERTAINTIES (PRESENTATION)	BDM/A-27-74-6H
A METHOD FOR THE PREDICTION OF EMP DAMAGE PROBABILITY	BDM/A-9-74-TM
DEFENSE NUCLEAR AGENCY EMP SEMINAR "SUBSYSTEM AND COMPONENT SUSCEPTIBILITY"	
B-1 SCALE MODEL PRELIMINARY TEST PLAN FOR MEASUREMENT OF WEAPONS BAY AND WHEEL WELL COUPLING (FINAL)	U224-13038-1
EXEMPT A DIGITAL COMPUTER EXECUTIVE PROGRAM FOR SYSTEMS ANALYSIS USER'S GUIDE	0224-13050-1
DETAILED TEST PLAN B-1 SCALE MODEL/ALECS TEST PROGRAM SECTION 5	0224-13006-1
F-111/ARES DETAIL TEST PLAN VOL.222, EXTERNAL COUPLING AND DELIBERATE ANTENNA EXPERIMENTS	0224-13008-3
B-1 EMP SUBSYSTEM ASSESSMENT DATA, HF RADIO AN/AFC-123	0224-13022-7
POST EXPERIMENT SUMMARY OF B-1 SCALE MODEL MEASUREMENTS FOR T03-19 INADVERTENT PENETRATIONS	
SRAM/ARES DETAIL TEST PLAN	0224-13008-4
B-1 ALECS POST EXPERIMENT SUMMARY FOR TECHNICAL DIRECTIVE 3-18 MEASUREMENTS	
B-1 EMP SUBSYSTEM ASSESSMENT DATA, IFF AN/APA-54	0224-13022-10

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

TITLE  
\*\*\*\*\*

D224-13022-9

B-1 EMP SUBSYSTEM ASSESSMENT DATA UHF RADIO AN/ARC-109

EMP SUSCEPTIBILITY OF INTEGRATED CIRCUITS

DNA EMP HANDBOOK CHAPTER 13 COMPONENT EMP SEMIACTIVITY AND SYSTEM  
JPSET

POSITION ON SEMICONDUCTOR DEVICE RESPONSE MODELING FOR THE NJC-EAR  
ENVIRONMENT

CSC-3040-1

KEY SUPPRESSION DEVICES PARAMETERS FOR EMP HARDENING

PEM-38

ADDENDUM TO EMP SUSCEPTIBILITY OF SEMICONDUCTOR COMPONENTS

D224-13042-2

ADDENDUM TO DISCRETE SEMICONDUCTOR EMP DATA SUMMARY

D224-13043-2

ADDENDUM TO EMP SUSCEPTIBILITY OF SEMICONDUCTOR COMPONENTS

D224-13042-2

FINAL REPORT FOR EMP INSTRUMENTATION PROJECT (DNAIACHO 75-815)  
MAGNETIC THIN FILM SENSORS UNIV. OF CALIF. / LIVERMORE

UCID-16945

ELECTROMAGNETIC PULSE HANDBOOK FOR ELECTRIC POWER SYSTEMS

DNA 3466F

EMP SUSCEPTIBILITY OF INTEGRATED CIRCUITS

RDM/A-69-75-IR-R1

EMP RESPONSE : DAMAGE MODELING OF DIODES, JUNCTION FIELD EFFECT  
TRANSISTOR DAMAGE TESTING AND SEMICONDUCTOR DEVICE FAILURE ANALYSIS

75 SDS 4279

PRELIMINARY REVIEW DRAFT-EMP PREFERRED TEST PROCEDURES (SELECTED  
ELECTRONIC PARTS)

NUCLEAR RADIATION TESTS OF EMP HARDENED CMOS CIRCUITS-FINAL REPORT

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

TITLE  
\*\*\*\*\*

PEM-37

SOME HANDBOOK REFERENCES AND A SUMMARY FOR EMP ENGINEERING AND  
DESIGN PRINCIPLES PUBLISHED BY REL. LABORATORIES  
EMP ENGINEERING AND DESIGN PRINCIPLES

COMPARISON OF ANTENNA-RELATED PREDICTIVE MODELS WITH B-1 SCALE  
MODEL MEASUREMENTS IN ALECS 0224-13052-2

GEOPRMS3 PROGRAM MANUAL (DRAFT) 0224-13071-1

F-111/ARES DETAIL TEST PLAN, VOLUME V PHASE II INTEGRATED TEST PLAN  
(FINAL) 0224-13008-5

DTP B-1 SCALE MODELS, SEC. 6 FINAL DETAILED TEST PLAN 0224-13006-1

F-111/ARES TEST SUPPORT, VOLUME I DRAFT FINAL REPORT 0224-13059-1

B-52 G/AGM-28A/VPD EXPERIMENT TECHNICAL REPORT VOLUME II DRAFT  
FINAL REPORT 0224-13069-2

VERTICALLY POLARIZED DIPOLE (VPD) R-52G/AGM-28A TECHNICAL REPORT  
VOLUME I (DRAFT) 0224-13069-1

SINGLIN PROGRAM MANUAL (FINAL) 0224-13072-1

EXTERNAL COUPLING OF AN ELECTROMAGNETIC PULSE TO THE B-1 AIRCRAFT 0224-13060-1

EMP RESPONSE OF THE B-1 AIRCRAFT FOR INADVERTENT PENETRATION  
COMPLING VOLUME I, FINAL REPORT 0224-13064-1

DNA EMP SEMINAR SYSTEM LEVEL TESTING

BIPOLAR VOLTAGE PULSE DAMAGE EFFECTS ON TRANSISTORS AD 766-685

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

DNA EMP AWARENESS COURSE NOTES

DNA-2772-T

EMP TRANSIENT PROTECTION

DEM-31

NUCLEAR VULNERABILITY ASSESSMENT

SEMICONDUCTOR DEVICE DAMAGE IN AN EMP ENVIRONMENT

TRANSIENT COLLECTOR BREAKDOWN IN THE PRESENCE OF GAMMA RADIATION AND  
CONDUCTED EMP

DRAFT OF CHAPTER 13 EMP COMPONENT SENSITIVITY AND SYSTEM UPSET  
ADVANCED RELEASE

NWE INDUCED ELECTRICAL OVERSTRESS JUNCTION FAILURES IN SEMICONDUCTION  
A PROPOSED PROGRAM

CHAPTER IV EMP EFFECTS ON COMPONENTS (PART OF< EMP RADIATION AND  
PROTECTIVE TECHNIQUES)

MECHANISMS OF RADIATION AND PULSED ELECTRICAL FAILURE IN  
SEMICONDUCTOR ELECTRONICS

MEMO 1H57-119

SOME ASPECTS OF EMP HARDNESS ASSJPPANCE

PEM-23

FINAL REPORT ON THE PRELIMINARY 9-1 EVALUATIONF EMP RELATED AIRCRAFT C73-310/201  
CHARACTERISTICS VOLUME II

AARNCP LOW LEVEL TEST PLAN

D226-10109-1

REPORT NUMBER TPD 002 FEASIBILITY STUDY INTO THE USE OF  
TRANSZORRS FOR EMP SJPPRESSION

TPD 002

IN-PLACE EMP WING III THRESHOLD VARIATION SURVEY

D2-19693-3

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

COMPUTER ANALYSIS OF EMP INDUCED CIRCUIT FAILURES

\*\*\*\*\*EQUIPMENT

PROTECTION OF SEMICONDUCTOR DEVICES, CIRCUITS AND EQUIPMENT  
FROM VOLTAGE TRANSIENTS

METHODS, DEVICES AND CIRCUITS FOR THE EMP HARDENING OF ARMY  
ELECTRONICS

ECOM-0085-F

METHODS, DEVICES AND CIRCUITS FOR THE EMP HARDENING OF ARMY  
ELECTRONICS

ECOM-0275-F

\*\*\*\*\*FAILURES

COMPUTER ANALYSIS OF EMP INDUCED CIRCUIT FAILURES

\*\*\*\*\*FAILURE

SURFACE ASPECTS OF THE THERMAL DEGRADATION OF GSAS P-N JUNCTION LASER  
AND TUNNEL DIODES

TRANSISTOR FAILURE BY SECOND BREAKDOWN

VOL. ED-13 NOS. 8/9

DETERMINATION OF THRESHOLD FAILURE LEVEL OF SEMICONDUCTOR DIODES AND  
TRANSISTORS DUE TO PULSE VOLTAGES.

DETERMINATION OF THRESHOLD FAILURE LEVELS OF SEMICONDUCTOR DIODES  
AND TRANSISTORS DUE TO PULSE VOLTAGES



DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

SEMICONDUCTOR DAMAGE STUDY-PRELIMINARY REPORTS

DETERMINATION OF SEMICONDUCTOR FAILURE LEVELS DUE TO HIGH VOLTAGE TRANSIENTS

DETERMINATION OF THRESHOLD FAILURE LEVELS OF SEMICONDUCTOR DIODES AND TRANSISTORS DUE TO PULSE VOLTAGES

PRELIMINARY REPORT-SEMICONDUCTOR DAMAGE STUDY

PRELIMINARY REPORT II-SEMICONDUCTOR DAMAGE STUDY

FORWARD CURRENT SURGE FAILURE IN SEMICONDUCTOR RECTIFIERS 77-746

ESTIMATES OF SEMICONDUCTOR FAILURE DUE TO MULTIPLE VOLTAGE PULSES

PRELIMINARY REPORT SEMICONDUCTOR DAMAGE STUDY (REVISED)

A MODEL TO PREDICT PULSE POWER FAILURE OF SEMICONDUCTOR DEVICES

BDM FINAL REPORT VOLUME I SEMICONDUCTOR AND NONSEMICONDUCTOR DAMAGE STUDY BDM-375-69-F-0168

PRELIMINARY REPORT AND WORKING DATA FOR SHORT PULSE DURATION SEMICONDUCTOR DAMAGE PROGRAM BDM-375-69-F-0168A

SEMICONDUCTOR VULNERABILITY PHASE II REPORT THEORETICAL ESTIMATES FAILURE LEVELS OF SELECTED SEMICONDUCTOR DIODES AND TRANSISTORS BDM/A-42-69-N

AUTONETICS ELECTRONIC COMPONENTS FAILURE MODE HANDBOOK 58-1329/501

SEMICONDUCTOR AND NON-SEMICONDUCTOR DAMAGE STUDY PERSHING DEVICES BDM-375-69-F-0168

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE *****	DOCUMENT NO./OTHER NO. *****
DETERMINATION OF THRESHOLD FAILURE LEVELS DUE TO HIGH VOLTAGE TRANSIENTS FOR A GA 53933 TRANSISTOR	BDM/A-27-69-M
MECHANISMS OF RADIATION INITIATED SEMICONDUCTOR DEVICE FAILURES	69SD323
SEMICONDUCTOR VULNERABILITY-PHASE I REPORT	BDM/A-37-69-R
SEMICONDUCTOR VULNERABILITY-PHASE II REPORT-THEORETICAL ESTIMATES OF FAILURE LEVELS OF SELECTED SEMICONDUCTOR DIODES AND TRANSISTORS	BDM/A-42-69-M
FORT BELVOIR SEMICONDUCTOR FAILURE PROGRAM REPORT	
DAMAGE LEVEL EVALUATION OF SEMICONDUCTOR COMPONENTS USING ULTIMA FAST RISETIME PULSER	RGE-IN-69-3
SEMICONDUCTOR DAMAGE TEST RESULTS FOR SANDIA DEVICES U2110, U2130, JZ9079	
SEMICONDUCTOR WHO'S TO BLAME FOR FAILURES	
THEORETICAL ESTIMATES OF FAILURE LEVELS OF SELECTED SEMICONDUCTOR DIODES AND TRANSISTORS	BDM/A-34-69R
PULSE POWER FAILURE MODES IN SEMICONDUCTORS	
FINAL REPORT ON SEMICONDUCTOR DAMAGE STUDY PHASE II	NFM/S 66-70-TR
SEMICONDUCTOR VULNERABILITY PHASE III REPORT EXPERIMENTAL THRESHOLD FAILURE LEVELS OF SELECTED DIODES AND TRANSISTORS	BDM/A-75-70-TR
A SURVEY OF SECOND BREAKDOWN PHENOMENA, MECHANISMS AND DAMAGE IN SEMICONDUCTOR JUNCTION DEVICES	HS-TR-70-19-TR
FINAL SUMMARY REPORT ON SEMICONDUCTOR DAMAGE STUDY PHASE II	BDM/A-84-70-TR

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

CONFERENCE PROCEEDINGS ON COMPONENT DEGRADATION FROM TRANSIENT  
INPUTS, SPONSORED BY US ARMY MORILITY EQUIPMENT RESEARCH : DEV. CIR

A SURVEY OF SECOND BREAKDOWN PHENOMENA, MECHANISMS AND DAMAGE IN  
SEMICONDUCTOR JUNCTION DEVICES RG-TR-70-19

USER'S MANUAL FOR THE NETWORK EMP DAMAGE ANALYSIS PROGRAM (NEDAP) RG-TR-70-2

COMPONENT VULNERABILITY

THE REAL CULPRIT IN DIODE FAILURE

PULSE POWER FAILURE MODES IN SEMICONDUCTORS

A PROGRAM TO INVESTIGATE RADIATION INITIATED, CURRENT INDUCED  
FAILURES IN SEMICONDUCTOR DEVICES MEMO 1457-117

THERMAL BREAKDOWN DELAY TIME IN SILICON P-N JUNCTIONS

STATISTICAL COMPONENT DAMAGE STUDY RG-TR-71-1

FINAL SUMMARY REPORT ON SEMICONDUCTOR DAMAGE STUDY-PHASE II HDM/A-84-70-TR

RF BURNOUT IN X-BAND SCHOTTKY MIXERS

METALLIZATION BURNOUT RESEARCH AT THE UNITED STATES AIR FORCE  
ACADEMY AFWL-TR-71-4

MISSILE AND AIRCRAFT COMPONENT VULNERABILITY TO EMP SC-TM-70-902

FAILURE ANALYSIS OF DAMAGED 2N700 TRANSISTORS NN/E-20/71

UNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

AN EXPERIMENTAL INVESTIGATION OF EMP INDUCED TRANSIENT UPSET OF  
INTEGRATED CIRCUITS SC-TM-71 0330

IN-PLACE EMP CRITICAL CIRCUIT THRESHOLD ANALYSIS 02-19693-2

ELECTRICAL PULSE OVERSTRESS EFFECTS IN MICROCIRCUITS NCL-72-6P

SECOND BREAKDOWN AND DAMAGE IN SEMICONDUCTOR JUNCTION DEVICES HG-TM-72-15

SEMICONDUCTOR DEVICE DEGRADATION BY HIGH CURRENT PULSES SC-DC-72-2288

ADAPTATION OF THE P-N JUNCTION BURNOUT MODEL TO CIRCUIT ANALYSIS  
CODES

PULSED-POWER BURNOUT OF INTEGRATED CIRCUITS SAMSO-TR-72-226

A COMPARISON OF RF AND DC - INDUCED DAMAGE TO METAL-SEMICONDUCTOR  
JUNCTIONS TR-2707

LIFE TESTS OF KEMET SOLID TANTALUM CHIP CAPACITORS AT HIGHLY  
ACCELERATED VOLTAGES M72-10

FAILURE THRESHOLD AND RESISTANCE OF THE PROTECTED AND UNPROTECTED  
2N2222 TRANSISTOR IN THE SHORT PULSE WIDTH REGIME PEM-7

SEMICONDUCTOR DEVICE DEGRADATION BY HIGH AMPLITUDE CURRENT PULSES SC-RR-72-0515

INTEGRATED CIRCUIT ELECTRO MAGNETIC SUSCEPTIBILITY INVESTIGATION  
DEVELOPMENT PHASE REPORT MDC D0690

SOLID STATE COMPONENTS RF SUSCEPTIBILITY PROGRAM-PROGRESS REPORT  
FY-72 FVR/VGP<MAC 3900/EMC

DEVELOPMENT OF A SEMICONDUCTOR FAILURE MODEL FOR LIGHTNING INDUCED  
PULSES ATN 72-001

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*  
DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

ELECTRICAL BREAKDOWN AND DISCHARGE IN A VACUUM  
FTD-MT-24-123-71

EMP DAMAGE HARDENING GUIDELINES  
D224-10016-1

THE DEGRADATION OF MOS TRANSISTORS RESULTING FROM JUNCTION AVALANCHE VOL. II  
BREAKDOWN

ANALYSIS OF ELECTRICAL OVERSTRESS FAILURES

ANALYSIS OF FAILURE OF ELECTRONIC CIRCUITS FROM EMP-INDUCED SIGNALS MDL-TR-1615  
REVIEW AND CONTRIBUTION

SECOND BREAKDOWN AND DAMAGE IN JUNCTION DEVICES

MOS DEVICE FAILURE PROGRAM FINAL REPORT C73-1175/501

SCANNING ELECTRON MICROSCOPE EXAMINATION OF METALLIZATION DEFECTS AFWL-TR-72-212

ELECTRO THERMAL OVERSTRESS FAILURE IN MICROELECTRONICS WADC-TR-73-87

TEST PLAN FOR MOS DEVICE FAILURE C73-573/501

THE SUSCEPTIBILITY OF X-BAND POINT CONTACT DIODES TO MICROWAVE  
RADIATION TR-2963

SEMICONDUCTOR VULNERABILITY VOL I THEORETICAL ESTIMATES OF FAILURE AFWL-TR-73-119 VOL I  
LEVELS OF SELECTED SEMICONDUCTOR DIODES AND TRANSISTORS-PHASE II

SEMICONDUCTOR VULNERABILITY VOL II - EMPIRICAL THRESHOLD FAILURE AFWL-TR-73-119 VOL II  
LEVELS OF SELECTED DIODES AND TRANSISTORS - PHASE III

SOLID STATE COMPONENT HF SUSCEPTIBILITY PROGRAM-PROGRESS REPORT FY73 FJR/VGP< HAC 3920



DNA OVERSTRESS REVIEW  
SUBJECT INDEX

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

TITLE  
\*\*\*\*\*

C73-1175/501

PROGRAM FINAL REPORT

MDC E0981

INTEGRATED CIRCUIT ELECTROMAGNETIC SUSCEPTIBILITY INVESTIGATION  
PHASE II INTERIM REPORT 2

NELC/TR 1902

R.F. FAILURE MECHANISMS RELATED TO MICROELECTRONICS PROCESS CONTROL

73SD4254

THEORETICAL AND EXPERIMENTAL STUDIES OF SEMICONDUCTOR DEVICE  
DEGRADATION DUE TO HIGH POWER ELECTRICAL TRANSIENTS

APPLICATION OF TIME DOMAIN METHODS TO INTEGRATED CIRCUIT  
SUSCEPTIBILITY

MDCE0921

INTEGRATED CIRCUIT ELECTROMAGNETIC SUSCEPTIBILITY INVESTIGATION  
PHASE II

SHORT COURSE IN NUCLEAR WEAPON EFFECTS AND SURVIVABILITY OF  
AEROSPACE SYSTEMS

MDAC PAPER WD2280

TECHNIQUES TO DETERMINE SUBSYSTEM LEVEL ELECTROMAGNETIC PULSE  
SUSCEPTIBILITY

VOL. R-22 NO.4

PULSE BURNOUT OF MICROWAVE MIXER DIODES

C73-946/201

EMP DEGRADATION ANALYSIS AND APPLICATION OF EMP FILTERS

ASPECTS OF SEMICONDUCTOR DEVICE DAMAGE DUE TO ELECTRICAL TRANSIENTS  
(DRAFT COPY) BDM/A-199-73-TM

WORK ORDER 2-14 FINAL TECHNICAL REPORT HF RADIO AN/ARC-123 PULSE  
TESTS 2-5170-430E-003

COMPONENT DAMAGE FROM ELECTROMAGNETIC PULSE (EMP) INDUCED TRANSIENTS  
(DRAFT)

MICROWAVE INDUCED DAMAGE AND FAILURE MODES IN LOW FREQUENCY  
TRANSISTORS RELATED TO DEVICE DESIGN AND PROCESS CONTROL

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

TITLE  
\*\*\*\*\*

AN INVESTIGATION OF INTEGRATED CIRCUIT DESTRUCTION BY NOISE PULSES

INTEGRATED CIRCUIT ELECTROMAGNETIC SUSCEPTIBILITY NOTEBOOK

EXPERIMENTAL DAMAGE CONSTANT SUMMARY

BDM/A-49-74-TR-21

EMP SUSCEPTIBILITY OF SEMICONDUCTOR COMPONENTS

BDM/A-110-74-TR

FAILURE ANALYSIS BY STATISTICAL TECHNIQUES (FAST) VOLUME II, USERS  
MANUAL (APPENDICES)

BOUNDING EMP DAMAGE PREDICTION UNCERTAINTIES (PRESENTATION)

BDM/A-27-74-BK

A METHOD FOR THE PREDICTION OF EMP DAMAGE PROBABILITY

BDM/A-9-74-TR

FINAL REPORT ANALYSIS OF COMMUNICATIONS SYSTEMS EQUIPMENT FAILURE  
MODELING

BDM/A-60-74-TR

DEFENSE NUCLEAR AGENCY EMP SEMINAR "SUBSYSTEM AND COMPONENT  
SUSCEPTIBILITY"

CAPACITOR FAILURE TO HIGH LEVEL ELECTRICAL TRANSIENTS DRAFT

TECHNIQUES FOR SCREENING BIPOLAR TRANSISTOR DEGRADATION DUE TO  
IONIZING RADIATION

NADCRANE TR/1024/C74/121

DIELECTRIC BREAKDOWN IN SOLIDS

KG-75-25

B-1 SETA TECHNICAL MEMORANDUM-STATUS OF REVERSE BIAS SEMICONDUCTION  
DAMAGE MODELING

T.M. 7.11/3

DNA EMP HANDBOOK CHAPTER 13 COMPONENT EMP SEMIACTIVITY AND SYSTEM  
JPSET

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*  
DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

PULSE POWER DAMAGE CHARACTERISTICS OF ELECTRICAL RESISTORS	D224-13058-1
PULSE POWER DAMAGE CHARACTERISTICS OF ELECTRICAL RESISTORS FINAL TECHNICAL REPORT	75SDS4213
PULSE POWER DAMAGE CHARACTERISTICS OF ELECTRICAL RESISTORS EXPERIMENTAL DATA REPORT	75SDS4214
PULSE POWER DAMAGE CHARACTERISTICS OF ELECTRICAL RESISTORS	D224-13058-1
ADDENDUM TO EMP SUSCEPTIBILITY OF SEMICONDUCTOR COMPONENTS	D224-13042-2
PULSED VOLTAGE FAILURE LEVELS OF CAPACITORS GENERAL TEST PLAN	75SDS4241
ELECTRICAL PULSE BURNOUT OF TRANSISTORS IN INTENSE IONIZING RADIATION, PREPRINT	SAND 75-5222
EMP SUSCEPTIBILITY OF INTEGRATED CIRCUITS	BDM/A-69-75-1R-R1
METHODS FOR ENSURING SEMICONDUCTOR METALLIZATION SURVIVABILITY FIRST DRAFT	BDM/A-75-10-14
FINAL REPORT RESISTOR SUSCEPTIBILITY SURVEY	75 SOS 4279
EMP RESPONSE : DAMAGE MODELING OF DIODES, JUNCTION FIELD EFFECT TRANSISTOR DAMAGE TESTING AND SEMICONDUCTOR DEVICE FAILURE ANALYSIS	HDL-TM-75-25
CAPACITOR FAILURE DUE TO HIGH LEVEL ELECTRICAL TRANSIENTS	RADC-TR-75-17
DEGRADATION OF MONOLITHIC SEMICONDUCTOR DEVICES BY HIGH AMPLITUDE CURRENT PULSES	BER 200-93
DETERMINATION OF SEMICONDUCTOR JUNCTION VULNERABILITY TO SECOND BREAKDOWN	

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

TITLE  
\*\*\*\*\*

RF FAILURE PREDICTION FOR MOS 4001 AND 4011 INTEGRATED CIRCUITS - TN 3107  
WORKING PAPER

FAILURE MECHANISMS IN SILICON SEMICONDUCTORS RADC-IDR-62-533

PULSED POWER BURNOVT OF INTEGRATED CIRCUITS SAMS0-TR-72-226

STUDY OF THE COMBINED EFFECTS OF IONIZATION, NEUTRONS, TEMPERATURE SLA-73-402  
AND TIME ON BIPOLAR DEVICES.

SEMICONDUCTOR CIRCUIT FAILURE AND PROTECTION IMPLEMENTATION SCHEMES PEM-21

THE DAMAGE SUSCEPTIBILITY OF INTEGRATED CIRCUITS TO A SIMULATED IEMP TRANSIENT

ON THE NECESSARY AND SUFFICIENT CONDITIONS (THRESHOLDS) FOR DAMAGE OF SEMICONDUCTOR JUNCTIONS FROM ELECTRICAL TRANSIENTS

A METHOD TO PREDICT SEMICONDUCTOR JUNCTION FAILURE DUE TO ELECTRICAL OVERSTRESS

APPENDIX A-2 BURNOVT CHAPTER OF A REPORT TITLED JFET HARDENING AND HIGH DOSE RATE STUDY AFCRL-72-0335

DETERMINATION OF SEMICONDUCTOR FAILURE LEVELS DUE TO HIGH VOLTAGE TRANSIENTS

SHORT PULSE WIDTH FAILURE LEVEL CHARACTERIZATION FOR THE 2N3821 JUNCTION FIELD EFFECT TRANSISTOR PEM-24

MODELING AND SIMULATION TECHNIQUES FOR DAMAGE PREDICTION AND SYSTEM ASSESSMENT

USE OF THE FAIRCHILD 600 TO DETERMINE DAMAGE PARAMETERS

CIRCUIT DAMAGE ANALYSIS TECHNIQUE

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

TITLE  
\*\*\*\*\*

SEMICONDUCTOR DAMAGE STUDY

SEMICONDUCTOR DAMAGE CONSTANTS

SEMICONDUCTOR DEVICE DAMAGE IN AN EMP ENVIRONMENT

SECTION II DISCRETE DAMAGE TESTS

CHAPTER 7 SUBSYSTEM DAMAGE SUSCEPTIBILITY

0224-10005-1

DRAFT OF CHAPTER 13 EMP COMPONENT SENSITIVITY AND SYSTEM UPSET  
ADVANCED RELEASE

VME INDUCED ELECTRICAL OVERSTRESS JUNCTION FAILURES IN SEMICONDUCTOR  
A PROPOSED PROGRAM

COMPUTER ANALYSIS OF HOT SPOT FORMATION IN POWER TRANSISTORS

DEVICE DEGRADATION BY HIGH AMPLITUDE CURRENTS AND RESPONSE  
CHARACTERISTICS OF DISCRETE RESISTORS

MECHANISMS OF RADIATION AND PULSED ELECTRICAL FAILURE IN  
SEMICONDUCTOR ELECTRONICS

MEMO 1457-114

IN-PLACE EMP WING III THRESHOLD VARIATION SURVEY

02-19693-3

SOME COMMENTS ON THE MODELS USED TO PREDICT SEMICONDUCTOR DAMAGE  
CONSTANTS

SECTION II A MODEL TO PREDICT POWER FAILURE OF SEMICONDUCTOR DEVICES

\*\*\*\*\*FETS

A COMPUTER AIDED ANALYSIS MODEL FOR THE JUNCTION FIELD EFFECT

SC-DR-70-366



DNA OVERSTRESS REVIEW  
SUBJECT INDEX

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

TITLE  
\*\*\*\*\*

EMP RESPONSE : DAMAGE MODELING OF DIODES, JUNCTION FIELD EFFECT TRANSISTOR DAMAGE TESTING AND SEMICONDUCTOR DEVICE FAILURE ANALYSIS	75 SDS 4279
APPENDIX A-2 BURNOUT CHAPTER OF A REPORT TITLED JFET HARDENING AND HIGH DOSE RATE STUDY	AFCRL-72-0335
SHORT PULSE WIDTH FAILURE LEVEL CHARACTERIZATION FOR THE 2N3821 JUNCTION FIELD EFFECT TRANSISTOR	PEM-24

\*\*\*\*\*HARDENING

RADIATION HARDENED AVIONICS GAIN INTEREST

APPROACHES TO SYSTEM HARDENING

3SR-399

NUCLEAR ELECTROMAGNETIC PULSE PROTECTIVE MEASURES APPLIED TO A TYPICAL COMMUNICATION SHELTER

N-1091

EMP THREAT AND PROTECTIVE MEASURES

TR-61

GATE PROTECTION OF MOS DEVICES

METHODS, DEVICES AND CIRCUITS FOR THE EMP HARDENING OF ARMY ELECTRONICS

ECOM-0085-F

DESIGNING ULTRAHIGH BIPOLAR TRANSISTORS

ECOM CONTRACT DAAB07-70-C-0085 MONTHLY AND QUARTERLY REPORTS (BOUND TOGETHER)

LIGHTNING ARRESTOR-CONNECTOR FEASIBILITY STUDY

SC-RR-71 0180

EMP PROTECTIVE SYSTEMS

TR-61-B

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

SIMPLIFIED MODELING OF INTEGRATED CIRCUITS FOR RADIATION PERFORMANCE PREDICTION	AFWL-TR-72-42
METHODS DEVICES AND CIRCUITS FOR THE EMP HARDENING OF ARMY ELECTRONICS	ECOM-0275-S
METHODS, DEVICES AND CIRCUITS FOR THE EMP HARDENING OF ARMY ELECTRONICS	BDM/A-119-72-TR
METHODS, DEVICES AND CIRCUITS FOR THE EMP HARDENING OF ARMY ELECTRONICS	ECOM-0275-F
FINAL REPORT ON THE EVALUATION OF SURGE PROTECTION DEVICES FOR EMP HARDENING APPLICATIONS	C72-712/201
EMP PROTECTION ENGINEERING THE NEED FOR DOCUMENTATION	PEM-1
SHIELDING EFFECTIVENESS OF THE LIQUID TIGHT FLEXIBLE CONDUIT FROM TRANSIENT TESTS	PEM-3
FINAL REPORT ON THE EVALUATION OF SURGE PROTECTION DEVICES FOR EMP HARDENING APPLICATION REVISION NO.1	C72-712/201
EMP DAMAGE HARDENING GUIDELINES	D224-10016-1
DESIGN GUIDELINES FOR EMP HARDENING OF AERONAUTICAL SYSTEMS (DRAFT)	C72-451/201
EMP PROTECTIVE SYSTEMS	TR-61-B
EMP PROTECTION FOR EMERGENCY OPERATING CENTERS	TR-61A
SUPPRESSION DEVICES USED FOR EMP PROTECTION	BDM/A-224-72-TR
EMP UPSET HARDENING GUIDELINES	D22A-10016-2

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

FEASIBILITY STUDY FOR EMP TERMINAL PROTECTION	TPD 003
DESIGN GUIDELINES FOR EMP HARDENING OF AERONAUTICAL SYSTEMS	AFWL-TR-73-117
EMP HARDENED CMOS CIRCUIT	HDL-TR-192-1
EMP SURGE SUPPRESSION CONNECTORS UTILIZING METAL OXIDE VARISTORS	73SD4293
EMP ELECTRONIC DESIGN HANDBOOK	0224-10019-1
EMP HARDENING OF G.F.E.	0224-10023-1
EMP SHIELDING EFFECTIVENESS AND MIL STD. 285	HDL-TR-1636
EMP HARDENING APPROACH FOR SAM-D	PEM-35
A GUIDE TO THE USE OF SPARK GAPS FOR ELECTROMAGNETIC PULSE (EMP) PROTECTION	JES-198-2.54
ASAP-1 FINAL REPORT	0224-12013-1
EMP DEGRADATION ANALYSIS AND APPLICATION OF EMP FILTERS	C73-946/201
ENGINEERING DESIGN GUIDELINES FOR EMP HARDENING OF NAVAL MISSILES AND AIRPLANES	AMRC-R-17
FEASIBILITY STUDY OF ELECTROSTATIC PROTECTION FOR ELECTROEXPLOSIVE DEVICES	74SD4237
EMP HARDENED CMOS CIRCUITS-FINAL REPORT	

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE *****	DOCUMENT NO./OTHER NO. *****
CHARACTERISTICS AND APPLICATIONS OF METAL OXIDE VARISTORS FOR EMP HARDENING	PEM-43
EMP TRANSIENT SUPPRESSION	PEM-31
EMP SURGE SUPPRESSION CONNECTORS UTILIZING METAL OXIDE VARISTORS	HDL-TR-177-1
DEVELOPMENT OF DISC TRANSORBS FOR TPO APPLICATIONS IN EMP SUPPRESSION	HDL-CR-143-1
ADVANCED ELECTRO-OPTICAL SYSTEM HARDENING	HDL-CR-047-2
SHIELDING EVALUATION OF BRAIDED CABLE SHEATHS AND MULTICONDUCTOR CABLES USING PULSE TEST METHODS	PEM-13
HYBRID SPARK GAP SURGE ARRESTORS: A HIGH FREQUENCY RECEIVER SYSTEM ARRESTOR FOR LIGHTNING AND EMP PROTECTION	PEM-42
ENGINEERING TECHNIQUES FOR ELECTROMAGNETIC PULSE HARDNESS TESTING	UNA3332F
CMOS RADIATION HARDENING	P75-116
AIRBORNE COMMAND POST AABNCP ELECTRONIC SYSTEM DETAILED PROGRAM PLAN CDRL A018 INTERIM REPORT	
B-1 EMP SUBSYSTEM ASSESSMENT DATA, HF RADIO AN/ARC-123	D224-13022-7
B-1 EMP SUBSYSTEM ASSESSMENT DATA UHF RADIO AN/ARC-109	D224-13022-8
SURVEY OF CIRCUIT ELEMENTS USED FOR REDUCTION OF AND PROTECTION FROM SYSTEMS GENERATED ELECTRO MAGNETIC PULSE EFFECTS	AFWL-TR-74-309
KEY SUPPRESSION DEVICES PARAMETERS FOR EMP HARDENING	PEM-38

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

TITLE  
\*\*\*\*\*

VOLTAGE CLAMPING LEVELS FOR SEVERAL "TRANSORB" TRANSIENT SUPPRESSION DEVICES PEM-33

ADDENDUM TO EMP SUSCEPTIBILITY OF SEMICONDUCTOR COMPONENTS D224-13042-2

ADDENDUM TO EMP SUSCEPTIBILITY OF SEMICONDUCTOR COMPONENTS D224-13042-2

METHODS FOR ENSURING SEMICONDUCTOR METALLIZATION SURVIVABILITY  
FIRST DRAFT

DNA HARDNESS ASSURANCE PROGRAM PLAN (DRAFT)

INTEL-RT 8106 056

NUCLEAR RADIATION TESTS OF EMP HARDENED CMOS CIRCUITS-FINAL REPORT

SOME HANDBOOK REFERENCES AND A SUMMARY FOR EMP ENGINEERING AND DESIGN PRINCIPLES PUBLISHED BY HELIX LABORATORIES PEM-37

MINUTES OF THE MICROELECTRONICS HARDNESS ASSURANCE STANDARDIZATION MEETING

ELECTRONICS RADIATION HARDNESS ASSURANCE TECHNIQUES STUDY

AFWL-TR-73-134

DEVELOPMENT OF A NON-DESTRUCTIVE RADIATION EFFECTS PREDICTION TECHNIQUE

HRLR-3586

NUCLEAR RADIATION HARDENING FOR ELECTRONIC COMPONENTS

LMSC A956-451

SEMICONDUCTOR CIRCUIT FAILURE AND PROTECTION IMPLEMENTATION SCHEMES PEM-21

EMP TRANSIENT PROTECTION

DEM-31

APPENDIX A-2 BURROJT CHAPTER OF A REPORT TITLED JFET HARDENING AND HIGH DOSE RATE STUDY AFCML-72-0335



DNA OVERSTRESS REVIEW  
SUBJECT INDEX

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

TITLE  
\*\*\*\*\*

DNA EMP HANDBOOK CHAPTER 4 SHIELDING ANALYSIS

HARDENING OF MJ577 SPACECRAFT AGAINST THE JUPITER RADIATION BELTS

CURRENT CROWDING IN HARDENED POWER TRANSISTORS

SOME ASPECTS OF EMP HARDNESS ASSURANCE

PEM-23

TEST REPORT ON CONDUCTED CURRENT SHIELDING EFFECTIVENESS OF BAYUNET  
CONNECTOR SHELLS WITH FINGERS

PEM-12

REPORT NUMBER JPD 002 FEASIBILITY STUDY INTO THE USE OF  
TRANSZORBS FOR EMP SUPPRESSION

TPD 002

METHODS, DEVICES, AND CIRCUITS FOR THE EMP HARDENING  
OF ARMY ELECTRONICS (REPORTS<FINAL,8/70,1/71,3/71,5/71,2/72,3/72,

HDM/A-119-72-TR

\*\*\*\*\*

MICROELECTRONIC PACKAGING CONCEPTS

RADC-TR-65-61

THERMAL MANAGEMENT OF INTEGRATED CIRCUITS

A COMPUTER MODEL FOR INTEGRATED CIRCUIT TRANSISTORS INCLUDING  
SUBSTRATE INTERACTIONS

THEORETICAL AND EXPERIMENTAL STUDY OF LATCH UP IN JUNCTION ISOLATED  
INTEGRATED CIRCUITS

FR-69-10-227

MICROELECTRONIC TECHNIQUES AND REQUIREMENTS FOR THE SPECIAL WEAPONS  
CENTER MICROELECTRONICS FACILITY-FINAL REPORT

EE-172(70)KAFB-076

PULSE POWER TESTING OF MICROELECTRONICS

RADC-TR-71-59

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

TITLE  
\*\*\*\*\*

GATE PROTECTION OF MOS DEVICES

PULSE POWER TESTING OF MICROCIRCUITS

AN EXPERIMENTAL INVESTIGATION OF EMP INDUCED TRANSIENT UPSET OF  
INTEGRATED CIRCUITS

PULSE POWER TESTING OF MICROCIRCUITS

SIMPLIFIED MODELING OF INTEGRATED CIRCUITS FOR RADIATION  
PERFORMANCE PREDICTION

HIGH POWER PULSE TESTING OF INTEGRATED CIRCUITS

ELECTRICAL PULSE OVERSTRESS EFFECTS IN MICROCIRCUITS

PULSED-POWER BURNOUT OF INTEGRATED CIRCUITS

INTEGRATED CIRCUIT ELECTRO MAGNETIC SUSCEPTIBILITY INVESTIGATION  
DEVELOPMENT PHASE REPORT

ELECTRO THERMAL OVERSTRESS FAILURE IN MICROELECTRONICS

DETAILED TEST PLAN-INTEGRATED CIRCUIT TEST

TEST PLAN FOR MOS DEVICE FAILURE

PLAN FOR PULSE POWER TESTING OF MOS DEVICES

WORK ORDER 2-14 INTEGRATED CIRCUITS TEST PROGRAM-FINAL REPORT

SC-TM-71 0330

RADC-TR-71-59

AFWL-TR-72-42

RG-72-22

NCL-72-GP

SAMS0-TR-72-22b

MDC D0690

RADC-TR-73-97

BDM/A-48-73-TR

C73-573/501

C73-5731501

BDM/A-98-73-TR

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*  
DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

RESPONSE OF INTEGRATED CIRCUITS TO A SIMULATED EMP ENVIRONMENT HDL-TR-1649

EMP HARDENED CMOS CIRCUIT HDL-TR-192-1

PROGRAM FINAL REPORT C73-1175/501

INTEGRATED CIRCUIT ELECTROMAGNETIC SUSCEPTIBILITY INVESTIGATION  
PHASE II INTERIM REPORT 2 MDC E0981

R.F. FAILURE MECHANISMS RELATED TO MICROELECTRONICS PROCESS CONTROL NELC/TR 1902

APPLICATION OF TIME DOMAIN METHODS TO INTEGRATED CIRCUIT  
SUSCEPTIBILITY

INTEGRATED CIRCUIT ELECTROMAGNETIC SUSCEPTIBILITY INVESTIGATION  
PHASE II MDCE0921

COMBINED DOCUMENTATION WORK ORDER 2-14

IC SIMULATES POWER TRANSISTOR

INTEGRATED CIRCUIT ELECTROMAGNETIC SUSCEPTIBILITY INVESTIGATION  
PHASE II-BIPOLAR NAND GATE STUDY MDC E1123

AN INVESTIGATION OF INTEGRATED CIRCUIT DESTRUCTION BY NOISE PULSES

INTEGRATED CIRCUIT MODEL DEVELOPMENT FOR EMP

EMP HARDENED CMOS CIRCUITS-FINAL REPORT

INTEGRATED CIRCUIT ELECTROMAGNETIC SUSCEPTIBILITY NOTEBOOK

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

DOCUMENT NO. 701-HER NO.  
\*\*\*\*\*

TITLE  
\*\*\*\*\*

BDM/A-112-74-TR

AFWL-TR-73-272

SAMSO-TR-75-281

BDM/A-69-75-TR-R1

NBS SPEC PUB. 400-15

TN 3107

ECOM-75-1344-1

SAMSO-TR-72-226

INTEGRATED CIRCUIT EMP DATA SUMMARY

SIMPLIFIED MICROCIRCUIT MODELING

EMP SUSCEPTIBILITY OF INTEGRATED CIRCUITS

STUDY OF IEMP EFFECTS ON OPERATIONAL AMPLIFIER CIRCUITS

EMP SUSCEPTIBILITY OF INTEGRATED CIRCUITS

NUCLEAR RADIATION TESTS OF EMP HARDED CMOS CIRCUITS-FINAL REPORT

MINUTES OF THE MICROELECTRONICS HARDNESS ASSURANCE STANDARDIZATION  
MEETING

SEMICONDUCTOR MEASUREMENT TECHNOLOGY< AMPA/NBS WORKSHOP III TEST  
PATTERNS FOR INTEGRATED CIRCUITS

RF FAILURE PREDICTION FOR MOS 4001 AND 4011 INTEGRATED CIRCUITS -  
WORKING PAPER

COMPUTER AIDED ENGINEERING OF SEMICONDUCTOR INTEGRATED CIRCUITS

PULSED POWER BURNOUT OF INTEGRATED CIRCUITS

THE DAMAGE SUSCEPTIBILITY OF INTEGRATED CIRCUITS TO A SIMULATED IEMP  
TRANSIENT

SIMPLIFIED MICROCIRCUIT MODELING

EFFECTIVE SCREENING OF INTEGRATED CIRCUITS

ONA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

PULSE DAMAGE DATA FROM INTEGRATED CIRCUITS AND ELECTRONIC PARTS

\*\*\*\*\*IFMP

A REVIEW OF INTERNAL IEMP TECHNOLOGY

AFWL-TR-71-47

RESPONSE OF INTEGRATED CIRCUITS TO A SIMULATED IEMP ENVIRONMENT

HDL-TR-1649

SURVEY OF CIRCUIT ELEMENTS USED FOR REDUCTION OF AND PROTECTION  
FROM SYSTEMS GENERATED ELECTRO MAGNETIC PULSE EFFECTS

AFWL-TR-74-309

STUDY OF IEMP EFFECTS ON OPERATIONAL AMPLIFIER CIRCUITS

SAMS0-TR-75-281

HDL IEMP EXPERIMENT SUMMARY

THE DAMAGE SUSCEPTIBILITY OF INTEGRATED CIRCUITS TO A SIMULATED IEMP  
TRANSIENT

\*\*\*\*\*INSTRUMENTATION

DESIGN STUDIES FOR ULTRA FAST, LOW IMPEDANCE, HIGH PEAK POWER  
PULSED SYSTEMS

AFWL-TR-65-21

THE SCANNING ELECTRON MICROSCOPE AS A MEANS OF INVESTIGATING  
"SECOND BREAKDOWN" AND SIMILAR PHENOMENA

SINGLE PULSE DELAY LINE

FTD-HT-23-333-69

EXPEDIENT METHOD OF OBTAINING INTERFACE STATE PROPERTIES FROM MIS  
CONDUCTANCE MEASUREMENTS



UNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*  
DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

FRANKLIN INSTITUTE REPORT ON EED PULSE TESTING	F-C2540
LASER TRIGGERED SWITCHING STUDY	AFWL-TR-69-87
SPARK GAP SIMULATES A-BOMB EMP	
ELECTROMAGNETIC PULSE SIMULATOR	
INSTRUMENTATION FOR NUCLEAR WEAPONS EFFECTS SIMULATION SYMPOSIUM- VOLUME I-ELECTROMAGNETIC PULSE	AFS-C-TR-70-S VOL. I
TRANSFORMER - TYPE HIGH - CURRENT ACCELERATOR	JPRS 50119
THE MODIFIED SIEGE 1.2 PULSE DRIVER	AFWL-TR-71-49
ELECTROMAGNETIC PULSE SENSOR HANDBOOK VOLUME I	
ELECTROMAGNETIC PULSE INSTRUMENTATION HANDBOOK-VOLUME I	
NWL MICROWAVE SUSCEPTIBILITY MEASUREMENT SYSTEMS FOR SOLID STATE COMPONENTS	TN-F/97-71
ELECTROMAGNETIC PULSE SENSOR HANDBOOK	AFWL MEASUREMENT 1-1
CHARACTERIZATION AND MEASUREMENT OF THE BASE AND EMITTER RESISTANCE OF BIPOLAR TRANSISTORS	VOL SC-7 NO.6
B-52/VPD GENERAL TEST PLAN	D224-10000-1
FINAL REPORT OF THE B-1 EMP SCALE MODEL FEASIBILITY STUDY	C72-302/201

CNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE *****	DOCUMENT NO./OTHER NO. *****
TECHNIQUES FOR MEASUREMENT OF THE VPD SPECTRUM & A TRADE STUDY	AL-897(72)
SCANNING ELECTRON MICROSCOPE EXAMINATION OF METALLIZATION DEFECTS	AFWL-TR-72-212
VPD/AGM-28 GENERAL TEST PLAN	C73-356-201
VPD/AGM-28A DETAILED TEST PLAN LONG WIRE BASELINE EXPERIMENT	C73-312.1/201
VPD/AGM-28 DETAILED TEST PLAN B-52G/AGM-28A BASELINE EXPERIMENT	C73-312.2/201
VPD/AGM-28A DETAILED TEST PLAN EXTERNAL COUPLING EXPERIMENT	C73-312.3/201
OBJECTIVES OF THE F8-111 A EMP TEST IN ARES	C73-424/201
TEST REPORT FOR EC-135C INTERNAL COUPLING MEASUREMENTS	0180-17726-1
THE DETERMINATION OF SEMICONDUCTOR JUNCTION VULNERABILITY TO SECOND BREAKDOWN BY LOW ENERGY ELECTRICAL MEASUREMENTS	155-93
SPECIAL DEVICES, TEST STRUCTURES, AND HYBRID CIRCUITS FOR SPECIAL ENVIRONMENTS	HDL-TR-003-1
INTEGRATED CIRCUIT ELECTROMAGNETIC SUSCEPTIBILITY NOTEBOOK	
SEMICONDUCTOR MEASUREMENT TECHNOLOGY QUARTERLY REPORT	400-12
SHIELDING EVALUATION OF BRAIDED CABLE SHEATHS AND MULTICONDUCTOR CABLES USING PULSE TEST METHODS	PEN-13
USERS MANUAL FOR THE PUDU INTERFACE BOX (PIB)	0224-13037-1

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

TITLE  
\*\*\*\*\*

ENGINEERING TECHNIQUES FOR ELECTROMAGNETIC PULSE HARDNESS TESTING	DNA3332F
F-111/ARES DETAIL TEST PLAN VOL.222, EXTERNAL COUPLING AND DELIBERATE ANTENNA EXPERIMENTS	D224-13008-3
SRAM/ARES DETAIL TEST PLAN	D224-13008-4
FINAL REPORT FOR EMP INSTRUMENTATION PROJECT (DNAIACMO 75-815) MAGNETIC THIN FILM SENSORS UNIV. OF CALIF. / LIVERMORE	UCID-16945
CABLE AND CONNECTOR SHIELDING ATTENUATION AND TRANSFER IMPEDANCE MEASUREMENT USING QUADRAXIAL AND QUINTAXIAL TEST METHODS	DEM-45
THE LLL TRANSIENT ELECTROMAGNETICS-MEASUREMENT FACILITY	PEM-47
SUBSYSTEM TEST METHODOLOGY FOR THE AFWL DIRECT DRIVE LABORATORY	D224-13057-1
DTP B-1 SCALE MODEL ALECS, SEC.6 FINAL DETAILED TEST PLAN	D224-13006-1
B-52 G/AGM-28A/VPD EXPERIMENT TECHNICAL REPORT VOLUME II DRAFT FINAL REPORT	D224-13069-2
VERTICALLY POLARIZED DIPOLE (VPD) R-52G/AGM-28A TECHNICAL REPORT VOLUME I (DRAFT)	D224-13069-1
SEMICONDUCTOR MEASUREMENT TECHNOLOGY< ARPA/NBS WORKSHOP III TEST PATTERNS FOR INTEGRATED CIRCUITS	NBS SPEC PUB.400-15
USE OF THE FAIRCHILD 600 TO DETERMINE DAMAGE PARAMETERS	
SUBNANOSECOND RISETIME MULTIKILOVOLT PULSE GENERATOR	

\*\*\*\*\*MATERIALS

ELECTRON MULTIPLICATION IN SILICON AND GERMANIUM

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

AVALANCHE BREAKDOWN IN GERMANIUM

SOLID SOLUBILITIES OF IMPURITY ELEMENTS IN GERMANIUM AND SILICON

IMPURITY REDISTRIBUTION AND JUNCTION FORMATION IN SILICON BY  
THERMAL OXIDATION

RESISTIVITY OF BULK SILICON AND OF DIFFUSED LAYERS IN SILICON

AVALANCHE BREAKDOWN VOLTAGES OF ABRUPT AND LINEARLY GRADED P-N  
JUNCTIONS IN GE, SI, GaAs AND GAP

SURFACE ASPECTS OF THE THERMAL DEGRADATION OF GSAS P-N JUNCTION LASER  
AND TUNNEL DIODES

PHYSICAL INVESTIGATION OF THE MESOPLASMA IN SILICON

CALCULATIONS OF CUTOFF FREQUENCY, BREAKDOWN VOLTAGE, AND CAPACITANCE  
FOR DIFFUSED JUNCTIONS IN THIN EPITAXIAL SILICON LAYERS

SILICON POWER DEVICE MATERIALS PROBLEMS

RESISTIVITY, MOBILITY AND IMPURITY LEVELS IN GEAS, GE AND SI AT  
300 DEG. K

RADIATION EFFECTS ON GALLIUM ARSENIDE DEVICES AND SCHOTTKY DIODES AFML-TR-68-31 VOL222

SILICON NITRIDE AS A MASK IN PHOSPHORUS DIFFUSION

A CENTER OF COMPETENCE IN SOLID STATE MATERIALS AND DEVICES AFCML-71-0309

BUCKLING OF THERMALLY GROWN SiO<sub>2</sub> THIN FILMS

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

SYNTHESIS OF GENERAL IMPURITY PROFILES USING A TWO-STEP  
DIFFUSION PROCESS

PERIPHERAL AND DIFFUSED LAYER EFFECTS ON DOPING PROFILES

FILAMENTATION IN SILICON-ON-SAPPHIRE HOMOGENEOUS THIN FILMS

PERMITTIVITY AND PERMEABILITY OF METAL OXIDE VARISTORS

HDL-TM-73-37

DIELECTRIC BREAKDOWN IN SOLIDS

RG-75-25

SOME TEMPERATURE ASPECTS OF MOS MATERIALS

HDL-TM-75-11

AN EVALUATION OF SILICON ON SAPPHIRE TECHNOLOGY

SECONDARY BREAKDOWN IN GERMANIUM GOLD-BONDED DIODES

SAMSO STANDARD- ELECTRONIC PARTS, MATERIALS AND PROCESSES FOR SPACE SAMSO-STD 73-2C  
AND MISSILE APPLICATIONS, STANDARD CONTROL PROGRAM FOR

\*\*\*\*\*MICROWAVE

ANALYSIS OF THE TEMPERATURE RISE IN PIN DIODES CAUSED BY MICROWAVE  
PULSE DISSIPATION

NWL MICROWAVE SUSCEPTIBILITY MEASUREMENT SYSTEMS FOR SOLID STATE  
COMPONENTS TN-F/97-71

THE SUSCEPTIBILITY OF X-BAND POINT CONTACT DIODES TO MICROWAVE  
RADIATION TR-2963

RF FAILURE PREDICTION FOR MOS 4001 AND 4011 INTEGRATED CIRCUITS -  
WORKING PAPER TV 3107



DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

\*\*\*\*\*MISSILES

SEMICONDUCTOR AND NON-SEMICONDUCTOR DAMAGE STUDY PERSHING DEVICES RDM-375-69-F-015H

MINUTEMAN III RE-ENTRY SYSTEM-ALECS-5 PROGRAM PIECE PARTS TEST SUPPORTS-FINAL REPORT 70SD401

MISSILE AND AIRCRAFT COMPONENT VULNERABILITY TO EMP SC-IM-70-902

ELECTROMAGNETIC PULSE HANDBOOK FOR MISSILES AND AIRCRAFT IN FLIGHT

EMP HARDENING APPROACH FOR SAM-D PEM-35

ENGINEERING DESIGN GUIDELINES FOR EMP HARDENING OF NAVAL MISSILES AND AIRPLANES AMRC-R-17

SRAM/ARES DETAIL TEST PLAN 0224-13008-4

F-111/ARES DETAIL TEST PLAN, VOLUME V PHASE II INTEGRATED TEST PLAN (FINAL) 0224-13008-5

SAMSO STANDARD- ELECTRONIC PARTS, MATERIALS AND PROCESSES FOR SPACE AND MISSILE APPLICATIONS, STANDARD CONTROL PROGRAM FOR SAMSO-STD 73-2C

\*\*\*\*\*MISSILE

SAMSO STANDARD- LIST OF PREFERRED PARTS FOR SPACE AND MISSILE SYSTEM SAMSO-STD 73-4 A

\*\*\*\*\*NON-DESTRUCTIVE SCREENING

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

\*\*\*\*\*

DESIGN STUDIES FOR ULTRA FAST, LOW IMPEDANCE, HIGH PEAK POWER PULSED SYSTEMS	AFWL-TR-65-21
INPUT POWER INDUCED THERMAL EFFECTS RELATED TO TRANSITION TIME BETWEEN AVALANCHE AND SECOND BREAKDOWN IN P-N SILICON JUNCTIONS	VOL. EC-13 NOS. 8/9
SOME NEW ASPECTS OF THERMAL INSTABILITY OF THE CURRENT DISTRIBUTION IN POWER TRANSISTORS	
EXPERIMENTAL DEMONSTRATION AND THEORY OF A CORRECTIVE TO SECOND BREAKDOWN IN SI POWER TRANSISTORS	
THERMAL INSTABILITY LIMITING POWER DISSIPATION IN TRANSISTORS	
A MODEL TO PREDICT PULSE POWER FAILURE OF SEMICONDUCTOR DEVICES	
TREES ON POWER HANDLING EQUIPMENT	
PULSE POWER FAILURE MODES IN SEMICONDUCTORS	
HIGH POWER EFFECTS IN SEMICONDUCTOR COMPONENTS	
PULSE POWER FAILURE MODES IN SEMICONDUCTORS	
PULSE POWER TESTING OF MICROCIRCUITS	RADC-TR-71-54
SPECIAL REPORT ON POWER TRANSISTORS	
PULSE POWER TESTING OF MICROCIRCUITS	RADC-TR-71-54

DVA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*  
DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

HIGH POWER PULSE TESTING OF INTEGRATED CIRCUITS	WG-72-22
PULSED-POWER BURNOJT OF INTEGRATED CIRCUITS	SAMSO-TR-72-226
PLAN FOR PULSE POWER TESTING OF MOS DEVICES	C73-5731501
THEORETICAL AND EXPERIMENTAL STUDIES OF SEMICONDUCTOR DEVICE DEGRADATION DUE TO HIGH POWER ELECTRICAL TRANSIENTS	73SD4259
FOCUS ON POWER SEMICONDUCTORS	NO. 23 VOL. 21
PULSE POWER DAMAGE CHARACTERISTICS OF ELECTRICAL RESISTORS	D224-13058-1
PULSE POWER DAMAGE CHARACTERISTICS OF ELECTRICAL RESISTORS FINAL TECHNICAL REPORT	75SDS4213
PULSE POWER DAMAGE CHARACTERISTICS OF ELECTRICAL RESISTORS EXPERIMENTAL DATA REPORT	75SDS4214
PULSE POWER DAMAGE CHARACTERISTICS OF ELECTRICAL RESISTORS	D224-13058-1
ELECTROMAGNETIC PULSE HANDBOOK FOR ELECTRIC POWER SYSTEMS	DVA 3466F
PULSED POWER BURNOJT OF INTEGRATED CIRCUITS	SAMSO-TR-72-226
SECTION II A MODEL TO PREDICT POWER FAILURE OF SEMICONDUCTOR DEVICES A COMPUTER MODEL FOR LATERAL THERMAL INSTABILITIES IN POWER TRANSISTORS	

\*\*\*\*\*PREDICTION

SIMPLIFIED MODELING OF INTEGRATED CIRCUITS FOR RADIATION  
AFWL-TR-72-62

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*  
DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

DEVELOPMENT OF A NON-DESTRUCTIVE RADIATION EFFECTS  
PREDICTION TECHNIQUE  
BRLR-3586

\*\*\*\*\*RADIATION

EXPERIMENTAL INVESTIGATION OF THE PERMANENT EFFECTS OF RF RADIATION  
IN X-BAND ON ELECTRONIC COMPONENTS  
T9-1399

RADIATION EFFECTS ON GALLIUM ARSENIDE DEVICES AND SCHOTTKY DIODES  
AFWL-TR-68-31 VOL222

MECHANISMS OF RADIATION INITIATED SEMICONDUCTOR DEVICE FAILURES  
69SD323

RADIATION HARDENED AVIONICS GAIN INTEREST

TREES ON POWER HANDLING EQUIPMENT

INSTRUMENTATION FOR NUCLEAR WEAPON EFFECTS SIMULATION SYMPOSIUM-  
VOLUME II - TRANSIENT RADIATION EFFECTS ON ELECTRONIC SYSTEMS  
AFSNC-TR-70-5 VOL.II

RADIO FREQUENCY NOISE PRODUCED BY HIGH INTENSITY FLASH X-RAY  
FACILITIES  
HDL-TM-M/-12

COAXIAL CABLE RESPONSE TO IONIZING RADIATION FROM FX-100 AND PR-1590 G0436  
FLASH X-RAY MACHINES

COMBINED EMP AND IONIZATION EFFECTS

A PROGRAM TO INVESTIGATE RADIATION INITIATED, CURRENT INDUCED  
FAILURES IN SEMICONDUCTOR DEVICES  
MEMO 1H57-117

SYNERGISTIC CONSIDERATIONS FOR THE SECOND BREAKDOWN OF A P-N  
JUNCTION IN A PULSED ELECTRICAL AND PULSED RADIATION ENVIRONMENT  
MEMO 1H57-55

RADIATION INDUCED SECOND BREAKDOWN  
AFWL-TR-70-42

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE *****	DOCUMENT NO./OTHER NO. *****
SIMPLIFIED MODELING OF INTEGRATED CIRCUITS FOR RADIATION PERFORMANCE PREDICTION	AFWL-TR-72-42
RESEARCH ON THE PHYSICS OF TRANSIENT RADIATION EFFECTS	HOL-TR-060-3
SECOND BREAKDOWN IN THE PRESENCE OF INTENSE IONIZING RADIATION AND RELATED STUDIES	DAAH-01-72-C-0894
SHORT COURSE IN NUCLEAR WEAPON EFFECTS AND SURVIVABILITY OF AEROSPACE SYSTEMS	
EFFECT OF IONIZING RADIATION ON SECOND BREAKDOWN	
TREE MODELING REQUIREMENTS, DNA COMPONENTS RESPONSE AND PREDICTION WORKING GROUP MEETING MATERIAL	
CMOS RADIATION HARDENING	P75-116
TECHNIQUES FOR SCREENING BIPOLAR TRANSISTOR DEGRADATION DUE TO IONIZING RADIATION	NADCRANE TR/7024/C74/121
SECOND BREAKDOWN IN THE PRESENCE OF INTENSE IONIZING RADIATION	RG-75-24
POSITION ON SEMICONDUCTOR DEVICE RESPONSE MODELING FOR THE NUCLEAR ENVIRONMENT	CSC-3040-1
RADIATION-INDUCED CURRENTS IN SUBMINIATURE COAXIAL CABLES	SAMSO-TR-75-296
ELECTRICAL PULSE BURNOFF OF TRANSISTORS IN INTENSE IONIZING RADIATION, PREPRINT	SAND 75-5222
AN MOS MODELING HIERARCHY INCLUDING RADIATION EFFECTS	BDM/A-89-75-TR-41
NUCLEAR RADIATION TESTS OF EMP HARDENED CMOS CIRCUITS-FINAL REPORT	



DNA OVERSTRESS REVIEW  
SUBJECT INDEX

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

TITLE  
\*\*\*\*\*

EFFECTS OF IONIZING RADIATION ON THE CHARACTERISTICS OF METAL-OXIDE  
SEMICONDUCTOR STRUCTURES HDL-CR-75-013-1

NEUTRON INDUCED NOISE IN JUNCTION FIELD EFFECT TRANSISTORS

ELECTRONICS RADIATION HARDNESS ASSURANCE TECHNIQUES STUDY AFWL-TR-73-134

EFFECT OF NUCLEAR RADIATION ON THE ELECTRICAL CHARACTERISTICS OF  
SEMICONDUCTOR DEVICES HARC-697

DEVELOPMENT OF A NON-DESTRUCTIVE RADIATION EFFECTS  
PREDICTION TECHNIQUE HRLR-3586

NEW RESULTS ON THE EFFECTS OF RADIATION ON ELECTRONIC AND  
AND ELECTROTECHNICAL MATERIALS AND DEVICES FTD-HC-23-2004-71

NUCLEAR RADIATION HARDENING FOR ELECTRONIC COMPONENTS LMSC A956-461

RADIATION EFFECTS ON ELECTRONIC PARTS NASA-CR-11 4354

RADIATION EFFECTS IN MICROWAVE BIPOLAR TRANSISTORS SC-DC-721233

APPENDIX A-2 BURNOUT CHAPTER OF A REPORT TITLED JFET HARDENING AND  
HIGH DOSE RATE STUDY AFCL-72-0335

NUCLEAR VULNERABILITY ASSESSMENT

TRANSIENT COLLECTOR BREAKDOWN IN THE PRESENCE OF GAMMA RADIATION AND  
CONDUCTED EMP

HARDENING OF MJS77 SPACECRAFT AGAINST THE JUPITER RADIATION BELTS

NUE INDUCED ELECTRICAL OVERSTRESS JUNCTION FAILURES IN SEMICONDUCTOR  
A PROPOSED PROGRAM

ONA OVERSTRESS REVIEW  
SUBJECT INDEX

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

TITLE  
\*\*\*\*\*

INTENSE BEAM PRELIMINARY EXPERIMENTS

MECHANISMS OF RADIATION AND PULSED ELECTRICAL FAILURE IN  
SEMICONDUCTOR ELECTRONICS MEMO 1M57-114

A MATHEMATICAL MODEL FOR PRIMARY PHOTO-CURRENTS INDUCED IN  
TRANSISTOR BASE REGIONS

\*\*\*\*\*RADIOS

NUCLEAR ELECTROMAGNETIC PULSE PROTECTIVE MEASURES APPLIED  
TO A TYPICAL COMMUNICATION SHELTER N-1091

ANALYSIS AND TEST OF COMMUNICATIONS ANTENNAS BDM/W-TR145-73

WORK ORDER 2-14 FINAL TECHNICAL REPORT HF RADIO AN/ARC-123 PULSE  
TESTS 2-5170-ARWE-003

AN/APT-47 UHF RADIO TRANSMITTER SET SYSTEM DESCRIPTION CORLA017

FINAL REPORT ANALYSIS OF COMMUNICATIONS SYSTEMS EQUIPMENT FAILURE  
MODELING BDM/A-60-74-14

\*\*\*\*\*RELIABILITY

THE PHYSICS OF INTERFACE INTERACTIONS RELATED TO RELIABILITY OF  
FUTURE ELECTRONIC DEVICES AFCL-TR-74-0194

RELIABILITY DATA FOR ELECTRONIC AND ELECTROMECHANICAL COMPONENTS A  
REPORT

RADC SERIES IN RELIABILITY VOLS. 3.4.5 RADC

AD-A047 964

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BIBLIOGRAPHY FOR ELECTRICAL OVERSTRESS REVIEW.(U)  
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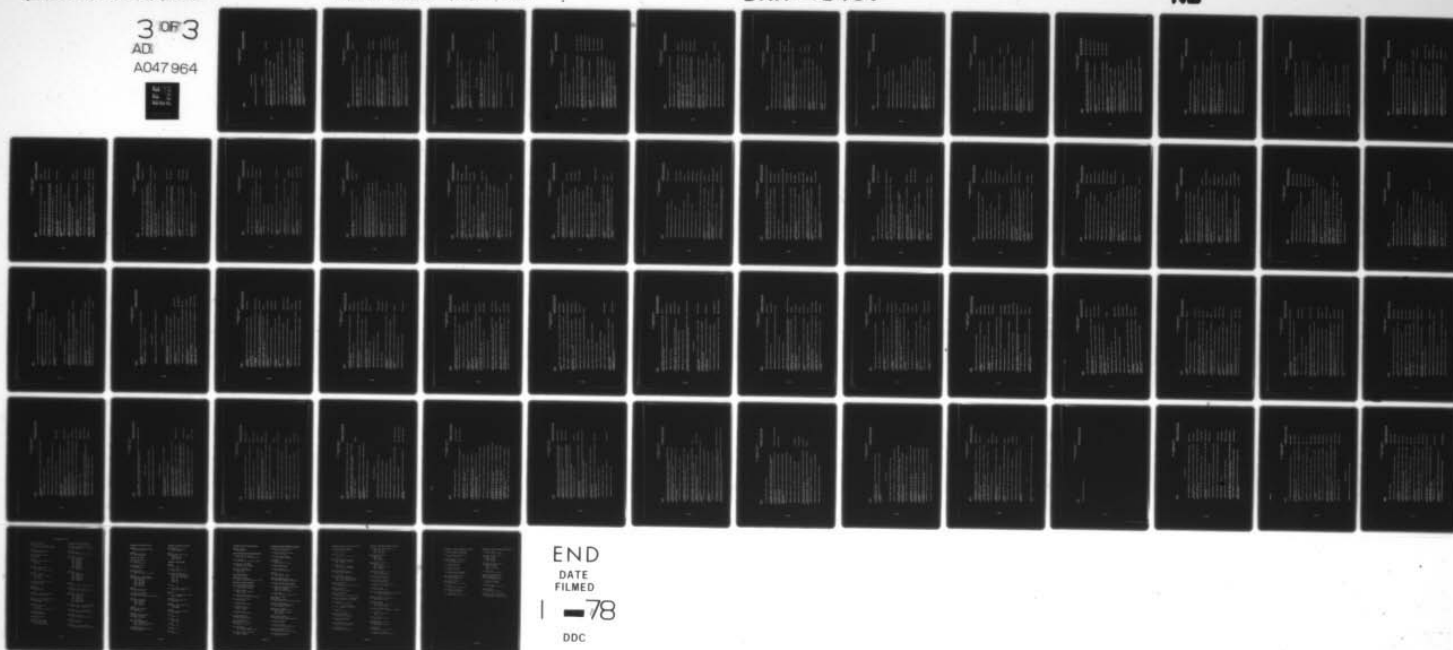
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3 OF 3

AD  
A047 964



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DATE  
FILMED

1 - 78

DDC

ONA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

\*\*\*\*\*RESISTANCE

SPREADING RESISTANCE CORRECTION FACTORS

\*\*\*\*\*RESPONSE

CONTROL OF ELECTRIC FIELD AT THE SURFACE OF P-N JUNCTIONS

ED-11-313

SOME NEW ASPECTS OF THERMAL INSTABILITY OF THE CURRENT  
DISTRIBUTION IN POWER TRANSISTORS

THERMAL SWITCHBACK IN HIGH F-T EPITAXIAL TRANSISTORS

EXPERIMENTAL RESULTS OF TESTING RESISTORS UNDER PULSE CONDITIONS

ELECTROMAGNETIC EFFECTS OF NUCLEAR EXPLOSIONS ON ELECTRONIC SYSTEMS

VOLT NO.5

HIGH POWER EFFECTS IN SEMICONDUCTOR COMPONENTS

INTERIM REPORT RESPONSE OF A MULTICONDUCTOR CABLE TO EXCITATION AT  
AN OPEN BREAK IN THE SHIELD

SC-CH-70-6152

JUNCTION CAPACITANCE AS A FUNCTION OF VOLTAGE FOR DIFFUSED P-N DIODES  
WITH EXPONENTIAL DOPING GRADIENTS

INTERIM REPORT RESPONSE OF A MULTICONDUCTOR TRANSMISSION LINE TO  
EXCITATION BY AN ARBITRARY MONOCHROMATIC IMPRESSED FIELD ALONG THE LINE

SC-CH-715075

SIMPLIFICATIONS IN THE STUDY OF GROUNDED-SHIELD, "BALANCED" TWIN-  
LEAD CABLES

SC-CH-715110

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

NCL-72-6P

ELECTRICAL PULSE OVERSTRESS EFFECTS IN MICROCIRCUITS

NUMERICAL APPROACH FOR CALCULATING THE RESPONSE OF A P-N JUNCTION  
CAPACITOR TO A RAMP SIGNAL

NUCLEAR AND SPACE RADIATION EFFECTS

FILAMENTATION IN SILICON-ON-SAPPHIRE HOMOGENEOUS THIN FILMS

HDL-TH-1449

RESPONSE OF INTEGRATED CIRCUITS TO A SIMULATED IEMP ENVIRONMENT

D224-13009-1

AABNCP LOW LEVEL TEST FINAL REPORT

TREE MODELING REQUIREMENTS, DNA COMPONENTS RESPONSE AND  
PREDICTION WORKING GROUP MEETING MATERIAL

SLA-74-0131

MATHEMATICAL MODELS FOR THE RESPONSE OF AEROSPACE SYSTEMS TO HIGH  
FREQUENCY ELECTROMAGNETIC ENVIRONMENTS

AFWL-TH-73-272

SIMPLIFIED MICROCIRCUIT MODELING

BDM/A-89-75-TH-41

AN MOS MODELING HIERARCHY INCLUDING RADIATION EFFECTS

75 SDS 4279

IEMP RESPONSE : DAMAGE MODELING OF DIODES, JUNCTION FIELD EFFECT  
TRANSISTOR DAMAGE TESTING AND SEMICONDUCTOR DEVICE FAILURE ANALYSIS

HDL-CJ-75-013-1

EFFECTS OF IONIZING RADIATION ON THE CHARACTERISTICS OF METAL-OXIDE  
SEMICONDUCTOR STRUCTURES

NOISE IN BIPOLAR JUNCTION TRANSISTORS AT HIGH INJECTION LEVELS

INVESTIGATION OF THE TRANSITION FROM FUNNELING TO IMPACT IONIZATION  
MULTIPLICATION IN SILICON P-N JUNCTION



DNA OVERSTRESS REVIEW  
SUBJECT INDEX

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

TITLE  
\*\*\*\*\*

TRANSIENT COLLECTOR BREAKDOWN IN THE PRESENCE OF GAMMA RADIATION AND  
CONDUCTED EMP

DEVICE DEGRADATION BY HIGH AMPLITUDE CURRENTS AND RESPONSE  
CHARACTERISTICS OF DISCRETE RESISTORS

THERMAL RESPONSE OF A SEMICONDUCTOR JUNCTION

A COMPUTER MODEL FOR LATERAL THERMAL INSTABILITIES IN POWER  
TRANSISTORS

\*\*\*\*\*SCREENING

FEASIBILITY STUDY OF DEVELOPING A NON-DESTRUCTIVE SCREENING  
PROCEDURE FOR THERMAL SECOND BREAKDOWN

NON-DESTRUCTIVE SCREENING FOR THERMAL SECOND BREAKDOWN

SCANNING ELECTRON MICROSCOPE EXAMINATION OF METALLIZATION DEFECTS AFWL-TN-72-212

TECHNIQUES FOR SCREENING BIPOLAR TRANSISTOR DEGRADATION DUE TO  
IONIZING RADIATION MADCHANE TR77024/C74/121

TECHNICAL NOTE 3 MODIFIED DISCRETE SEMICONDUCTOR FIRST LEVEL SCREEN

EFFECTIVE SCREENING OF INTEGRATED CIRCUITS

\*\*\*\*\*SECOND BREAKDOWN

MESAPLASMA BREAKDOWN IN SILICON JUNCTIONS

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

TITLE  
\*\*\*\*\*

AN ASPECT OF SECOND BREAKDOWN IN TRANSISTORS

FINE STRUCTURE AND ELECTRO MAGNETIC RADIATION IN SECOND BREAKDOWN

A SURVEY OF SECOND BREAKDOWN

TRANSISTOR DEGRADATION FOLLOWING SECOND BREAKDOWN

SECOND BREAKDOWN IN SIMPLIFIED TRANSISTOR STRUCTURES AND DIODES

VOL. ED-13, NOS. 8/9

INPUT POWER INDUCED THERMAL EFFECTS RELATED TO TRANSITION TIME  
BETWEEN AVALANCHE AND SECOND BREAKDOWN IN P-N SILICON JUNCTIONS

VOL. ED-13 NOS. 8/9

TRANSISTOR FAILURE BY SECOND BREAKDOWN

VOL. ED-13 NOS. 8/9

TRANSIENT JUNCTION TEMPERATURE RISE AND SECOND BREAKDOWN IN  
TRANSISTORS

VOL. ED-13, NO.11

SECOND BREAKDOWN IN MOS TRANSISTORS

VOL. ED-13, NO.11

CURRENT MODE SECOND BREAKDOWN IN EPITAXIAL PLANAR TRANSISTORS

VOL. ED-13, NO.11

SECONDARY BREAKDOWN THERMAL CHARACTERIZATION AND IMPROVEMENT OF  
SEMICONDUCTOR DEVICES

VOL. ED-13, NO.11

THE SCANNING ELECTRON MICROSCOPE AS A MEANS OF INVESTIGATING  
"SECOND BREAKDOWN" AND SIMILAR PHENOMENA

EXPERIMENTAL DEMONSTRATION AND THEORY OF A CORRECTIVE TO  
SECOND BREAKDOWN IN SI POWER TRANSISTORS

A CHARACTERIZATION TECHNIQUE FOR SECOND BREAKDOWN IN GE  
ALLOYED JUNCTION TRANSISTORS

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

SECOND BREAKDOWN IN THE FORWARD AND REVERSE BASE CURRENT REGION

SECOND BREAKDOWN - A COMPREHENSIVE REVIEW

ENERGY-TIME DEPENDENCE OF SECOND BREAKDOWN IN SEMICONDUCTORS FOR  
SUBMICROSECOND ELECTRICAL PULSES. 67SD7253

A SURVEY OF SECOND BREAKDOWN PHENOMENA, MECHANISMS AND DAMAGE IN  
SEMICONDUCTOR JUNCTION DEVICES HG-IR-70-19-14

A SURVEY OF SECOND BREAKDOWN PHENOMENA, MECHANISMS AND DAMAGE IN  
SEMICONDUCTOR JUNCTION DEVICES HG-IR-70-19

SYNERGISTIC CONSIDERATIONS FOR THE SECOND BREAKDOWN OF A P-N  
JUNCTION IN A PULSED ELECTRICAL AND PULSED RADIATION ENVIRONMENT MEMO 1457-55

RADIATION INDUCED SECOND BREAKDOWN AFWL-IR-70-42

CORRELATION BETWEEN SECOND BREAKDOWN AND INFRARED RADIATION IN  
POWER TRANSISTORS

FEASIBILITY STUDY OF DEVELOPING A NON-DESTRUCTIVE SCREENING  
PROCEDURE FOR THERMAL SECOND BREAKDOWN

SECOND-BREAKDOWN PHENOMENA IN AVALANCHING SILICON ON SAPPHIRE DIODES

NON-DESTRUCTIVE SCREENING FOR THERMAL SECOND BREAKDOWN

SECOND BREAKDOWN AND DAMAGE IN SEMICONDUCTOR JUNCTION DEVICES HG-IR-72-15

SECOND BREAKDOWN PHENOMENA IN AVALANCHING SILICON ON SAPPHIRE DIODES

NON-DESTRUCTIVE SCREENING FOR THERMAL SECOND BREAKDOWN

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

SUSCEPTIBILITY OF SEMICONDUCTOR DEVICES TO THERMAL SECOND BREAKDOWN

SECOND BREAKDOWN AND DAMAGE IN JUNCTION DEVICES

INVESTIGATION OF SECOND BREAKDOWN IN SEMICONDUCTOR JUNCTION DEVICES 34/UATN-73-002

FEASIBILITY OF USING FINITE ELEMENTS IN ANALYSIS OF SECOND  
BREAKDOWN IN SEMICONDUCTOR DEVICES

RG-73-14

SECOND BREAKDOWN IN THE PRESENCE OF INTENSE IONIZING RADIATION AND  
RELATED STUDIES

DAAM-01-72-C-089

THE DETERMINATION OF SEMICONDUCTOR JUNCTION VULNERABILITY TO SECOND  
BREAKDOWN BY LOW ENERGY ELECTRICAL MEASUREMENTS

155-93

EFFECT OF IONIZING RADIATION ON SECOND BREAKDOWN

AN INVESTIGATION OF CURRENT MODE SECOND BREAKDOWN

177-93

SECOND BREAKDOWN IN THE PRESENCE OF INTENSE IONIZING RADIATION

H3-75-24

DETERMINATION OF SEMICONDUCTOR JUNCTION VULNERABILITY TO SECOND  
BREAKDOWN

DEM 200-93

SECOND BREAKDOWN AND LOW FREQUENCY NOISE IN BIPOLAR JUNCTION  
TRANSISTORS

AN ELECTRO-THERMAL MODEL OF SECOND BREAKDOWN: SUMMARY

FEASIBILITY OF USING FINITE ELEMENTS IN ANALYSIS OF  
BREAKDOWN

AD 765-688

MODELING SECOND BREAKDOWN WITH NET-2

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

TITLE  
\*\*\*\*\*

SECONDARY BREAKDOWN IN GERMANIUM GOLD-BONDED DIODES

\*\*\*\*\*SEMICONDUCTORS

BREAKDOWN VOLTAGE OF PLANAR SILICON JUNCTIONS

ELECTRON MULTIPLICATION IN SILICON AND GERMANIUM

AVALANCHE BREAKDOWN IN GERMANIUM

TRANSISTOR JUNCTION TEMPERATURE AS A FUNCTION OF TIME

HIGH VOLTAGE CONDUCTIVITY MODULATED SILICON RECTIFIER

A NEW HIGH CURRENT MODE OF TRANSISTOR OPERATION

ELECTRICAL PROPERTIES OF GOLD DOPED DIFFUSED SILICON COMPUTER  
DIODES

SOLID SOLUBILITIES OF IMPURITY ELEMENTS IN GERMANIUM AND SILICON

THEORY OF CURRENT-CARRIER TRANSPORT AND PHOTOCONDUCTIVITY IN  
SEMICONDUCTORS WITH TRAPPING

IMPURITY MEDISTIMULATION AND JUNCTION FORMATION IN SILICON BY  
THERMAL OXIDATION

POTENTIAL DISTRIBUTION AND CAPACITANCE OF A GRADED P-N JUNCTION

DIFFUSED JUNCTION DEPLETION LAYER CALCULATIONS



DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

AVALANCE BREAKDOWN CHARACTERISTICS OF A DIFFUSED P-N JUNCTION

RESISTIVITY OF BULK SILICON AND OF DIFFUSED LAYERS IN SILICON

MESAPLASMA BREAKDOWN IN SILICON JUNCTIONS

FORWARD TRANSIENT BEHAVIOR OF P-N JUNCTION DIODES AT HIGH INJECTION LEVELS

AN ASPECT OF SECOND BREAKDOWN IN TRANSISTORS

CONTROL OF ELECTRIC FIELD AT THE SURFACE OF P-N JUNCTIONS

ED-11-313

ANALYSIS OF THE IMPURITY ATOM DISTRIBUTION NEAR THE DIFFUSION MASK FOR A PLANAR P-N JUNCTION

MICROELECTRONIC PACKAGING CONCEPTS

MADC-TR-65-51

EFFECT OF JUNCTION CURVATURE ON BREAKDOWN VOLTAGE IN SEMICONDUCTIONS

AVALANCHE BREAKDOWN VOLTAGES OF ABRUPT AND LINEARLY GRADED P-N JUNCTIONS IN GE, SI, GaAs AND GAP

SURFACE ASPECTS OF THE THERMAL DEGRADATION OF GSAS P-N JUNCTION LASER AND TUNNEL DIODES

TRANSISTOR DEGRADATION FOLLOWING SECOND BREAKDOWN

ANALYSIS OF THE TEMPERATURE RISE IN PIN DIODES CAUSED BY MICROWAVE PULSE DISSIPATION

SECOND BREAKDOWN IN SIMPLIFIED TRANSISTOR STRUCTURES AND DIODES

VOL. ED-13-NUS B/9

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

INPUT POWER INDUCED THERMAL EFFECTS RELATED TO TRANSITION TIME  
BETWEEN AVALANCHE AND SECOND BREAKDOWN IN P-N SILICON JUNCTIONS

TRANSISTOR FAILURE BY SECOND BREAKDOWN

VOL. ED-13 NOS. 8/9

TRANSIENT JUNCTION TEMPERATURE RISE AND SECOND BREAKDOWN IN  
TRANSISTORS

SECOND BREAKDOWN IN MOS TRANSISTORS

CURRENT MODE SECOND BREAKDOWN IN EPITAXIAL PLAIN TRANSISTORS

SECONDARY BREAKDOWN THERMAL CHARACTERIZATION AND IMPROVEMENT OF  
SEMICONDUCTOR DEVICES

SOME NEW ASPECTS OF THERMAL INSTABILITY OF THE CURRENT  
DISTRIBUTION IN POWER TRANSISTORS

THERMAL SWITCHBACK IN HIGH F-T EPITAXIAL TRANSISTORS

EXPERIMENTAL DEMONSTRATION AND THEORY OF A CORRECTIVE TO  
SECOND BREAKDOWN IN SI POWER TRANSISTORS

A CHARACTERIZATION TECHNIQUE FOR SECOND BREAKDOWN IN GE  
ALLOYED JUNCTION TRANSISTORS

SECOND BREAKDOWN IN THE FORWARD AND REVERSE BIAS CURRENT REGION

STATIC V-I RELATIONSHIPS IN TRANSISTORS AT HIGH INJECTION LEVELS

AVALANCHE BREAKDOWN OF DIFFUSED SILICON P-N JUNCTIONS

CALCULATIONS OF CUTOFF FREQUENCY, BREAKDOWN VOLTAGE, AND CAPACITANCE  
FOR DIFFUSED JUNCTIONS IN THIN EPITAXIAL SILICON LAYERS

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

SILICON POWER DEVICE MATERIALS PROBLEMS

PROTECTION OF SEMICONDUCTION DEVICES, CIRCUITS AND EQUIPMENT  
FROM VOLTAGE TRANSIENTS

SILICON POWER ZENER TRANSIENT SUPPRESSORS

EXPERIMENTAL STUDY OF AVALANCHE BREAKDOWN IN SILICON PLANAR P-N  
JUNCTIONS

HIGH VOLTAGE THYRISTOR STRINGS FOR INVERTER APPLICATIONS

ENERGY-TIME DEPENDENCE OF SECOND BREAKDOWN IN SEMICONDUCTORS FOR  
SUBMICROSECOND ELECTRICAL PULSES. 67SD725J

AN ACCURATE NUMERICAL STEADY STATE ONE DIMENSIONAL SOLUTION OF THE  
P-N JUNCTION

ZENER AND AVALANCHE BREAKDOWN IN SILICON ALLOYED P-N JUNCTIONS  
-I- ANALYSIS OF REVERSE CHARACTERISTICS

METAL-SILICON SCHOTTKY BARRIERS

DETERMINATION OF A PHYSICAL MODEL FOR DOUBLE DIFFUSED TRANSISTORS

EVALUATION OF DOPING PROFILES FROM CAPACITIVE MEASUREMENTS

RESISTIVITY, MOBILITY AND IMPURITY LEVELS IN GEAS, GE AND SI AT  
300 DEG. K

RADIATION EFFECTS ON GALLIUM ARSENIDE DEVICES AND SCHOTTKY DIODES

AFWL-TR-68-31 VOL222

NEGATIVE RESISTANCE AND FILAMENTARY CURRENTS IN AVALANCHING SILICON

[illegible]

# DÉTERMINATION OF THRESHOLD FAILURE LEVELS OF SEMICONDUCTOR DIODES AND TRANSISTORS DUE TO PULSE VOLTAGES

## SEMICONDUCTOR DAMAGE STUDY-PRELIMINARY REPORTS

# DETERMINATION OF SEMICONDUCTOR FAILURE LEVELS DUE TO HIGH VOLTAGE TRANSIENTS

# DETERMINATION OF THRESHOLD FAILURE LEVELS OF SEMICONDUCTOR DIODES AND TRANSISTORS DUE TO PULSE VOLTAGES

## PRELIMINARY REPORT-SEMICONDUCTOR DAMAGE STUDY

## PRELIMINARY REPORT II-SEMICONDUCTOR DAMAGE STUDY

# FORWARD CURRENT SURGE FAILURE IN SEMICONDUCTOR DEVICES

77-746

# ESTIMATES OF SEMICONDUCTOR FAILURE DUE TO MULTIPLE VOLTAGE PULSES

## PRELIMINARY REPORT SEMICONDUCTOR DAMAGE STUDY (REVISED)

## THERMAL MANAGEMENT OF INTEGRATED CIRCUITS

# A COMPUTER MODEL FOR INTEGRATED CIRCUIT TRANSISTORS INCLUDING SUBSTRATE INTERACTIONS

## SPREADING RESISTANCE CORRECTION FACTORS

## THERMAL INSTABILITY LIMITING POWER DISSIPATION IN TRANSISTORS

## ON THE TRANSPORT CHARACTERISTICS OF A P-N JUNCTION WITH NANOMETER-DIFFUSED REGION

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

SILICON NITRIDE AS A MASK IN PHOSPHORUS DIFFUSION

DEPLETION LAYER AND CAPACITANCE CALCULATIONS FOR GAUSSIAN DIFFUSED JUNCTIONS

DEPLETION LAYER CALCULATIONS FOR ERROR FUNCTION DIFFUSED JUNCTIONS

MEASUREMENTS ON THE DEPLETION LAYER PROPERTIES OF PLANAR DIODES

THE BUILT-IN VOLTAGE OF DIFFUSED P-N JUNCTIONS

THEORETICAL AND EXPERIMENTAL STUDY OF LATCH UP IN JUNCTION ISOLATED INTEGRATED CIRCUITS FR-69-10-227

SEMICONDUCTOR VULNERABILITY PHASE I REPORT RDM/A-37-69-W

A MODEL TO PREDICT PULSE POWER FAILURE OF SEMICONDUCTOR DEVICES

PRELIMINARY REPORT AND WORKING DATA FOR SHORT PULSE DURATION SEMICONDUCTOR DAMAGE PROGRAM RDM-375-69-F-0168A

AUTONETICS ELECTRONIC COMPONENTS FAILURE MODE HANDBOOK 58-1329/501

SEMICONDUCTOR AND NON-SEMICONDUCTOR DAMAGE STUDY PERSHING DEVICES RDM-375-69-F-0169

EMP CHARACTERIZATION OF SPRINT AIRCRAFT COMPONENTS-FINAL REPORT CREG 69-2

DETERMINATION OF THRESHOLD FAILURE LEVELS DUE TO HIGH VOLTAGE TRANSIENTS FOR A GA 53933 TRANSISTOR RDM/A-27-69-W

FRANKLIN INSTITUTE REPORT ON ESD PULSE TESTING F-C2540



DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE *****	DOCUMENT NO./OTHER NO. *****
MECHANISMS OF RADIATION INITIATED SEMICONDUCTOR DEVICE FAILURES	69SD323
SEMICONDUCTOR VULNERABILITY-PHASE I REPORT	BDM/A-37-69-M
SEMICONDUCTOR VULNERABILITY-PHASE II REPORT-THEORETICAL ESTIMATES OF FAILURE LEVELS OF SELECTED SEMICONDUCTOR DIODES AND TRANSISTORS	BDM/A-42-69-M
FORT BELVOIR SEMICONDUCTOR FAILURE PROGRAM REPORT	
DAMAGE LEVEL EVALUATION OF SEMICONDUCTOR COMPONENTS USING ULTRA FAST RISETIME PULSER	HSE-IN-69-3
SEMICONDUCTOR DAMAGE TEST RESULTS FOR SANDIA DEVICES UZ110,UZ130, JZ9079	
SEMICONDUCTOR #MDDJN1K WHO'S TO BLAME FOR FAILURES	
MODELS FOR THE PN DIODE AND THE VPM AND PNP TRANSISTOR FOR USE IN COMPUTER AIDED DESIGN AND ANALYSIS PROGRAMS	
TRANSISTOR AND DIODE MODEL HANDBOOK	69-521-1
THEORETICAL ESTIMATES OF FAILURE LEVELS OF SELECTED SEMICONDUCTOR DIODES AND TRANSISTORS	BDM/A-34-69-M
PULSE POWER FAILURE MODES IN SEMICONDUCTORS	
FINAL REPORT ON SEMICONDUCTOR DAMAGE STUDY PHASE II	NFM/S 68-70-1R
SEMICONDUCTOR VULNERABILITY PHASE III REPORT EXPERIMENTAL THRESHOLD FAILURE LEVELS OF SELECTED DIODES AND TRANSISTORS	BDM/A-75-70-1M
A SURVEY OF SECOND BREAKDOWN PHENOMENA, MECHANISMS AND DAMAGE IN SEMICONDUCTOR JUNCTION DEVICES	RS-TR-70-19-1R

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

FINAL SUMMARY REPORT ON SEMICONDUCTOR DAMAGE STUDY PHASE II HDM/A-84-70-14

CONFERENCE PROCEEDINGS ON COMPONENT DEGRADATION FROM TRANSIENT  
INPUTS, SPONSORED BY US ARMY MOBILITY EQUIPMENT RESEARCH : DEV. CIR

MICROELECTRONIC TECHNIQUES AND REQUIREMENTS FOR THE SPECIAL WEAPONS  
CENTER MICROELECTRONICS FACILITY-FINAL REPORT EE-172(70)KAFB-076

A SURVEY OF SECOND BREAKDOWN PHENOMENA, MECHANISMS AND DAMAGE IN  
SEMICONDUCTOR JUNCTION DEVICES HG-TR-70-19

THE REAL CULPRIT IN DIODE FAILURE

PULSE POWER FAILURE MODES IN SEMICONDUCTORS

A PROGRAM TO INVESTIGATE RADIATION INITIATED, CURRENT INDUCED  
FAILURES IN SEMICONDUCTOR DEVICES MEMO 1457-117

SYNERGISTIC CONSIDERATIONS FOR THE SECOND BREAKDOWN OF A P-N  
JUNCTION IN A PULSED ELECTRICAL AND PULSED RADIATION ENVIRONMENT MEMO 1457-55

NET TRANSISTOR AND DIODE LIBRARY TAPE 4925

A COMPUTER AIDED ANALYSIS MODEL FOR THE JUNCTION FIELD EFFECT  
TRANSISTOR SC-DN-70-365

A CENTER OF COMPETENCE IN SOLID STATE MATERIALS AND DEVICES AFCRL-71-0304

PULSE POWER TESTING OF MICROCIRCUITS WADC-TR-71-59

CORRELATION BETWEEN SECOND BREAKDOWN AND INFRARED RADIATION IN  
POWER TRANSISTORS

THERMAL BREAKDOWN DELAY TIME IN SILICON P-N JUNCTIONS

DNA OVERSTRESS REVIEW\*  
SUBJECT INDEX

TITLE *****	DOCUMENT NO./OTHER NO. *****
STATISTICAL COMPONENT DAMAGE STUDY	RG-TM-71-1
FINAL SUMMARY REPORT ON SEMICONDUCTOR DAMAGE STUDY-PHASE II	BCM/A-84-70-1M
INVESTIGATION INTO ELECTROMAGNETIC PULSE VULNERABILITY ON SELECTED BIPOLAR TRANSISTORS	MDC E027A
METHODS, DEVICES AND CIRCUITS FOR THE EMP HARDENING OF ARMY ELECTRONICS	ECOM-0045-F
PULSE POWER TESTING OF MICROCIRCUITS	
RF BURNOUT IN X-BAND SCHOTTKY MIXERS	
SPECIAL REPORT ON POWER TRANSISTORS	
METALLIZATION BURNOUT RESEARCH AT THE UNITED STATES AIR FORCE ACADEMY	AF-L-TR-71-4
DESIGNING ULTRAHIGH BIPOLAR TRANSISTORS	
JUNCTION CAPACITANCE AS A FUNCTION OF VOLTAGE FOR DIFFUSED P-N DIODES WITH EXPONENTIAL DOPING GRADIENTS	
FAILURE ANALYSIS OF DAMAGED 2N700 TRANSISTORS	NV/E-20/71
NWL MICROWAVE SUSCEPTIBILITY MEASUREMENT SYSTEMS FOR SOLID STATE COMPONENTS	TM-F/47-71
AN EXPERIMENTAL INVESTIGATION OF EMP INDUCED TRANSIENT UPSET OF INTEGRATED CIRCUITS	SC-TM-71 0330
PULSE POWER TESTING OF MICROCIRCUITS	WADC-TM-71-59

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

SIMPLIFIED MODELING OF INTEGRATED CIRCUITS FOR RADIATION  
PERFORMANCE PREDICTION

AFWL-TR-72-42

HIGH POWER PULSE TESTING OF INTEGRATED CIRCUITS

MG-72-22

A COMPARISON OF TWO TRANSISTOR MODELS

AN ANALYTICAL EXPRESSION FOR THE MULTIPLICATION FACTOR  $M$  IN  
SEMICONDUCTORS WITH EQUAL IONIZATION COEFFICIENT

MODELING OF BIPOLAR TRANSISTOR USING INTEGRAL CHARGE CONTROL MODEL  
WITH APPLICATION TO THIRD-ORDER DISTORTION STUDIES

SIMPLIFIED COMPUTER AIDED ANALYSIS OF DOUBLE DIFFUSED TRANSISTORS  
INCLUDING TWO-DIMENSIONAL HIGH LEVEL EFFECTS

SECOND-BREAKDOWN PHENOMENA IN AVALANCHING SILICON ON SAPPHIRE DIODES

SYNTHESIS OF GENERAL IMPURITY PROFILES USING A TWO-STEP  
DIFFUSION PROCESS

PERIPHERAL AND DIFFUSED LAYER EFFECTS ON DOPING PROFILES

EFFECT OF THE SPATIALLY VARYING MINORITY CARRIER MOBILITY IN THE  
DRIFT TRANSISTOR

LIMITATIONS IN MICROELECTRONICS-II. BIPOLAR TECHNOLOGY

ITERATIVE SCHEME FOR COMPUTER SIMULATION OF SEMICONDUCTOR DEVICES

A SIMPLE METHOD FOR DETERMINING STATIC PARAMETERS OF LARGE SIGNAL  
SEMICONDUCTOR DIODE AND TRANSISTOR MODELS

THERMIONIC SATURATION OF DIFFUSION CURRENTS IN TRANSISTORS



DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

SEMICONDUCTOR DEVICE DEGRADATION BY HIGH AMPLITUDE CURRENT PULSES SC-RR-72-0513

INTEGRATED CIRCUIT ELECTRO MAGNETIC SUSCEPTIBILITY INVESTIGATION MDC D0690  
DEVELOPMENT PHASE REPORT

SOLID STATE COMPONENTS RF SUSCEPTIBILITY PROGRAM-PROGRESS REPORT FVR/VGP<MAC J900/EMC  
FY-72

DEVELOPMENT OF A SEMICONDUCTOR FAILURE MODEL FOR LIGHTNING INDUCED PULSES ATN 72-001

GE-MOU VARISTOR-THE SUPER ALPHA VARISTOR 72 CRD 260

NUMERICAL APPROACH FOR CALCULATING THE RESPONSE OF A P-N JUNCTION CAPACITOR TO A PAMP SIGNAL

CHARACTERIZATION AND MEASUREMENT OF THE BASE AND EMITTER RESISTANCE OF BIPOLAR TRANSISTORS VOL SC-7 NO.6

THE DEGRADATION OF MOS TRANSISTORS RESULTING FROM JUNCTION AVALANCHE VOL. 11  
BREAKDOWN

1972 THIRTEENTH SCINTILLATION AND SEMICONDUCTOR COUNTER SYMPOSIUM

A TWO-DIMENSIONAL NUMERICAL ANALYSIS OF A SILICON NPN TRANSISTOR

COMPUTER-AIDED TWO DIMENSIONAL NUMERICAL ANALYSIS OF BIPOLAR TRANSISTORS

POWER TRANSISTOR AND THYRISTOR SPEC SHEETS DON'T TELL IT ALL

SUSCEPTIBILITY OF SEMICONDUCTOR DEVICES TO THERMAL SECOND BREAKDOWN

IMPROVEMENT OF SEMICONDUCTOR DEVICES

HDL-002-1



DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

AVALANCHE BREAKDOWN IN SILICON DIFFUSED JUNCTIONS

A THEORETICAL INVESTIGATION ON THE GENERATION CURRENT IN SILICON P-N  
JUNCTIONS UNDER REVERSE BIAS

ELECTRICAL PULSE OVERSTRESS EFFECTS IN MICROCIRCUITS

NCL-72-6P

METHODS DEVICES AND CIRCUITS FOR THE EMP HARDENING OF ARMY  
ELECTRONICS

ECOM-0275-S

SECOND BREAKDOWN AND DAMAGE IN SEMICONDUCTOR JUNCTION DEVICES

RG-TR-72-15

SEMICONDUCTOR DEVICE DEGRADATION BY HIGH CURRENT PULSES

SC-DC-72-2298

STEADY STATE JUNCTION TEMPERATURES OF SEMICONDUCTOR CHIPS

ADAPTATION OF THE P-N JUNCTION BURNOJT MODEL TO CIRCUIT ANALYSIS  
CODES

LUMPED MODEL ANALYSIS OF SEMICONDUCTOR DEVICES USING THE NET-2  
CIRCUIT/SYSTEM ANALYSIS PROGRAM

PULSED-POWER BURNOJT OF INTEGRATED CIRCUITS

SAMSO-TK-72-226

SHORT PULSE EFFECTS IN SEMICONDUCTOR DIODES

A COMPARISON OF RF AND DC - INDUCED DAMAGE TO METAL-SEMICONDUCTOR  
JUNCTIONS

TR-2707

FAILURE THRESHOLD AND RESISTANCE OF THE PROTECTED AND UNPROTECTED  
2N2222 TRANSISTOR IN THE SHORT PULSE WIDTH REGIME

PEM-7

METHODS, DEVICES AND CIRCUITS FOR THE EMP HARDENING OF ARMY  
ELECTRONICS

ECOM-0275-F

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE *****	DOCUMENT NO./OTHER NO. *****
REVIEW OF RDM EMP COMPONENT TEST PROGRAMS	BDM/A-143-73-TM
SECOND BREAKDOWN AND DAMAGE IN JUNCTION DEVICES	
MOS DEVICE FAILURE PROGRAM FINAL REPORT	C73-1175/501
REVIEW OF DIELECTRICS AND SWITCHING	AFWL-TM-72-88
FEASIBILITY STUDY FOR EMP TERMINAL PROTECTION	TPD 003
ELECTRO THERMAL OVERSTRESS FAILURE IN MICROELECTRONICS	WADC-TM-73-87
DETAILED TEST PLAN-INTEGRATED CIRCUIT TEST	BDM/A-48-73-TM
TEST PLAN FOR MOS DEVICE FAILURE	C73-573/501
INVESTIGATION OF SECOND BREAKDOWN IN SEMICONDUCTOR JUNCTION DEVICES	34/UATN-73-002
THE SUSCEPTIBILITY OF X-BAND POINT CONTACT DIODES TO MICROWAVE RADIATION	TR-2963
FEASIBILITY OF USING FINITE ELEMENTS IN ANALYSIS OF SECOND BREAKDOWN IN SEMICONDUCTOR DEVICES	MG-73-14
SECOND BREAKDOWN IN THE PRESENCE OF INTENSE IONIZING RADIATION AND RELATED STUDIES	DAAM-01-72-C-0894
PLAN FOR PULSE POWER TESTING OF MOS DEVICES	C73-5731501
SEMICONDUCTOR VULNERABILITY VOL I THEORETICAL ESTIMATES OF FAILURE LEVELS OF SELECTED SEMICONDUCTOR DIODES AND TRANSISTORS-PHASE II	AFWL-TM-73-119 VOL I

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE *****	DOCUMENT NO./OTHER NO. *****
SEMICONDUCTOR VULNERABILITY VOL II - EXPERIMENTAL THRESHOLD FAILURE LEVELS OF SELECTED DIODES AND TRANSISTORS - PHASE III	AFWL-TR-73-119 VOL II
WORK ORDER 2-14 INTEGRATED CIRCUITS TEST PROGRAM-FINAL REPORT	BDM/A-98-73-TR
RESPONSE OF INTEGRATED CIRCUITS TO A SIMULATED IEMP ENVIRONMENT	HDL-TR-16-9
EMP HARDENED CMOS CIRCUIT	HDL-TR-192-1
SOLID STATE COMPONENT RF SUSCEPTIBILITY PROGRAM-PROGRESS REPORT FY73 FJR/VGP< MAC 3920	
PROGRAM FINAL REPORT	C73-1175/501
BOND IMPROVEMENTS PROGRAM FOR HARRY DIAMOND LASS - FINAL REPORT	HDL-TR-127-1
INTEGRATED CIRCUIT ELECTROMAGNETIC SUSCEPTIBILITY INVESTIGATION PHASE II INTERIM REPORT 2	MDC E0981
PERMITTIVITY AND PERMEABILITY OF METAL OXIDE VARISTORS	HDL-TM-73-37
R.F. FAILURE MECHANISMS RELATED TO MICROELECTRONICS PROCESS CONTROL	NELC/TM 1902
THEORETICAL AND EXPERIMENTAL STUDIES OF SEMICONDUCTOR DEVICE DEGRADATION DUE TO HIGH POWER ELECTRICAL TRANSIENTS	73SD-259
INTEGRATED CIRCUIT ELECTROMAGNETIC SUSCEPTIBILITY INVESTIGATION PHASE II	MDCE0921
PULSE GURNOUT OF MICROWAVE MIXER DIODES	VOL. M-22 NO.4
A REPORT AND PROPOSAL FOR EXTREMELY HIGH CURRENT INJECTION MODELING OF SEMICONDUCTOR DEVICES	

UNA OVERSTRESS REVIEW  
SUBJECT INDEX

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

NO. 23 VOL. 21

TITLE  
\*\*\*\*

FOCUS ON POWER SEMICONDUCTORS

COMBINED DOCUMENTATION WORK ORDER 2-14

ASPECTS OF SEMICONDUCTOR DEVICE DAMAGE DUE TO ELECTRICAL TRANSIENTS RDM/A-199-73-14  
(DRAFT COPY)

THE DETERMINATION OF SEMICONDUCTOR JUNCTION VULNERABILITY TO SECOND 155-93  
BREAKDOWN BY LOW ENERGY ELECTRICAL MEASUREMENTS

IC SIMULATES POWER TRANSISTOR

MICROWAVE INDUCED DAMAGE AND FAILURE MODES IN LOW FREQUENCY  
TRANSISTORS RELATED TO DEVICE DESIGN AND PROCESS CONTROL  
CONSTANT VOLTAGE DIODES ARE GETTING SHARPER

INTEGRATED CIRCUIT ELECTROMAGNETIC SUSCEPTIBILITY INVESTIGATION MDC-E1123  
PHASE II-BIPOLAR NAND GATE STUDY

SEMICONDUCTOR MEASUREMENT TECHNOLOGY REPORT NO. 400-12  
QUARTERLY REPORT

SEMICONDUCTOR MEASUREMENT, TECHNOLOGY-PROGRESS REPORT REPORT NO. 400-12

DEFENSE NUCLEAR AGENCY EMP SEMINAR-SUBSYSTEM AND COMPONENT  
SUSCEPTIBILITY

EMP HARDENED CMOS CIRCUITS-FINAL REPORT

CHARACTERISTICS AND APPLICATIONS OF METAL OXIDE VARISTORS FOR EMP PEM-43  
HARDENING

EMP SURGE SUPPRESSION CONNECTORS UTILIZING METAL OXIDE VARISTORS HDL-TR-177-1



DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

INTEGRATED CIRCUIT ELECTROMAGNETIC SUSCEPTIBILITY NOTEBOOK

SEMICONDUCTOR MEASUREMENT TECHNOLOGY QUARTERLY REPORT

EXPERIMENTAL DAMAGE CONSTANT SUMMARY

EMP SUSCEPTIBILITY OF SEMICONDUCTOR COMPONENTS

DISCRETE SEMICONDUCTOR EMP DATA SUMMARY

HIGH CURRENT INJECTION MODELING OF SEMICONDUCTOR DEVICES

CMOS RADIATION HARDENING

SIMPLIFIED MICROCIRCUIT MODELING

TECHNIQUES FOR SCREENING BIPOLAR TRANSISTOR DEGRADATION DUE TO  
IONIZING RADIATION

B-1 SETA TECHNICAL MEMORANDUM-STATUS OF REVERSE BIAS SEMICONDUCTOR  
DAMAGE MODELING

SURVEY OF CIRCUIT ELEMENTS USED FOR REDUCTION OF AND PROTECTION  
FROM SYSTEMS GENERATED ELECTRO MAGNETIC PULSE EFFECTS

A STUDY OF AMORPHOUS SEMICONDUCTORS FOR SYMMETRICAL VARISTOR  
APPLICATIONS

POSITION ON SEMICONDUCTOR DEVICE RESPONSE MODELING FOR THE NUCLEAR  
ENVIRONMENT

ADDENDUM TO EMP SUSCEPTIBILITY OF SEMICONDUCTOR COMPONENTS

400-12

HDM/A-49-74-TR-R1

HDM/A-110-74-TR

HDM/A-111-74-TR

TR-EE-74-43

P75-116

AFWL-TR-73-272

NADCRANE TR/1024/C74/121

T.M. 7.11/3

AFWL-TR-74-309

CSC-3040-1

D224-13042-2



DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE *****	DOCUMENT NO./OTHER NO. *****
ADDENDUM TO DISCRETE SEMICONDUCTOR EMP DATA SUMMARY	D224-13043-2
ADDENDUM TO EMP SUSCEPTIBILITY OF SEMICONDUCTOR COMPONENTS	D224-13042-2
STUDY OF IEMP EFFECTS ON OPERATIONAL AMPLIFIER CIRCUITS	SAMS0-TR-75-281
SEMICONDUCTOR DATA REDUCTION ALGORITHM CONTENTS	D224-13042-3
PROGRAM REPORT ON T.D. 4-6 DEVICE TESTING	BDM/A-CHKJ-0346-75
SERIES RESISTANCE EFFECTS IN SEMICONDUCTOR C V PROFILING	VOL. ED-22 NO.5
ELECTRICAL PULSE BURNOUT OF TRANSISTORS IN INTENSE IONIZING RADIATION, PREPRINT	SAND 75-5222
AN MOS MODELING HIERARCHY INCLUDING RADIATION EFFECTS	BDM/A-89-75-TR-R1
METHODS FOR ENSURING SEMICONDUCTOR METALLIZATION SURVIVABILITY FIRST DRAFT	
DEGRADATION OF MONOLITHIC SEMICONDUCTOR DEVICES BY HIGH AMPLITUDE CURRENT PULSES	MADC-TR-75-11
NUCLEAR RADIATION TESTS OF EMP HARDENED CMOS CIRCUITS-FINAL REPORT	
TECHNICAL NOTE 3 MODIFIED DISCRETE SEMICONDUCTOR FIRST LEVEL SCREEN	
MINUTES OF THE MICROELECTRONICS HARDNESS ASSURANCE STANDARDIZATION MEETING	
DETERMINATION OF SEMICONDUCTOR JUNCTION VULNERABILITY TO SECOND BREAKDOWN	HEH 200-93

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*  
DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

SECOND BREAKDOWN AND LOW FREQUENCY NOISE IN BIPOLAR JUNCTION TRANSISTORS

NOISE IN BIPOLAR JUNCTION TRANSISTORS AT HIGH INJECTION LEVELS

NEUTRON INDUCED NOISE IN JUNCTION FIELD EFFECT TRANSISTORS

INVESTIGATION OF THE TRANSITION FROM FUNNELING TO IMPACT IONIZATION MULTIPLICATION IN SI-JCN P-N JUNCTION

HIGH CURRENT INJECTION MODELING OF SEMICONDUCTOR DEVICES

TR-EE-76-1

SEMICONDUCTOR MEASUREMENT TECHNOLOGY: ARPA/NBS WORKSHOP III TEST PATTERNS FOR INTEGRATED CIRCUITS

NBS SPEC PUB. 400-15

RF FAILURE PREDICTION FOR MOS 4001 AND 4011 INTEGRATED CIRCUITS - WORKING PAPER

TN 3107

COMPUTER AIDED ENGINEERING OF SEMICONDUCTOR INTEGRATED CIRCUITS

ECON-75-1344-1

FEASIBILITY OF USING FINITE ELEMENTS IN ANALYSIS OF BREAKDOWN

AD 766-688

ELECTRONICS RADIATION HARDNESS ASSURANCE TECHNIQUES STUDY

AFML-TR-73-134

EFFECT OF NUCLEAR RADIATION ON THE ELECTRICAL CHARACTERISTICS OF SEMICONDUCTOR DEVICES

BARC-697

LOW COST TRANSIENT SUPPRESSOR

ECON-0168-73-F

NEW RESULTS ON THE EFFECTS OF RADIATION ON ELECTRONIC AND AND ELECTROTECHNICAL MATERIALS AND DEVICES

FTD-HC-23-2004-71

NUCLEAR RADIATION HARDENING FOR ELECTRONIC COMPONENTS

LMSC A956-461

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*  
DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

RADIATION EFFECTS ON ELECTRONIC PARTS  
NASA-CR-11 4364

FAILURE MECHANISMS IN SILICON SEMICONDUCTORS  
NADC-TDM-62-533

THE EFFECTS OF PULSED GAMMA RADIATION ON ELECTRONIC COMPONENTS  
RTD-TDM-63-3110

PULSED POWER BURNOVT OF INTEGRATED CIRCUITS  
SAMSO-TM-72-226

RADIATION EFFECTS IN MICROWAVE BIPOLAR TRANSISTORS  
SC-DC-721233

STUDY OF THE COMBINED EFFECTS OF IONIZATION, NEUTRONS, TEMPERATURE  
AND TIME ON BIPOLAR DEVICES.  
SLA-73-402

SEMICONDUCTOR CIRCUIT FAILURE AND PROTECTION IMPLEMENTATION SCHEMES  
PEM-21

THE DAMAGE SUSCEPTIBILITY OF INTEGRATED CIRCUITS TO A SIMULATED IEMP  
TRANSIENT

ON THE NECESSARY AND SUFFICIENT CONDITIONS (THRESHOLDS) FOR DAMAGE  
OF SEMICONDUCTOR JUNCTIONS FROM ELECTRICAL TRANSIENTS

A METHOD TO PREDICT SEMICONDUCTOR JUNCTION FAILURE DUE TO  
ELECTRICAL OVERSTRESS

APPENDIX A-2 BURNOVT CHAPTER OF A REPORT TITLED JFET HARDENING AND  
HIGH DOSE RATE STUDY  
AFCML-72-0335

SHORT PULSE WIDTH-4 FAILURE LEVEL CHARACTERIZATION FOR THE 2N3821  
JUNCTION FIELD EFFECT TRANSISTOR  
PEM-24

USE OF THE FAIRCHILD 600 TO DETERMINE DAMAGE PARAMETERS

SEMICONDUCTOR DAMAGE STUDY

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

TITLE  
\*\*\*\*\*

SEMICONDUCTOR DAMAGE CONSTANTS

TEMPERATURE DEPENDENCE OF JUNCTION TRANSISTOR PARAMETERS

SEMICONDUCTOR DEVICE DAMAGE IN AN EMP ENVIRONMENT

SIMPLIFIED MICROCIRCUIT MODELING

HIGH CURRENT TRANSIENT INDUCED JUNCTION SHORTS

NWE INDUCED ELECTRICAL OVERSTRESS JUNCTION FAILURES IN SEMICONDUCTION  
A PROPOSED PROGRAM

MEMO-TECHNICAL REVIEW OF DNA PROGRAMS FOR FY77 IN THE SEMICONDUCTOR  
DEVICES, EXCLUDING MOS, AREA

COMPUTER ANALYSIS OF HOT SPOT FORMATION IN POWER TRANSISTORS

CURRENT CROWDING IN HARDENED POWER TRANSISTORS

MECHANISMS OF RADIATION AND PULSED ELECTRICAL FAILURE IN  
SEMICONDUCTOR ELECTRONICS

MEMO 1M57-115

A MATHEMATICAL MODEL FOR PRIMARY PHOTO-CURRENTS INDUCED IN  
TRANSISTOR BASE REGIONS

SECONDARY BREAKDOWN IN GERMANIUM GOLD-BONDED DIODES

HIGH CURRENT INJECTION MODELING OF SEMICONDUCTION DEVICES  
(DRAFT COPY)

EFFECTIVE SCREENING OF INTEGRATED CIRCUITS

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

PULSE DAMAGE DATA FROM INTEGRATED CIRCUITS AND ELECTRONIC PARTS

SOME COMMENTS ON THE MODELS USED TO PREDICT SEMICONDUCTOR DAMAGE  
CONSTANTS

SECTION II A MODEL TO PREDICT POWER FAILURE OF SEMICONDUCTOR DEVICES

CHAPTER II - PROGRAM APPROACH AND TECHNICAL DISCUSSION

A COMPUTER MODEL FOR LATERAL THERMAL INSTABILITIES IN POWER  
TRANSISTORS

\*\*\*\*\*SEMICONDUCTOR

A SURVEY OF SECOND BREAKDOWN

DETERMINATION OF THRESHOLD FAILURE LEVEL OF SEMICONDUCTOR DIODES AND  
TRANSISTORS DUE TO PULSE VOLTAGES.

SEMICONDUCTOR VULNERABILITY PHASE II REPORT THEORETICAL ESTIMATES  
FAILURE LEVELS OF SELECTED SEMICONDUCTOR DIODES AND TRANSISTORS

BDM/A-42-69-M

HIGH POWER EFFECTS IN SEMICONDUCTOR COMPONENTS

SECOND BREAKDOWN PHENOMENA IN AVALANCHING SILICON ON SAPPHIRE DIODES

EVALUATION OF SEMICONDUCTOR DEVICE ANALYSIS USING THE NET-2 COMPUTER HDL-065-1  
PROGRAM-FINAL REPORT

EFFECTS OF IONIZING RADIATION ON THE CHARACTERISTICS OF METAL-OXIDE  
SEMICONDUCTOR STRUCTURES

HDL-CA-75-013-1

BIPOLAR VOLTAGE PULSE DAMAGE EFFECTS ON TRANSISTORS

AD 760-685



DNA OVERSTRESS REVIEW  
SUBJECT INDEX

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

TITLE  
\*\*\*\*\*

DETERMINATION OF SEMICONDUCTOR FAILURE LEVELS DUE TO HIGH VOLTAGE TRANSIENTS

THERMAL RESPONSE OF A SEMICONDUCTOR JUNCTION

\*\*\*\*\*SPACECRAFT

HARDENING OF MJ577 SPACECRAFT AGAINST THE JUPITER RADIATION BELTS

\*\*\*\*\*SUBSYSTEMS

PROTECTION OF SEMICONDUCTOR DEVICES, CIRCUITS AND EQUIPMENT FROM VOLTAGE TRANSIENTS

HIGH VOLTAGE THYRISTOR STRINGS FOR INVERTER APPLICATIONS

AN EXAMPLE OF THE APPLICATION OF ECAP TO CIRCUIT ANALYSIS OF AN A-C POWER SUPPLY RG-TR-67-16

1968 IEEE ELECTROMAGNETIC COMPATIBILITY SYMPOSIUM RECORD IEEE 68C12-EMC

ELECTROMAGNETIC EFFECTS OF NUCLEAR EXPLOSIONS ON ELECTRONIC SYSTEMS VOL7 NO.5

MEASUREMENTS AND ANALYSIS OF LIGHTNING INDUCED VOLTAGE IN AIRCRAFT ELECTRICAL CIRCUITS HVL-63-161

INTERIM REPORT RESPONSE OF A MULTICONDUCTOR CABLE TO EXCITATION AT AN OPEN BREAK IN THE SHIELD SC-CR-70-6152

INTERIM NOTES 3-52 EMP TEST PROGRAM VOTE 6 GENERAL PROCEDURES FOR SUBSYSTEM EMP TESTING RDM/A-121-70-PN

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

TITLE  
\*\*\*\*\*

METHODS, DEVICES AND CIRCUITS FOR THE EMP HARDENING OF ARMY ELECTRONICS	ECOM-0085-F
ECOM CONTRACT DAAB07-70-C-0085 MONTHLY AND QUARTERLY REPORTS (BOUND TOGETHER)	
RECOMMENDED INTERNAL COUPLING ANALYSIS TECHNIQUES FOR THE D-523 EMP TEST PROGRAM	BDM/A-66-71-TR
INTERIM REPORT RESPONSE OF A MULTICONDUCTION TRANSMISSION LINE TO EXCITATION BY AN ARBITRARY MONOCHROMATIC IMPRESSED FIELD ALONG THE LINE	SC-CR-715076
CIRCUS-2 A DIGITAL COMPUTER PROGRAM FOR TRANSIENT ANALYSIS OF ELECTRONIC CIRCUITS USER'S GUIDE	0070-1
SIMPLIFICATIONS IN THE STUDY OF GROUNDED-SHIELD, "BALANCED" TWIN-LEAD CABLES	SC-CR-715110
IN-PLACE EMP CRITICAL CIRCUIT THRESHOLD ANALYSIS	02-19693-2
METHODS, DEVICES AND CIRCUITS FOR THE EMP HARDENING OF ARMY ELECTRONICS	ECOM-0275-S
ADAPTATION OF THE P-N JUNCTION BJRNJOI MODEL TO CIRCUIT ANALYSIS CODES	
DRAFT AEROSPACE VEHICLE EMI TRANSIENT TEST TECHNIQUES	BDM/A-51-72-IR
METHODS, DEVICES AND CIRCUITS FOR THE EMP HARDENING OF ARMY ELECTRONICS	BDM/A-119-72-TR
SPECIAL PULSE TESTING OF THE D45A1 DETONATOR	F-C30H1
DESIGN GUIDELINES FOR EMP HARDENING OF AERONAUTICAL SYSTEMS (DRAFT)	C72-451/201
CIRCUIT ANALYSIS USING THE DRIVING-POINT-IMPEDANCE TECHNIQUE	SC-M-71 0896

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE *****	DOCUMENT NO./OTHER NO. *****
LIGHTNING AND HIGH VOLTAGE SURGE PROTECTION FOR BALANCED DIGITAL TRANSMISSION DEVICES	ECOM-4027
EMP UPSET HARDENING GUIDELINES	022A-10016-2
ANALYSIS OF FAILURE OF ELECTRONIC CIRCUITS FROM EMP-INDUCED SIGNALS REVIEW AND CONTRIBUTION	HDL-TR-1615
DESIGN GUIDELINES FOR EMP HARDENING OF AERONAUTICAL SYSTEMS	AFWL-TR-73-117
THE PHYSICS OF INTERFACE INTERACTIONS RELATED TO RELIABILITY OF FUTURE ELECTRONIC DEVICES	AFCHL-TR-74-0194
EMP HARDENING APPROACH FOR SAM-D	PEM-35
COMBINED DOCUMENTATION WORK ORDER 2-14	
ANALYSIS AND TEST OF COMMUNICATIONS ANTENNAS	HDM/W-TH145-73
ASAP-1 FINAL REPORT	0224-12013-1
SPECIAL DEVICES, TEST STRUCTURES, AND HYBRID CIRCUITS FOR SPECIAL ENVIRONMENTS	HDL-TR-003-1
DEFENSE NUCLEAR AGENCY EMP SEMINAR-SUBSYSTEM AND COMPONENT SUSCEPTIBILITY	
FEASIBILITY STUDY OF ELECTROSTATIC PROTECTION FOR ELECTROEXPLOSIVE DEVICES	74SD4237
EMP HARDENED CMOS CIRCUITS-FINAL REPORT	
ADVANCED ELECTRO-OPTICAL SYSTEM HARDENING	HDL-CR-047-2

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

IDENTIFICATION FRIEND OR FOE/AIR TRAFFIC CONTROL (IFF/ATC) SYSTEM AN/APX-72 SYSTEM DESCRIPTION	CDRL A017
AN/ART-47 UHF RADIO TRANSMITTER SET SYSTEM DESCRIPTION	CDHLA017
A METHOD FOR THE PREDICTION OF EMP DAMAGE PROBABILITY	BDM/A-9-74-TM
SECOND PROGRESS REPORT ON ELECTRONICS MODELING AND CIRCUIT SIMULATION	HDW/M-74-021TM
DEFENSE NUCLEAR AGENCY EMP SEMINAR "SUBSYSTEM AND COMPONENT SUSCEPTIBILITY"	
AIRBORNE COMMAND POST AARNCP ELECTRONIC SYSTEM DETAILED PROGRAM PLAN CDRL A018 INTERIM REPORT	
B-1 SCALE MODEL PRELIMINARY TEST PLAN FOR MEASUREMENT OF WEAPONS RAY AND WHEEL WHEEL COUPLING (FINAL)	0224-13038-1
B-1 EMP SUBSYSTEM ASSESSMENT DATA, IFF AN/APX-54	0224-13022-10
SIMPLIFIED SUBSYSTEM INTERFACE MODEL	
SURVEY OF CIRCUIT ELEMENTS USED FOR REDUCTION OF AND PROTECTION FROM SYSTEMS GENERATED ELECTRO MAGNETIC PULSE EFFECTS	AFWL-TR-74-309
RECOMMENDED COMPONENT/SUBSYSTEM RESEARCH PROGRAM BRIEFING	HDW/A-22-75-BM
CABLE AND CONNECTOR SHIELDING ATTENUATION AND TRANSFER IMPEDANCE MEASUREMENT USING QUADRAXIAL AND QUINTAXIAL TEST METHODS	DEM-45
COMPARISON OF ANTENNA-RELATED PREDICTIVE MODELS WITH B-1 SCALE MODEL MEASUREMENTS IN ALECS	0224-13052-2
SUBSYSTEM TEST METHODOLOGY FOR THE AFWL DIRECT DRIVE LABORATORY	0224-13057-1



DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

F-111/ARES DETAIL TEST PLAN, VOLUME V PHASE II INTEGRATED TEST PLAN (FINAL)	D224-13008-5
EXTERNAL COMPLING OF AN ELECTROMAGNETIC PULSE TO THE B-1 AIRCRAFT	D224-13060-1
SAMSO STANDARD- LIST OF PREFERRED PARTS FOR SPACE AND MISSILE SYSTEM SAMSO-STD 73-4 A	
EMP RESPONSE OF THE B-1 AIRCRAFT FOR INADVERTENT PENETRATION COMPLING VOLUME I. FINAL REPORT	U224-13064-1
SUBSYSTEM TEST METHODOLOGY FOR THE AFWL DIRECT DRIVE LABORATORY	BDM/A-23-75-1M
OVERVOLTAGE TRANSIENT STUDIES OF LEVEL SENSOR AMPLIFIER CKTS.	RG-TR-71-5
SEMICONDUCTOR CIRCUIT FAILURE AND PROTECTION IMPLEMENTATION SCHEMES	PEM-21
SIMPLIFIED SUBSYSTEM INTERFACE MODELS	
USING DRIVING POINT IMPEDANCE METHODS ON ACTIVE NETWORKS	
CIRCUIT DAMAGE ANALYSIS TECHNIQUE	
A SURVEY OF SELECTED NETWORK ANALYSIS PROGRAMS	
CHAPTER 7 SUBSYSTEM DAMAGE SUSCEPTIBILITY	D224-10005-1
DRAFT OF CHAPTER 13 EMP COMPONENT SENSITIVITY AND SYSTEM UPSET ADVANCED RELEASE	
MECHANISMS OF RADIATION AND PULSED ELECTRICAL FAILURE IN SEMICONDUCTOR ELECTRONICS	MEMO 1M57-119



DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

TEST REPORT ON CONDUCTED CURRENT SHIELDING EFFECTIVENESS OF DAYONET PEM-12  
CONNECTOR SHELLS WITH 4 FINGERS

FINAL REPORT EC-135 PRETEST ANALYSIS VOLUME II SYSTEMS DESCRIPTION BDM/A 12-71-41

AABNCP LOW LEVEL TEST PLAN 0226-10109-1

METHODS, DEVICES, AND CIRCUITS FOR THE EMP HANDLING  
OF ARMY ELECTRONICS (REPORTS<FINAL,8/70,1/71,3/71,5/71,2/72,3/72,  
IN-PLACE EMP WING III THRESHOLD VARIATION SURVEY 02-19693-3

COMPUTER ANALYSIS OF EMP INDUCED CIRCUIT FAILURES

SAMSO STANDARD- ELECTRONIC PARTS, MATERIALS AND PROCESSES FOR SPACE SAMSO-STD 73-2C  
AND MISSILE APPLICATIONS, STANDARD CONTROL PROGRAM FOR

\*\*\*\*\*SYSTEMS

DESIGN STUDIES FOR ULTRA FAST, LOW IMPEDANCE, HIGH PEAK POWER  
PULSED SYSTEMS AFWL-TR-65-21

PROTECTION OF SEMICONDUCTOR DEVICES, CIRCUITS AND EQUIPMENT  
FROM VOLTAGE TRANSIENTS

AN EXAMPLE OF THE APPLICATION OF ECAP TO CIRCUIT ANALYSIS OF AN  
A-C POWER SUPPLY HG-TR-67-16

OUTLINE FOR SYSTEM VULNERABILITY/SURVIVABILITY ANALYSIS

1968 IEEE ELECTROMAGNETIC COMPATIBILITY SYMPOSIUM RECORD IEEE 68C12-EMC

SEMICONDUCTOR AND NON-SEMICONDUCTOR DAMAGE STUDY PERTAINING DEVICES BDM-375-69-F-0168

ONA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

EMP CHARACTERIZATION OF SPRINT AUTOPILOT COMPONENTS-FINAL REPORT

CREG 69-2

LASER TRIGGERED SWITCHING STUDY

AFWL-TH-69-37

ELECTROMAGNETIC EFFECTS OF NUCLEAR EXPLOSIONS ON ELECTRONIC SYSTEMS

VOL7 NO.5

RADIATION HARDENED AVIONICS GAIN INTEREST

TREES ON POWER HANDLING EQUIPMENT

INSTRUMENTATION FOR NUCLEAR WEAPON EFFECTS SIMULATION SYMPOSIUM-  
VOLUME II - TRANSIENT RADIATION EFFECTS ON ELECTRONIC SYSTEMS

AFSWC-TH-70-S VOL.II

MINUTEMAN III RE-ENTRY SYSTEM-ALECS-S PROGRAM PIECE PARTS TEST  
SUPPORTS-FINAL REPORT

70SD401

MEASUREMENTS AND ANALYSIS OF LIGHTNING INDUCED VOLTAGE IN AIRCRAFT  
ELECTRICAL CIRCUITS

MVL-69-161

APPROACHES TO SYSTEM HARDENING

3SK-399

AN ANALYTICAL AND LOW-LEVEL TESTING APPROACH TO THE EMP SYSTEMS  
PROBLEM

SMV TM-70-7

NUCLEAR ELECTROMAGNETIC PULSE PROTECTIVE MEASURES APPLIED  
TO A TYPICAL COMMUNICATION SHELTER

N-1091

INTERIM REPORT RESPONSE OF A MULTICONDUCTOR CABLE TO EXCITATION AT  
AN OPEN BREAK IN THE SHIELD

SC-CR-70-6152

INTERIM NOTES B-52 EMP TEST PROGRAM VOTE 6 GENERAL PROCEDURES FOR  
SUBSYSTEM EMP TESTING

BDM/A-121-70-PN

METHODS, DEVICES AND CIRCUITS FOR THE EMP HARDENING OF ARMY  
ELECTRONICS

ECOM-00085-F

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

TITLE  
\*\*\*\*\*

FUNCTIONAL DESIGN OF GENERIC ELECTRONIC ELECTRIC TARGETS

BRL-MR-2130

CABLE SYSTEM ANALYSIS

AFWL-TM-71-100 VOL I

ECOM CONTRACT DAAB07-70-C-0085 MONTHLY AND QUARTERLY REPORTS  
(AROUND TOGETHER)

MISSILE AND AIRCRAFT COMPONENT VULNERABILITY TO EMP

SC-TM-70-902

RECOMMENDED INTERNAL COUPLING ANALYSIS TECHNIQUES FOR THE B-52S EMP  
TEST PROGRAM

BDM/A-66-71-1M

INTERIM REPORT RESPONSE OF A MULTICONDUCTOR TRANSMISSION LINE TO  
EXCITATION BY AN ARBITRARY MONOCHROMATIC IMPRESSED FIELD ALONG THE LINE

SC-CH-715075

CIRCUS-2 A DIGITAL COMPUTER PROGRAM FOR TRANSIENT ANALYSIS OF  
ELECTRONIC CIRCUITS USER'S GUIDE

0070-1

SIMPLIFICATIONS IN THE STUDY OF GROUNDED-SHIELD, "BALANCED" TWIN-  
LEAD CABLES

SC-CH-715110

IN-PLACE EMP CRITICAL CIRCUIT THRESHOLD ANALYSIS

02-19693-2

EMP PROTECTIVE SYSTEMS

12-61-B

METHODS DEVICES AND CIRCUITS FOR THE EMP HARDENING OF ARMY  
ELECTRONICS

ECOM-J275-S

ADAPTATION OF THE P-N JUNCTION BURNOUT MODEL TO CIRCUIT ANALYSIS  
CODES

DRAFT AEROSPACE VEHICLE EMI TRANSIENT TEST TECHNIQUES

BDM/A-51-72-1M

METHODS, DEVICES AND CIRCUITS FOR THE EMP HARDENING OF ARMY  
ELECTRONICS

BDM/A-119-72-1M

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE *****	DOCUMENT NO./OTHER NO. *****
SPECIAL PULSE TESTING OF THE D45A1 DETONATOR	F-C3081
METHODS, DEVICES AND CIRCUITS FOR THE EMP HARDENING OF ARMY ELECTRONICS	ECOM-0275-F
AERONAUTICAL SYSTEMS EMP TECHNOLOGY REVIEW	D224-10004-1
MEMORANDUM REPORT N.2200 GENERIC ELECTRONIC TARGET DESIGN /DEVELOPMENT	HRL MR 2200
MULTICONDUCTOR CABEL MODELING	D224-10013-2
ELECTROMAGNETIC PULSE HANDBOOK FOR MISSILES AND AIRCRAFT IN FLIGHT	
DESIGN GUIDELINES FOR EMP HARDENING OF AERONAUTICAL SYSTEMS (DRAFT)	C72-451/201
B-52/VPD GENERAL TEST PLAN	D224-10000-1
CIRCUIT ANALYSIS USING THE DRIVING-POINT-IMPEDANCE TECHNIQUE	SC-W-71 0895
AEROSPACE VEHICLE EMI TRANSIENT TEST TECHNIQUES	AFAL-TR-72-102
FIELD AND LABORATORY TESTING IDENTIFICATION AND SUMMARY AERONAUTICAL SYSTEMS EMP INTEGRATED TEST PROGRAM ROUGH DRAFT	
EMP PROTECTIVE SYSTEMS	TR-61-B
EMP PROTECTION FOR EMERGENCY OPERATING CENTERS	TR-61A
LIGHTNING AND HIGH VOLTAGE SURGE PROTECTION FOR BALANCED DIGITAL TRANSMISSION DEVICES	ECOM-4027



ONA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*  
DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

EMP UPSET HARDENING GUIDELINES	D22A-10016-2
ANALYSIS OF FAILURE OF ELECTRONIC CIRCUITS FROM EMP-INDUCED SIGNALS REVIEW AND CONTRIBUTION	HDL-TR-1615
DESIGN GUIDELINES FOR EMP HARDENING OF AERONAUTICAL SYSTEMS	AFWL-TR-73-117
THE PHYSICS OF INTERFACE INTERACTIONS RELATED TO RELIABILITY OF FUTURE ELECTRONIC DEVICES	AFCHL-TR-74-0194
SHORT COURSE IN NUCLEAR WEAPON EFFECTS AND SURVIVABILITY OF AEROSPACE SYSTEMS	
EMP HARDENING APPROACH FOR SAM-D	PEM-35
COMBINED DOCUMENTATION WORK ORDER 2-14	
COMMON MODE MODEL DEVELOPMENT FOR COMPLEX CABLE SYSTEMS	D22A-10015-4
ANALYSIS AND TEST OF COMMUNICATIONS ANTENNAS	BDM/W-TR145-73
ASAP-1 FINAL REPORT	D22A-12013-1
WORK ORDER 2-14 FINAL TECHNICAL REPORT HF RADIO AN/ARC-123 PULSE TESTS	2-S170-ABOE-003
ENGINEERING DESIGN GUIDELINES FOR EMP HARDENING OF NAVAL MISSILES AND AIRPLANES	AMRC-R-17
SPECIAL DEVICES, TEST STRUCTURES, AND HYBRID CIRCUITS FOR SPECIAL ENVIRONMENTS	HDL-TR-003-1
DEFENSE NUCLEAR AGENCY EMP SEMINAR-SUBSYSTEM AND COMPONENT SUSCEPTIBILITY	



DNA OVERSTRESS REVIEW  
SUBJECT INDEX

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

TITLE  
\*\*\*\*\*

74SD4237

FEASIBILITY STUDY OF ELECTROSTATIC PROTECTION FOR ELECTROEXPLOSIVE DEVICES

EMP HARDENED CMOS CIRCUITS-FINAL REPORT

HDL-CR-047-2

ADVANCED ELECTRO-OPTICAL SYSTEM HARDENING

SLA-74-0131

MATHEMATICAL MODELS FOR THE RESPONSE OF AEROSPACE SYSTEMS TO HIGH FREQUENCY ELECTROMAGNETIC ENVIRONMENTS

CDRL A017

IDENTIFICATION FRIEND OR FOE/AIR TRAFFIC CONTROL (IFF/AIC) SYSTEM AN/APX-72 SYSTEM DESCRIPTION

CDHLA017

AN/ART-47 UHF RADIO TRANSMITTER SET SYSTEM DESCRIPTION

PEM-13

SHIELDING EVALUATION OF BRAIDED CABLE SHEATHS AND MULTICONDUCTOR CABLES USING PULSE TEST METHODS

BDM/A-9-74-TR

A METHOD FOR THE PREDICTION OF EMP DAMAGE PROBABILITY

BDM/W-74-0211R

SECOND PROGRESS REPORT ON ELECTRONICS MODELING AND CIRCUIT SIMULATION

BDM/A-60-74-TR

FINAL REPORT ANALYSIS OF COMMUNICATIONS SYSTEMS EQUIPMENT FAILURE MODELING

DEFENSE NUCLEAR AGENCY EMP SEMINAR "SUBSYSTEM AND COMPONENT SUSCEPTIBILITY"

AIRBORNE COMMAND POST AABNCP ELECTRONIC SYSTEM DETAILED PROGRAM PLAN CDRL A018 INTERIM REPORT

D224-13038-1

B-1 SCALE MODEL PRELIMINARY TEST PLAN FOR MEASUREMENT OF WEAPONS BAY AND WHEEL WELL COUPLING (FINAL)

D224-13005-1

DETAILED TEST PLAN B-1 SCALE MODEL/ALECS TEST PROGRAM SECTION 5

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

TITLE  
\*\*\*\*\*

F-111/ARES DETAIL TEST PLAN VOL.222, EXTERNAL COUPLING AND DELIBERATE D224-13008-3  
ANTENNA EXPERIMENTS

POST EXPERIMENT SUMMARY OF B-1 SCALE MODEL MEASUREMENTS FOR T03-19  
INADVERTENT PENETRATIONS

SRAM/ARES DETAIL TEST PLAN D224-13009-4

B-1 EMP SUBSYSTEM ASSESSMENT DATA, IFF AN/APX-54 D224-13022-10

SIMPLIFIED SUBSYSTEM INTERFACE MODEL

SURVEY OF CIRCUIT ELEMENTS USED FOR REDUCTION OF AND PROTECTION  
FROM SYSTEMS GENERATED ELECTRO MAGNETIC PULSE EFFECTS AFWL-TR-74-309

DNA EMP HANDBOOK CHAPTER 13 COMPONENT EMP SEMIACTIVITY AND SYSTEM  
UPSET

RECOMMENDED COMPONENT/SUBSYSTEM RESEARCH PROGRAM BRIEFING HDM/A-22-75-8M

ELECTROMAGNETIC PULSE HANDBOOK FOR ELECTRIC POWER SYSTEMS DNA 3466F

RADIATION-INDUCED CURRENTS IN SUBMINIATURE COAXIAL CABLES SAMS0-TR-75-296

CABLE AND CONNECTOR SHIELDING ATTENUATION AND TRANSFER IMPEDANCE  
MEASUREMENT USING QUADRAXICAL AND QUINTAXIAL TEST METHODS DEM-45

COMPARISON OF ANTENNA-RELATED PREDICTIVE MODELS WITH B-1 SCALE  
MODEL MEASUREMENTS IN ALECS D224-13052-2

SUBSYSTEM TEST METHODOLOGY FOR THE AFWL DIRECT DRIVE LABORATORY D224-13057-1

F-111/ARES DETAIL TEST PLAN, VOLUME V PHASE II INTEGRATED TEST PLAN D224-13008-5  
(FINAL)

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

DTP B-1 SCALE MODE. ALECS. SEC.6 FINAL DETAILED TEST PLAN	D224-13006-1
B-1 EMP RESPONSE FOR INADVERTENT PENETRATION COMPLING FINAL REPORT (DRAFT)	D224-13064-1
F-111/ARES TEST SUPPORT, VOLUME I DRAFT FINAL REPORT	D224-13059-1
B-52 G/AGM-28A/VPD EXPERIMENT TECHNICAL REPORT VOLUME II DRAFT FINAL REPORT	D224-13069-2
VERTICALLY POLARIZED DIPOLE (VPD) B-52G/AGM-28A TECHNICAL REPORT VOLUME I (DRAFT)	D224-13069-1
EXTERNAL COMPLING OF AN ELECTROMAGNETIC PULSE TO THE B-1 AIRCRAFT	D224-13060-1
SAMSO STANDARD- LIST OF PREFERRED PARTS FOR SPACE AND MISSILE SYSTEM SAMSO-STD 73-4 A	
EMP RESPONSE OF THE B-1 AIRCRAFT FOR INADVERTENT PENETRATION COMPLING VOLUME I, FINAL REPORT	D224-13064-1
DNA EMP SEMINAR SYSTEM LEVEL TESTING	
SUBSYSTEM TEST METHODOLOGY FOR THE AFWL DIRECT DRIVE LABORATORY	HDM/A-23-75-1M
SEMICONDUCTOR CIRCUIT FAILURE AND PROTECTION IMPLEMENTATION SCHEMES	PEM-21
SIMPLIFIED SUBSYSTEM INTERFACE MODELS	
MODELING TECHNIQUES FOR MULTICONDUCTOR CABLES< THEORY AND PRACTICE	AFWL-TR-72-89
USING DRIVING POINT IMPEDANCE METHODS ON ACTIVE NETWORKS	

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

MODELING AND SIMULATION TECHNIQUES FOR DAMAGE PREDICTION AND SYSTEM  
ASSESSMENT

CIRCUIT DAMAGE ANALYSIS TECHNIQUE

A SURVEY OF SELECTED NETWORK ANALYSIS PROGRAMS

HARDENING OF MJS77 SPACECRAFT AGAINST THE JUPITER RADIATION BELTS

CHAPTER 7 SUBSYSTEM DAMAGE SUSCEPTIBILITY

D224-10005-1

DRAFT OF CHAPTER 13 EMP COMPONENT SENSITIVITY AND SYSTEM UPSET  
ADVANCED RELEASE

MECHANISMS OF RADIATION AND PULSED ELECTRICAL FAILURE IN  
SEMICONDUCTOR ELECTRONICS

MEMO 1M57-119

TEST REPORT ON CONDUCTED CURRENT SHIELDING EFFECTIVENESS OF BAYONET  
CONNECTOR SHELLS WITH FINGERS PEM-12

FINAL REPORT ON THE PRELIMINARY 3-1 EVALUATION OF EMP RELATED AIRCRAFT C73-310/201  
CHARACTERISTICS VOLUME II

FINAL REPORT EC-135 PRETEST ANALYSIS VOLUME II SYSTEMS DESCRIPTION

ADM/A 12-71-41

AABNCP LOW LEVEL TEST PLAN

D226-10109-1

METHODS, DEVICES, AND CIRCUITS FOR THE EMP HARDENING  
OF ARMY ELECTRONICS (REPORTS FINAL, R70, 1/71, 3/71, 5/71, 2/72, 3/72,

BDM/A-119-72-1M

IN-PLACE EMP WING III THRESHOLD VARIATION SURVEY

D2-1969J-3

COMPUTER ANALYSIS OF EMP-INDUCED CIRCUIT FAILURES

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*  
DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

SAMSO STANDARD- ELECTRONIC PARTS, MATERIALS AND PROCESSES FOR SPACE AND MISSILE APPLICATIONS. STANDARD CONTROL PROGRAM FOR SAMSO-STD 73-2C

\*\*\*\*\*THYRISTORS

HIGH VOLTAGE THYRISTOR STRINGS FOR INVERTER APPLICATIONS

POWER TRANSISTOR AND THYRISTOR SPEC SHEETS DON'T TELL IT ALL

\*\*\*\*\*TRANSIENTS

PROTECTION OF SEMICONDUCTOR DEVICES, CIRCUITS AND EQUIPMENT FROM VOLTAGE TRANSIENTS

SILICON POWER ZENER TRANSIENT SUPPRESSORS

AN ACCURATE NUMERICAL ONE-DIMENSIONAL SOLUTION OF THE P-N JUNCTION UNDER ARBITRARY TRANSIENT CONDITIONS

DETERMINATION OF THRESHOLD FAILURE LEVELS DUE TO HIGH VOLTAGE TRANSIENTS FOR A GA 53933 TRANSISTOR

HDM/A-27-69-M

CONFERENCE PROCEEDINGS ON COMPONENT DEGRADATION FROM TRANSIENT INPUTS, SPONSORED BY US ARMY MOBILITY EQUIPMENT RESEARCH : DEV. CIR

AN EXPERIMENTAL INVESTIGATION OF EMP INDUCED TRANSIENT UPSET OF INTEGRATED CIRCUITS

SC-TM-71 0330

CIRCUS-2 A DIGITAL COMPUTER PROGRAM FOR TRANSIENT ANALYSIS OF ELECTRONIC CIRCUITS USER'S GUIDE

0070-1

RESEARCH ON THE PHYSICS OF TRANSIENT RADIATION EFFECTS

HDL-TM-060-3



UNA OVERSTRESS REVIEW  
SUBJECT INDEX

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

TITLE  
\*\*\*\*\*

DRAFT AEROSPACE VEHICLE EMI TRANSIENT TEST TECHNIQUES	BDM/A-51-72-14
SHIELDING EFFECTIVENESS OF THE LIQUID TIGHT FLEXIBLE CONDUIT FROM TRANSIENT TESTS	PEM-3
AEROSPACE VEHICLE EMI TRANSIENT TEST TECHNIQUES	AFAL-TR-72-102
LIGHTNING AND HIGH VOLTAGE SURGE PROTECTION FOR BALANCED DIGITAL TRANSMISSION DEVICES	ECON-4027
THEORETICAL AND EXPERIMENTAL STUDIES OF SEMICONDUCTOR DEVICE DEGRADATION DUE TO HIGH POWER ELECTRICAL TRANSIENTS	73SD4259
ASPECTS OF SEMICONDUCTOR DEVICE DAMAGE DUE TO ELECTRICAL TRANSIENTS (DRAFT COPY)	BDM/A-149-73-TR
COMPONENT DAMAGE FROM ELECTROMAGNETIC PULSE (EMP) INDUCED TRANSIENTS (DRAFT)	
EMP TRANSIENT SUPPRESSION	PEM-31
EMP SURGE SUPPRESSION CONNECTORS UTILIZING METAL OXIDE VARISTORS	HDL-TR-177-1
CAPACITOR FAILURE TO HIGH LEVEL ELECTRICAL TRANSIENTS DRAFT	
VOLTAGE CLAMPING LEVELS FOR SEVERAL "TRANSORB" TRANSIENT SUPPRESSION DEVICES	PEM-33
THE LLL TRANSIENT ELECTROMAGNETICS-MEASUREMENT FACILITY	PEM-47
CAPACITOR FAILURE DUE TO HIGH LEVEL ELECTRICAL TRANSIENTS	HDL-TR-75-25
OVERVOLTAGE TRANSIENT STUDIES OF LEVEL SENSOR AMPLIFIER CKTS.	HG-TR-71-5

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

TITLE  
\*\*\*\*\*

THE DAMAGE SUSCEPTIBILITY OF INTEGRATED CIRCUITS TO A SIMULATED IEMP  
TRANSIENT

ON THE NECESSARY AND SUFFICIENT CONDITIONS (THRESHOLDS) FOR DAMAGE  
OF SEMICONDUCTOR JUNCTIONS FROM ELECTRICAL TRANSIENTS

EMP TRANSIENT PROTECTION

DEM-31

DETERMINATION OF SEMICONDUCTOR FAILURE LEVELS DUE TO HIGH VOLTAGE  
TRANSIENTS

TRANSIENT COLLECTOR BREAKDOWN IN THE PRESENCE OF GAMMA RADIATION AND  
CONDUCTED EMP

HIGH CURRENT TRANSIENT INDUCED JUNCTION SHORTS

\*\*\*\*\*TRANSISTORS

TRANSISTOR JUNCTION TEMPERATURE AS A FUNCTION OF TIME

A NEW HIGH CURRENT MODE OF TRANSISTOR OPERATION

AN ASPECT OF SECOND BREAKDOWN IN TRANSISTORS

TRANSISTOR DEGRADATION FOLLOWING SECOND BREAKDOWN

SECOND BREAKDOWN IN SIMPLIFIED TRANSISTOR STRUCTURES AND DIODES

VOL. ED-13, NOS 8/9

TRANSISTOR FAILURE BY SECOND BREAKDOWN

VOL. ED-13 NOS. 8/9

TRANSIENT JUNCTION TEMPERATURE RISE AND SECOND BREAKDOWN IN  
TRANSISTORS

VOL. ED-13, NO.11

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

TITLE  
\*\*\*\*\*

VOL. ED-13, NO.11

VOL. ED-13, NO.11

SECOND BREAKDOWN IN MOS TRANSISTORS

CURRENT MODE SECOND BREAKDOWN IN EPIITAXIAL PLAYAR TRANSISTORS

SOME NEW ASPECTS OF THERMAL INSTABILITY OF THE CURRENT  
DISTRIBUTION IN POWER TRANSISTORS

THERMAL SWITCHBACK IN HIGH F-T EPIITAXIAL TRANSISTORS

EXPERIMENTAL DEMONSTRATION AND THEORY OF A CORRECTIVE TO  
SECOND BREAKDOWN IN SI POWER TRANSISTORS

A CHARACTERIZATION TECHNIQUE FOR SECOND BREAKDOWN IN GE  
ALLOYED JUNCTION TRANSISTORS

SECOND BREAKDOWN IN THE FORWARD AND REVERSE BASE CURRENT REGION

STATIC V-I RELATIONSHIPS IN TRANSISTORS AT HIGH INJECTION LEVEL

DETERMINATION OF A PHYSICAL MODEL FOR DOUBLE DIFFUSED TRANSISTORS

DETERMINATION OF THRESHOLD FAILURE LEVEL OF SEMICONDUCTOR DIODES AND  
TRANSISTORS DUE TO PULSE VOLTAGES.

DETERMINATION OF THRESHOLD FAILURE LEVELS OF SEMICONDUCTOR DIODES  
AND TRANSISTORS DUE TO PULSE VOLTAGES

DETERMINATION OF THRESHOLD FAILURE LEVELS OF SEMICONDUCTOR DIODES  
AND TRANSISTORS DUE TO PULSE VOLTAGES

A COMPUTER MODEL FOR INTEGRATED CIRCUIT TRANSISTORS INCLUDING  
SUBSTRATE INTERACTIONS

THERMAL INSTABILITY LIMITING POWER DISSIPATION IN TRANSISTORS

UNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*  
DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

SEMICONDUCTOR VULNERABILITY PHASE II REPORT THEORETICAL ESTIMATES  
FAILURE LEVELS OF SELECTED SEMICONDUCTOR DIODES AND TRANSISTORS  
BDM/A-42-69-M

DETERMINATION OF THRESHOLD FAILURE LEVELS DUE TO HIGH VOLTAGE  
TRANSIENTS FOR A GA 5393J TRANSISTOR  
BDM/A-27-69-M

SEMICONDUCTOR VULNERABILITY-PHASE II REPORT-THEORETICAL ESTIMATES  
OF FAILURE LEVELS OF SELECTED SEMICONDUCTOR DIODES AND TRANSISTORS  
BDM/A-42-69-M

MODELS FOR THE PN DIODE AND THE NPN AND PNP TRANSISTOR FOR USE IN  
COMPUTER AIDED DESIGN AND ANALYSIS PROGRAMS

TRANSISTOR AND DIODE MODEL HANDBOOK  
69-521-1

THEORETICAL ESTIMATES OF FAILURE LEVELS OF SELECTED SEMICONDUCTOR  
DIODES AND TRANSISTORS  
HDM/A-34-69R

SEMICONDUCTOR VULNERABILITY PHASE III REPORT EXPERIMENTAL THRESHOLD  
FAILURE LEVELS OF SELECTED DIODES AND TRANSISTORS  
BDM/A-75-70-TR

NET TRANSISTOR AND DIODE LIBRARY TAPE 4925

CORRELATION BETWEEN SECOND BREAKDOWN AND INFRARED RADIATION IN  
POWER TRANSISTORS

INVESTIGATION INTO ELECTROMAGNETIC PULSE VULNERABILITY ON SELECTED  
BIPOLAR TRANSISTORS  
MDC E0278

SPECIAL REPORT ON POWER TRANSISTORS

DESIGNING ULTRAHIGH BIPOLAR TRANSISTORS

FAILURE ANALYSIS OF DAMAGED 2N700 TRANSISTORS  
NN/E-20/71

A COMPARISON OF TWO TRANSISTOR MODELS



ONA OVERSTRESS REVIEW  
SUBJECT INDEX

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

TITLE  
\*\*\*\*\*

MODELING OF BIPOLAR TRANSISTOR USING INTEGRAL CHARGE CONTROL MODEL  
WITH APPLICATION TO THIRD-ORDER DISTORTION STUDIES

SIMPLIFIED COMPUTER AIDED ANALYSIS OF DOUBLE DIFFUSED TRANSISTORS  
INCLUDING TWO-DIMENSIONAL HIGH LEVEL EFFECTS

EFFECT OF THE SPATIALLY VARYING MINORITY CARRIER MOBILITY IN THE  
SHIFT TRANSISTOR

LIMITATIONS IN MICROELECTRONICS-II. BIPOLAR TECHNOLOGY

A SIMPLE METHOD FOR DETERMINING STATIC PARAMETERS OF LARGE SIGNAL  
SEMICONDUCTOR DIODE AND TRANSISTOR MODELS

THERMIONIC SATURATION OF DIFFUSION CURRENTS IN TRANSISTORS

FAILURE THRESHOLD AND RESISTANCE OF THE PROTECTED AND UNPROTECTED  
2N2222 TRANSISTOR IN THE SHORT PULSE WIDTH REGIME PEM-7

CHARACTERIZATION AND MEASUREMENT OF THE BASE AND EMITTER  
RESISTANCE OF BIPOLAR TRANSISTORS VOL SC-7 NO.6

THE DEGRADATION OF MOS TRANSISTORS RESULTING FROM JUNCTION AVALANCHE VOL. 11  
BREAKDOWN

A TWO-DIMENSIONAL NUMERICAL ANALYSIS OF A SILICON NPN TRANSISTOR

COMPUTER-AIDED TWO DIMENSIONAL NUMERICAL ANALYSIS OF BIPOLAR  
TRANSISTORS

POWER TRANSISTOR AND THYRISTOR SPEC SHEETS DON'T TELL IT ALL

SEMICONDUCTOR VULNERABILITY VOL I THEORETICAL ESTIMATES OF FAILURE  
LEVELS OF SELECTED SEMICONDUCTOR DIODES AND TRANSISTORS-PHASE II AFWL-TR-73-119 VOL I

SEMICONDUCTOR VULNERABILITY VOL II - EXPERIMENTAL THRESHOLD FAILURE  
LEVELS OF SELECTED DIODES AND TRANSISTORS - PHASE III AFWL-TR-73-119 VOL II



DNA OVERSTRESS REVIEW  
SUBJECT INDEX

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

TITLE  
\*\*\*\*\*

IC SIMULATES POWER TRANSISTOR

MICROWAVE INDUCED DAMAGE AND FAILURE MODES IN LOW FREQUENCY TRANSISTORS RELATED TO DEVICE DESIGN AND PROCESS CONTROL

TECHNIQUES FOR SCREENING BIPOLAR TRANSISTOR DEGRADATION DUE TO IONIZING RADIATION

ELECTRICAL PULSE BURNOUT OF TRANSISTORS IN INTENSE IONIZING RADIATION, PREPRINT

SECOND BREAKDOWN AND LOW FREQUENCY NOISE IN BIPOLAR JUNCTION TRANSISTORS

NOISE IN BIPOLAR JUNCTION TRANSISTORS AT HIGH INJECTION LEVELS

NEUTRON INDUCED NOISE IN JUNCTION FIELD EFFECT TRANSISTORS

BIPOLAR VOLTAGE PULSE DAMAGE EFFECTS ON TRANSISTORS

RADIATION EFFECTS IN MICROWAVE BIPOLAR TRANSISTORS

STUDY OF THE COMBINED EFFECTS OF IONIZATION, NEUTRONS, TEMPERATURE AND TIME ON BIPOLAR DEVICES.

SHORT PULSE WIDTH FAILURE LEVEL CHARACTERIZATION FOR THE 2N3821 JUNCTION FIELD EFFECT TRANSISTOR

TEMPERATURE DEPENDENCE OF JUNCTION TRANSISTOR PARAMETERS

COMPUTER ANALYSIS OF HOT SPOT FORMATION IN POWER TRANSISTORS

CURRENT CROWDING IN HARDENED POWER TRANSISTORS

NADCRANE TR/7024/C74/121

SAND 75-5222

AD 766-685

SC-DC-721233

SLA-73-402

PEM-24

UNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

A MATHEMATICAL MODEL FOR PRIMARY PHOTO-CURRENTS INDUCED IN  
TRANSISTOR BASE REGIONS

A COMPUTER MODEL FOR LATERAL THERMAL INSTABILITIES IN POWER  
TRANSISTORS

\*\*\*\*\*VOLTAGE

HIGH VOLTAGE CONDUCTIVITY MODULATED SILICON RECTIFIER

STATIC V-I RELATIONSHIPS IN TRANSISTORS AT HIGH INJECTION LEVELS

CALCULATIONS OF CUTOFF FREQUENCY, BREAKDOWN VOLTAGE, AND CAPACITANCE  
FOR DIFFUSED JUNCTIONS IN THIN EPITAXIAL SILICON LAYERS

PROTECTION OF SEMICONDUCTOR DEVICES, CIRCUITS AND EQUIPMENT  
FROM VOLTAGE TRANSIENTS

HIGH VOLTAGE THYRISTOR STRINGS FOR INVERTER APPLICATIONS

DETERMINATION OF THRESHOLD FAILURE LEVEL OF SEMICONDUCTOR DIODES AND  
TRANSISTORS DUE TO PULSE VOLTAGES.

DETERMINATION OF THRESHOLD FAILURE LEVELS OF SEMICONDUCTOR DIODES  
AND TRANSISTORS DUE TO PULSE VOLTAGES

DETERMINATION OF SEMICONDUCTOR FAILURE LEVELS DUE TO HIGH VOLTAGE  
TRANSIENTS

DETERMINATION OF THRESHOLD FAILURE LEVELS OF SEMICONDUCTOR DIODES  
AND TRANSISTORS DUE TO PULSE VOLTAGES

ESTIMATES OF SEMICONDUCTOR FAILURE DUE TO MULTIPLE VOLTAGE PULSES

THE BUILT-IN VOLTAGE OF DIFFUSED P-N JUNCTIONS

UNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*  
DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

DETERMINATION OF THRESHOLD FAILURE LEVELS DUE TO HIGH VOLTAGE TRANSIENTS FOR A GA 53933 TRANSISTOR	BDM/A-27-69-M
MEASUREMENTS AND ANALYSIS OF LIGHTNING INDUCED VOLTAGE IN AIRCRAFT ELECTRICAL CIRCUITS	HVL-69-161
JUNCTION CAPACITANCE AS A FUNCTION OF VOLTAGE FOR DIFFUSED P-N DIODES WITH EXPONENTIAL DOPING GRADIENTS	
LIFE TESTS OF 4MET SOLID TANTALUM CHIP CAPACITORS AT HIGHLY ACCELERATED VOLTAGES	M72-10
HIGH VOLTAGE ARC INTERRUPTION STUDY	RADC-TR-72-40
LIGHTNING AND HIGH VOLTAGE SURGE PROTECTION FOR BALANCED DIGITAL TRANSMISSION DEVICES	ECOM-4027
CONSTANT VOLTAGE DIODES ARE GETTING SHARPER	
VOLTAGE CLAMPING LEVELS FOR SEVERAL "TRANSORB" TRANSIENT SUPPRESSION DEVICES	PEM-33
PULSED VOLTAGE FAILURE LEVELS OF CAPACITORS GENERAL TEST PLAN	75SDS4241
BIPOLAR VOLTAGE PULSE DAMAGE EFFECTS ON TRANSISTORS	AD 766-685
OVERVOLTAGE TRANSIENT STUDIES OF LEVEL SENSOR AMPLIFIER CKTS.	RG-TR-71-5
DETERMINATION OF SEMICONDUCTOR FAILURE LEVELS DUE TO HIGH VOLTAGE TRANSIENTS	

\*\*\*\*\*

8-1 EMP RESPONSE FOR INADVERTENT PENETRATION COMPLYING FINAL REPORT (DRAFT) 0224-13064-1

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

TITLE  
\*\*\*\*\*

SECTION VI DESIGN PRACTICES



DNA OVERSTRESS REVIEW  
SUBJECT INDEX

TITLE  
\*\*\*\*\*

DOCUMENT NO./OTHER NO.  
\*\*\*\*\*

\*\*\*\*\*AIRCRAFT

EMP CHARACTERIZATION OF SPRINT AUTOMILJT COMPONENTS-FINAL REPORT	CREG 69-2
MEASUREMENTS AND ANALYSIS OF LIGHTNING INDUCED VOLTAGE IN AIRCRAFT ELECTRICAL CIRCUITS	MVL-69-161
INTERIM NOTES B-52 EMP TEST PROGRAM NOTE 5 GENERAL PROCEDURES FOR SUBSYSTEM EMP TESTING	BDM/A-121-70-PN
MISSILE AND AIRCRAFT COMPONENT VULNERABILITY TO EMP	SC-TM-70-902
RECOMMENDED INTERNAL COUPLING ANALYSIS TECHNIQUES FOR THE B-52S EMP TEST PROGRAM	BDM/A-66-71-1M
AERONAUTICAL SYSTEMS EMP TECHNOLOGY REVIEW	D224-10004-1
ELECTROMAGNETIC PULSE HANDBOOK FOR MISSILES AND AIRCRAFT IN FLIGHT	
DESIGN GUIDELINES FOR EMP HARDENING OF AERONAUTICAL SYSTEMS (DRAFT)	C72-451/201
B-52/VPD GENERAL TEST PLAN	D224-10000-1
AEROSPACE VEHICLE EMI TRANSIENT TEST TECHNIQUES	AFAL-TR-72-102
FIELD AND LABORATORY TESTING IDENTIFICATION AND SUMMARY AERONAUTICAL SYSTEMS EMP INTEGRATED TEST PROGRAM ROUGH DRAFT	D224-10012-1
DESIGN GUIDELINES FOR EMP HARDENING OF AERONAUTICAL SYSTEMS	AFWL-TR-73-117
SHORT COURSE IN NUCLEAR WEAPON EFFECTS AND SURVIVABILITY OF AEROSPACE SYSTEMS	



UNA OVERSTRESS REVIEW  
SUBJECT INDEX

DOCUMENT NO./JFH-4 NO.  
\*\*\*\*\*

TITLE  
\*\*\*\*\*

3-1 EMP SUBSYSTEM ASSESSMENT DATA UHF RADIO AN/44C-109	0224-13022-8
COMPARISON OF ANTENNA-RELATED PREDICTIVE MODELS WITH 3-1 SCALE MODEL MEASUREMENTS IN ALECS	0224-13052-2
F-111/ARES DETAIL TEST PLAN, VOLUME V PHASE II INTEGRATED TEST PLAN (FINAL)	0224-13004-5
DTP 3-1 SCALE MODEL ALECS, SEC. 6 FINAL DETAILED TEST PLAN	0224-13006-1
3-1 EMP RESPONSE FOR INADVERTENT PENETRATION COMPLYING FINAL REPORT (DRAFT)	0224-13064-1
F-111/ARES TEST SUPPORT, VOLUME I DRAFT FINAL REPORT	0224-13059-1
3-52 G/AGM-28A/VPD EXPERIMENT TECHNICAL REPORT VOLUME II DRAFT FINAL REPORT	0224-13069-2
VERTICALLY POLARIZED DIPOLE (VPD) 3-52/AGM-28A TECHNICAL REPORT VOLUME I (DRAFT)	0224-13069-1
EXTERNAL CUMULING OF AN ELECTROMAGNETIC PULSE TO THE 3-1 AIRCRAFT	0224-13060-1
EMP RESPONSE OF THE 3-1 AIRCRAFT FOR INADVERTENT PENETRATION COMPLYING VOLUME I, FINAL REPORT	0224-13064-1
FINAL REPORT ON THE PRELIMINARY 3-1 EVALUATION OF EMP RELATED AIRCRAFT C/3-310/201 CHARACTERISTICS VOLUME II	
FINAL REPORT EC-135 PRETEST ANALYSIS VOLUME II SYSTEMS DESCRIPTION	WDM/A 12-71-41
AABNCP LOW LEVEL TEST PLAN	0226-10109-1

\*\*\*\*\*ANALYSIS

DIFFUSED JUNCTION DEPLETION LAYER CALCULATIONS

DNA OVERSTRESS REVIEW  
SUBJECT INDEX

DOCUMENT NO./OTHER NO.  
.....

TITLE  
.....

0224-12013-1

ASAP-1 FINAL REPORT

0180-17726-1

TEST REPORT FOR EC-135C INTERNAL COUPLING MEASUREMENTS

ENGINEERING DESIGN GUIDELINES FOR EMP HARDENING OF NAVAL MISSILES  
AND AIRPLANES

MATHEMATICAL MODELS FOR THE RESPONSE OF AEROSPACE SYSTEMS TO HIGH  
FREQUENCY ELECTROMAGNETIC ENVIRONMENTS

IDENTIFICATION FRIEND OR FOE/AIR TRAFFIC CONTROL (IFF/ATC) SYSTEM  
AN/APX-72 SYSTEM DESCRIPTION

AN/ART-47 UHF RADIO TRANSMITTER SET SYSTEM DESCRIPTION

AIRBORNE COMMAND POST AASNC ELECTRONIC SYSTEM DETAILED PROGRAM PLAN CDRL 4018  
INTERIM REPORT

B-1 SCALE MODEL PRELIMINARY TEST PLAN FOR MEASUREMENT OF WEAPONS  
BAY AND WHEEL WELL COUPLING (FINAL)

DETAILED TEST PLAN B-1 SCALE MODEL/ALECS TEST PROGRAM SECTION 5

F-111/ARES DETAIL TEST PLAN VOL.222, EXTERNAL COUPLING AND DELIBERATE  
ANTENNA EXPERIMENTS

POST EXPERIMENT SUMMARY OF B-1 SCALE MODEL MEASUREMENTS FOR T03-19  
INADVERTENT PENETRATIONS

SRAM/ARES DETAIL TEST PLAN

B-1 ALECS POST EXPERIMENT SUMMARY FOR TECHNICAL DIRECTIVE J-14  
MEASUREMENTS

B-1 EMP SUBSYSTEM ASSESSMENT DATA, IFF AN/APX-66

0224-13022-10

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